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(54) Title: ACENAPHTHYLENE IMIDE-DERIVED SEMICONDUCTORS

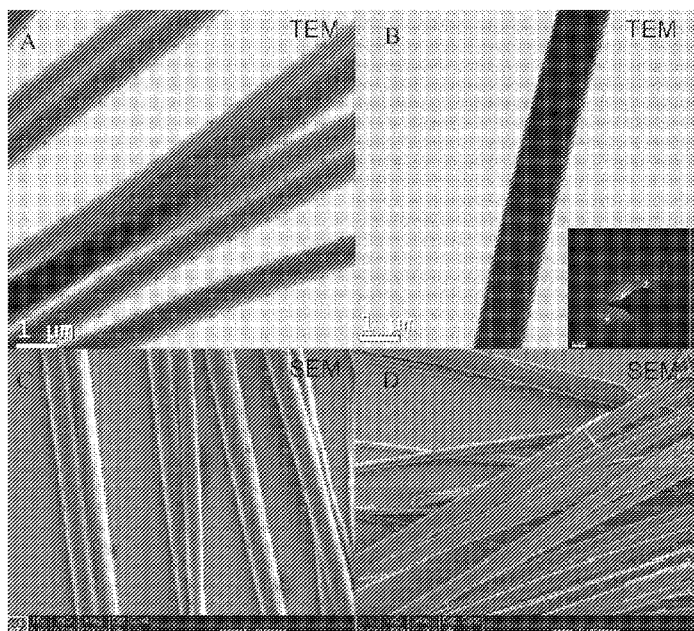


Figure 1

(57) Abstract: Novel acenaphthylene imide-derived semiconductor materials, including small molecule compounds, polymers and oligomers. Also provided are methods for making the novel semiconductor materials and the use of the novel semiconducting materials in electronic or optoelectronic device. In some embodiments, the novel semiconducting materials are used as n-channel component in organic field-effect transistors as well as complementary electronic circuits including inverters. High mobility can be achieved.



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ACENAPHTHYLENE IMIDE-DERIVED SEMICONDUCTORS

BACKGROUND

N-type organic semiconductors are needed for fabricating n-channel organic field effect transistors, p-n junction diodes, and complementary organic logic circuits. However, high performance electron transport materials are still relatively rare. Therefore, development of new n-type organic semiconductors with high charge carrier mobility, improved processability, high thermal and oxidative stability remains a major challenge in the field of organic electronics.

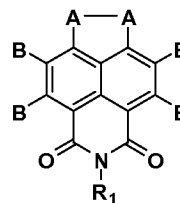
Among the existing n-type organic semiconductors, naphthalene diimides (NDIs) and perylene diimides (PDIs) and their derivatives are of particular interest as electron-transport materials because of their high electron affinity, chemical stability, as well as their relatively large planar structures (Anthony *et al.*, *Adv. Mater.* 2010, 22, (34), 3876; Zhan *et al.*, *Adv. Mater.* 23, (2), 268). Recent research has also developed other new diimide compounds, such as benzene and anthracene diimides (Zheng *et al.*, *J. Am. Chem. Soc.* 2008, 130, 14410; Wang *et al.*, *J. Am. Chem. Soc.* 2007, 129, 13362). Other attempts have also aimed to increase the molecular size in order to extend the π -conjugation and promote better solid state packing by expansion of the NDI and PDI cores (Gao *et al.*, *J. Am. Chem. Soc.* 2010, 132, 3697; Tan *et al.*, *J. Mater. Chem.*, 2011, 21, (44), 18042). Beside the interesting properties obtained from thin films of arylene diimides, self-assembly of nanowires of naphthalene diimides and perylene diimides and their applications in organic nanoelectronics have also been extensively investigated, showing that a dramatic increase in electron mobility can result from crystalline nanostructures (Kim *et al.*, *Chem. Mater.* 2011, 23, 682; Briseno *et al.*, *Nano Lett.* 2007, 7, 2847). Another family of n-type organic semiconductors which has drawn attention is the imine nitrogen-containing heteroaromatics, including pyridine, quinoline, pyrazine, thiazole, benzothiadiazole, benzobisthiazole, etc. Members of this later class are also known for their low lying LUMO energy levels, high electron affinities and high field-effect mobilities (Tonzola *et al.*, *J. Am. Chem. Soc.* 2003, 125, 13548).

Further, polymer-based semiconductors have also been studied in Babel *et al.*, *J. Am. Chem. Soc.*, 2003, 125, 13656; Briseno *et al.*, *Chem. Mater.* 2008, 20, 4712; Chen *et al.*, *J. Am. Chem. Soc.* 2009, 131, 8; Yan *et al.*, *Nature* 2009, 457, (7230), 679; Huttner *et al.*, *Appl. Phys. Lett.* 2008, 92, 093302; Letizia *et al.*, *J. Am. Chem. Soc.* 2008, 130, (30), 9679; Zhan *et al.*, *J. Am. Chem. Soc.* 2007, 129, 7246; and Ahmed *et al.*, *Chem. Mater.* 2011, 23, (20), 4563.

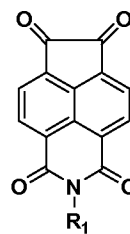
Thus, a need exists for novel organic semiconductors, including n-type small molecule-based and polymer-based semiconductors suitable for uses as active components in organic electronic and optoelectronic devices. In particular, materials which provide good transistor performance such as high charge mobility, high on/off current ratios, and low threshold voltages are needed. Good solubility and thermal stability is also needed.

SUMMARY

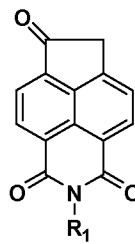
Embodiments described herein include compounds, compositions, devices, methods of making, and methods of using.



For example, provided is a compound represented by: (I), wherein: (i) one or both of A are $-\text{C}(\text{O})-$, and the remaining A, if any, is $-\text{CH}_2-$; (ii) R_1 is an optionally substituted $\text{C}_1\text{-C}_{50}$ organic group; and (iii) B at each occurrence is independently selected from hydrogen, halogen, cyano, nitro, optionally substituted alkyl group and optionally substituted heteroalkyl group, or a structure wherein each pair of substituents B in ortho position optionally forms a conjugated ring.

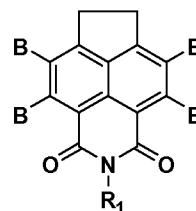


In one embodiment, the compound is represented by: (II).



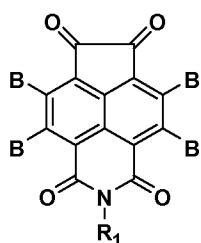
In another embodiment, the compound is represented by: (III).

Also provided is a method for making the compound described above, comprising



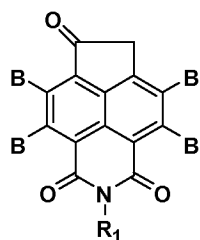
(i) reacting an oxidant with a compound represented by formula (IV): (IV),

wherein R_1 and B have the same definitions as previously described; and (ii) separating a first



product represented by

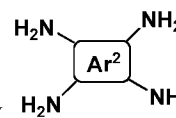
(V) from a second product represented by

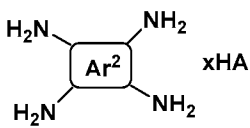


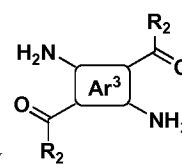
(VI). In one embodiment, the oxidant is selected from CrO_3 and SeO_2 .

Also provided is a method for using the compound described above, comprising reacting said compound with a second compound comprising one or more primary amine groups.

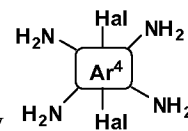
In one embodiment, the second compound is represented by



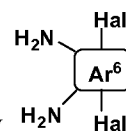
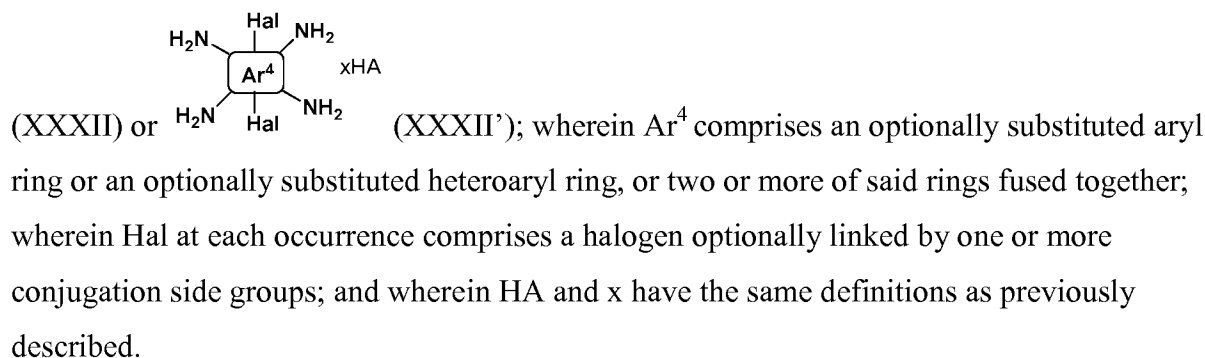
its acid complex  (XX'); wherein Ar^2 comprises an optionally substituted aryl ring or an optionally substituted heteroaryl ring, or two or more of said rings fused together; and wherein HA is HCl, HBr, HI, CH_3COOH , H_2SO_4 or H_3PO_4 , x is 1, 2, 3 or 4.

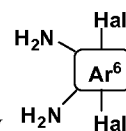


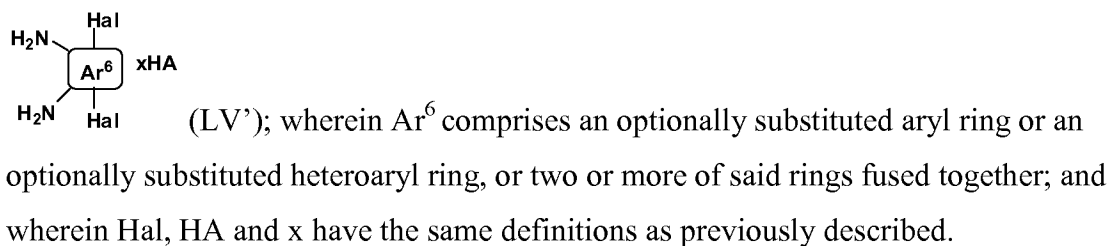
In another embodiment, the second compound is represented by (XXII); wherein Ar^3 comprises an optionally substituted aryl ring or an optionally substituted heteroaryl ring, or two or more of said rings fused together; and wherein R_2 at each occurrence is an end group optionally linked by a single bond or by one or more conjugation side groups.



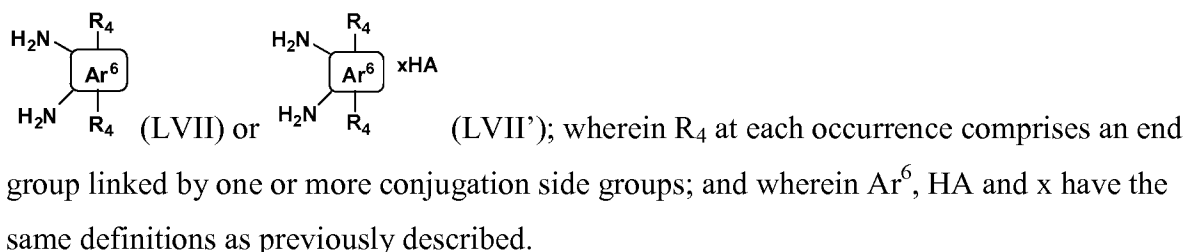
In a further embodiment, the second compound is represented by



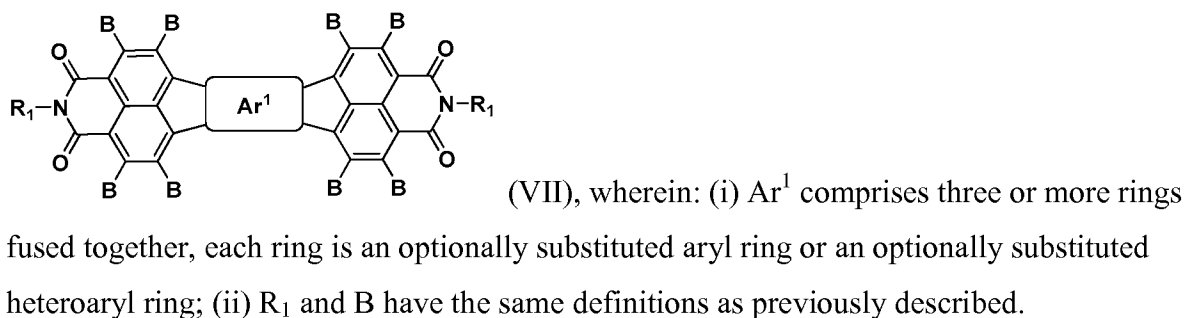
In yet another embodiment, the second compound is represented by  (LV) or



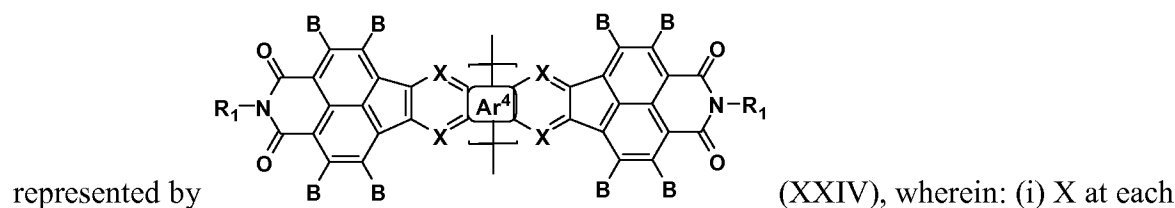
In yet a further embodiment, the second compound is represented by represented by



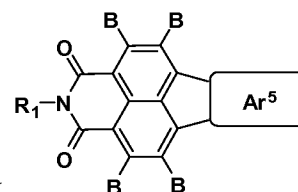
Further provided is a compound represented by:



Further provided is a polymer comprising one or more first repeating units RU1

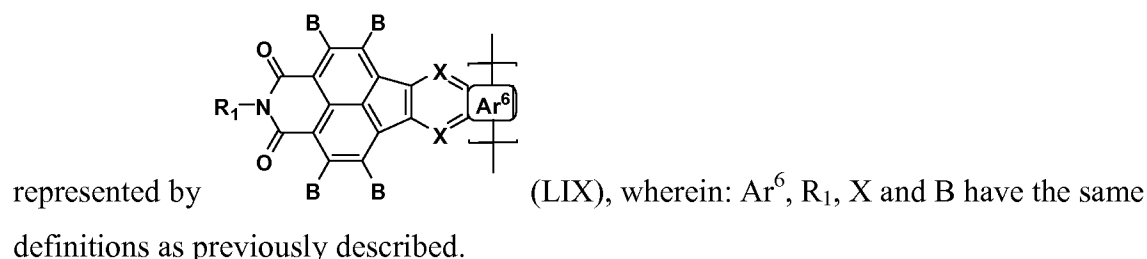


occurrence is independently selected from —N= and $\text{—C(R}_2\text{)=}$; and (ii) Ar⁴, R₁, R₂ and B have the same definitions as previously described.



Additionally provided is a compound represented by (XXXIV), wherein: (i) Ar⁵ comprises two or more rings fused together, each ring is an optionally substituted aryl ring or an optionally substituted heteroaryl ring; (ii) R₁ and B have the same definitions as previously described.

Additionally provided is a polymer comprising one or more first repeating units RU3



Also provided are compositions as well as electronic or optoelectronic devices comprising at least one compound or polymer described herein or made by any of the methods described herein. In one embodiment, the device is a transistor such as an organic-field effect transistor. In another embodiment, the device is a complementary electronic circuit such as an inverter.

At least one advantage for at least some embodiments of the semiconducting materials described herein is high charge carrier mobility.

At least another advantage for at least some embodiments of the semiconducting materials described herein is good solution processability.

At least another advantage for at least some embodiments of the semiconducting materials described herein is good thermal stability.

At least one further advantage for at least some embodiments of the semiconducting materials described herein is increased electron affinity.

At least one further advantage for at least some embodiments of the semiconducting materials described herein is extended π -conjugation and improved intermolecular electronic coupling.

At least one further advantage for at least one of the embodiments of the semiconducting materials described herein is ready self-assembling into single crystalline nano- or microstructures.

At least one further advantage for at least one of the embodiments of the semiconducting materials described herein is good switching characteristics when used as the n-channel component in complementary electronic circuits such as an inverter.

At least one further advantage for at least one of the embodiments of the semiconducting materials described herein is comparable on-current and off-current when used as n-channel component in complementary electronic circuits such as an inverter.

At least one further advantage for at least one of the embodiments of the semiconducting materials described herein is high gain when used as n-channel component in complementary electronic circuits such as an inverter.

Another further advantage for at least some embodiments is synthetic versatility and ability to tune the electronic properties based on structural variations.

BRIEF DESCRIPTION OF THE DRAWINGS

Figure 1 shows SEM and TEM images with corresponding electron diffraction (inset) of an exemplary compound described herein (BFI)

Figure 2 shows XRD patterns of the thin film of an exemplary polymer described herein (PBFI-T), drop-casted on a glass substrate after annealing at 250 °C for 10 min. The plots of intensity vs 2θ were collected in a selected area; the incident angle between the input beam and the sample was fixed at 3°; the substrate is fixed at 90° (A) and the incident angle between the input beam and the sample was fixed at 5°; the substrate is fixed at 90° and 54.5° to give a in plane (green line) and out of plane (blue line, (B)) signals, respectively.

Figure 3 (A, B) Current–voltage output and transfer curves of the PBFI-T transistors with silver source-drain electrodes on an OTS8-treated substrate after annealing for 10 min at 200 °C. A field-effect electron mobility of 0.3 cm²/Vs was observed in saturation region. (C,

D) Output curve family and transfer curves of PBFI-BT transistors with gold electrodes on a BCB-treated substrate after annealing for 10 min at 200 °C.

Figure 4 shows annealing temperature dependence of electron mobility of PBFI-T transistors with various electrodes: silver (black square), gold (wine circle), and calcium capped with gold (green triangle).

Figure 5 shows transfer curves of constituent polymer transistors in polymer complementary inverters based on PBFI-T (n-channel) and PSOxTT (p-channel) transistors.

Figure 6 shows static switching characteristics of the polymer complementary inverters based on PBFI-T (n-channel) and PSOxTT (p-channel) transistors: Output voltage (A), gain (B) and current (C) as a function of input voltage (V_{IN}) with various power supply voltages (V_{DD}).

Figure 7 shows: a) J-V characteristics of PSEHTT:T2-BFI (1:4 wt/wt) blend solar cell and b) the corresponding EQE spectrum.

DETAILED DESCRIPTION

INTRODUCTION

All references described herein are hereby incorporated by reference in their entireties. Various terms are further described herein below:

“A”, “an”, and “the” can refer to “at least one” or “one or more” unless specified otherwise.

“Optionally substituted” groups can refer to, for example, functional groups that may be substituted or unsubstituted by additional functional groups. For example, when a group is unsubstituted, it can be referred to as the group name, for example alkyl or aryl. When a group is substituted with additional functional groups, it may more generically be referred to as substituted alkyl or substituted aryl.

“Alkyl” can refer to, for example, linear, branched, or cyclic alkyl groups. This term is exemplified by groups such as methyl, ethyl, n-propyl, isopropyl, n-butyl, t-butyl, n-pentyl, ethylhexyl, dodecyl, isopentyl, cyclohexyl, and the like.

“Aryl” can refer to, for example, aromatic carbocyclic groups having one or more single rings (e.g., phenyl or biphenyl) or multiple condensed rings (e.g., naphthyl or anthryl).

“Heteroalkyl” can refer to, for example, an alkyl group wherein one or more carbon atoms are substituted with heteroatoms.

“Heteroaryl” can refer to, for example, an aryl group wherein one or more carbon atoms are substituted with heteroatoms.

“Fluoroalkyl” can refer to, for example, an alkyl group wherein one or more hydrogen atoms are substituted with fluoro. Fluoroalkyl described herein include perfluoroalkyl as well as partially fluorinated alkyl.

“Fluoroalkoxide” can refer to, for example, an alkoxide group wherein one or more hydrogen atoms are substituted with fluoro. Fluoroalkoxide described herein include perfluoroalkoxide group as well as partially fluorinated alkoxide.

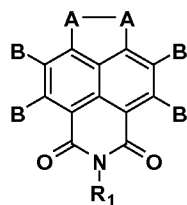
“n” and “m” can refer to a positive integer.

PART I – MONOKETO AND DIKETO INTERMEDIATE

STRUCTURE OF MONOKETO AND DIKETO INTERMEDIATE

A variety of 1,2-dihydroacenaphthylene-based compounds are known in the art and described in, for example, (i) Huang *et al.*, *Dyes Pigm.* 2011, 90, (3), 297-303; (ii) Sun *et al.*, *Org. Lett.* 2010, 12, (20), 4690-4693; (iii) Nietfeld *et al.*, *The Journal of Organic Chemistry* 2011, 76, (15), 6383-6388; (iv) Palmaerts *et al.*, *Polymer* 2009, 50, (21), 5007-5015; (v) Wen *et al.*, *Synth. Met.* 2009, 159, (21-22), 2299-2301; (vi) González *et al.*, *The Journal of Physical Chemistry A* 2008, 112, (29), 6732-6740; (vii) Ortiz *et al.*, *J. Am. Chem. Soc.* 2010, 132, (24), 8440-8452; (viii) Trost *et al.*, *J. Am. Chem. Soc.* 1971, 93, 737-745; (ix) Trost *et al.*, *J. Am. Chem. Soc.* 1969, 91, (4), 918-923; and (x) WO/2009/126203, all of which are hereby incorporated by reference by their entireties.

Many embodiments described herein relate to a compound represented by formula (I):



(I), wherein: (i) one or both of A are $-\text{C}(\text{O})-$, and the remaining A, if any, is $-\text{CH}_2-$; (ii) R_1 is an optionally substituted C_1 - C_{50} organic group; and (iii) B at each occurrence is independently selected from hydrogen, halogen, cyano, nitro, optionally substituted alkyl group and optionally substituted heteroalkyl group, or a structure wherein each pair of substituents B in ortho position optionally forms a conjugated ring.

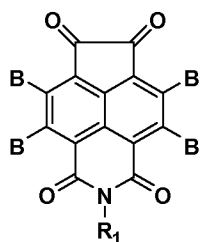
R_1 can be, for example, an optionally substituted linear, branched or cyclic C_1 - C_{36} alkyl group or an optionally substituted linear, branched or cyclic C_1 - C_{36} heteroalkyl group. R_1 can be, for example, an optionally substituted linear or branched C_{12} - C_{36} alkyl group or an optionally substituted linear or branched C_{12} - C_{36} heteroalkyl group. R_1 can be, for example, unsubstituted or substituted with one or more halogens. R_1 can be, for example, a linear or

branched fluoroalkyl group or a linear or branched fluoroalkoxide group. In addition, R_1 can be any other solubilizing group known in the art.

B can be, for example, hydrogen, halogen, cyano, nitro, an optionally substituted alkyl group, or an optionally substituted heteroalkyl group. B at each occurrence can be, for example, hydrogen, fluoro, a linear or branched C_1 - C_{24} , C_1 - C_{12} or C_1 - C_6 alkyl group, or a linear or branched C_1 - C_{24} , C_1 - C_{12} or C_1 - C_6 heteroalkyl group. In addition, for example, B at each occurrence can be hydrogen or independently selected from an optionally substituted C_1 - C_{30} organic group. In one embodiment, each B is the same. This can provide for a symmetrical compound.

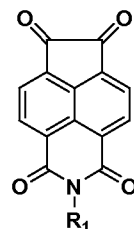
In one embodiment, B at each occurrence is hydrogen. In another embodiment, each pair of substituents B in ortho position forms a conjugated ring such as, for example, a benzene ring. In a further embodiment, at least one B comprises a reactive group. In yet another embodiment, at least two B comprise reactive groups, and the compound is a monomer suitable for polymerization. In yet a further embodiment, at least one B comprises a side conjugation group described herein.

In some embodiments, both A are $-C(O)-$, and the compound is a diketo intermediate



represented by formula (V):

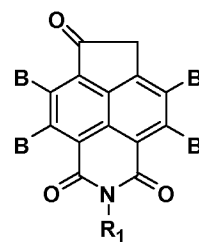
(V). In a particular embodiment wherein B is



hydrogen, the diketo intermediate can be represented by formula (II):

(II).

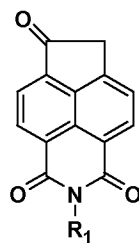
In some embodiments, only one A is $-C(O)-$ with the other being hydrogen, and the



compound is a monoketo intermediate represented by formula (VI):

(VI). In

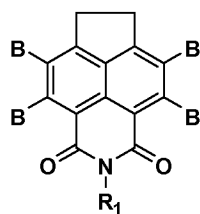
a particular embodiment wherein B is hydrogen, the monoketo intermediate is represented by



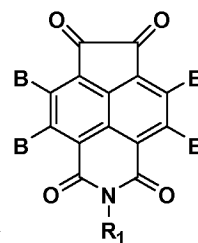
formula (III): (III).

METHODS FOR MAKING MONOKETO AND DIKETO INTERMEDIATE

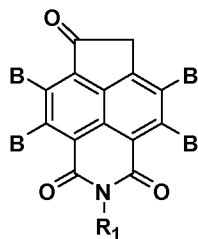
The monoketo intermediate and the diketo intermediate described herein can be made by, for example, reacting an oxidant with a compound represented by formula (IV):



(IV), and separating a first product represented by



(V) from a



second product represented by (VI).

Oxidation agents and oxidants are generally known in the art. The oxidant can be, for example, selected from CrO_3 , H_2CrO_4 , Na_2CrO_4 , O_3 , RCO_3H , $\text{tBuOOH}/\text{NaOCl}$, $\text{DMSO}/\text{PyHBr}_3$, $\text{DMSO}/2\text{-pyrrolidinone HBr}_3$, SeO_2 and MnO_2 . In one embodiment, the oxidant is CrO_3 . In another embodiment, the oxidant is SeO_2 .

The first product and the second product can be obtained under different reaction conditions, for example under different reaction temperatures. See, for example, working examples below.

The first product and the second product can be separated by, for example, chromatographic methods. Various chromatographic methods are known in the art and described in, for example, James M. Miller, *Chromatography: Concepts and Contrasts*, 2nd Ed., John Wiley, 2009, which is hereby incorporated by reference in its entirety. In a particular embodiment, the first product and the second product are separated by thin film chromatography.

USE OF MONOKETO AND DIKETO INTERMEDIATE

Reactions at the ketone can be carried out as known in organic synthetic chemistry. For example, the ketone can be reacted with nucleophilic groups. The monoketo intermediate and the diketo intermediate described herein can be used to, for example, synthesize downstream compounds, monomers, oligomers, and polymers. The intermediate compound can be reacted with, for example, a second compound comprising one or more amine groups, including primary and secondary amines, preferably primary amine groups.

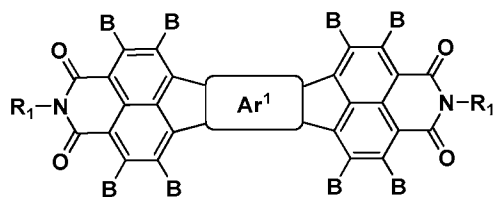
The second compound can comprise, for example, at least one primary amine group, at least two primary amine groups, or at least four primary amine groups. The second compound can comprise, for example, at least one aromatic or heteroaromatic ring. The aromatic or heteroaromatic ring can be, for example, a five-membered ring or a six-membered ring. The second compound can comprise, for example, one pair of ortho-positioned primary amine groups on an aromatic or heteroaromatic ring, or two pairs of ortho-positioned primary amine groups on the same or two different aromatic or heteroaromatic rings. The second compound can comprise, for example, one pair of ortho-positioned groups, comprising a primary amine group and a ketone or an aldehyde group, on an aromatic or heteroaromatic ring. The second compound can comprise, for example, two pairs of ortho-positioned groups, each pair comprising a primary amine group and a ketone or an aldehyde group, on the same or two different aromatic or heteroaromatic rings.

Additional reactions for the ketone compounds are described hereinbelow.

PART II – TYPE-A COMPOUND

STRUCTURE OF TYPE-A COMPOUND

Many embodiments described herein relate to Type-A compounds represented by formula (VII):

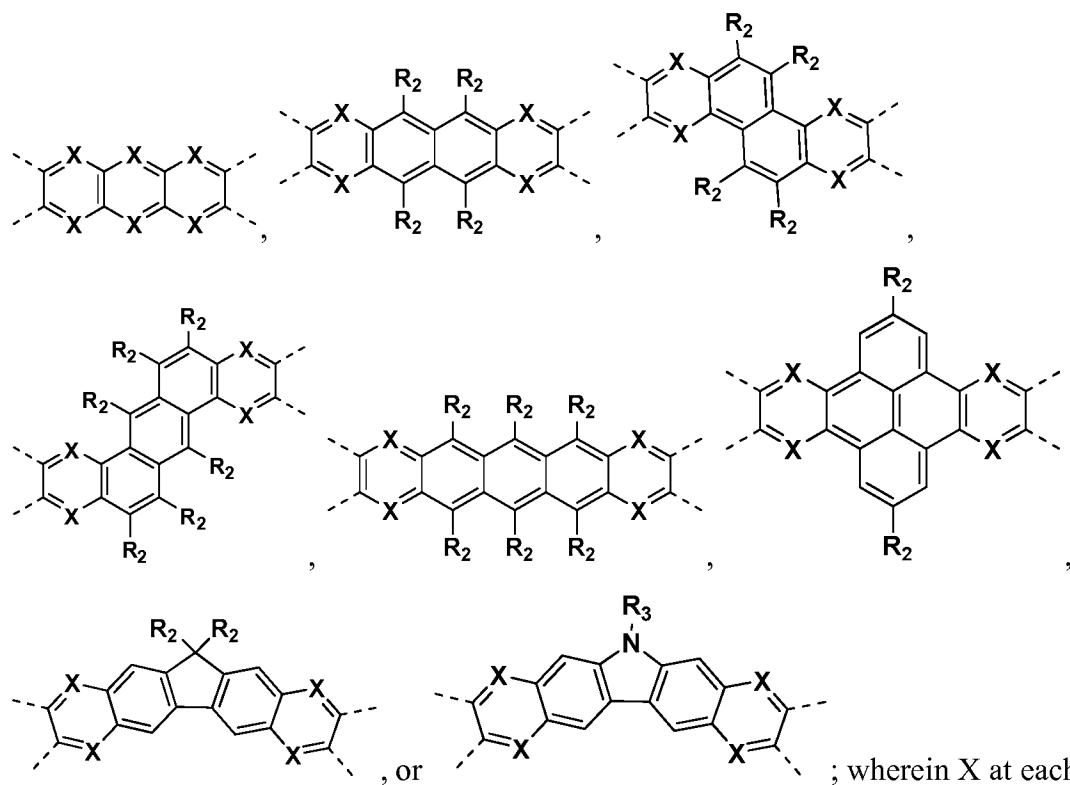


(VII), wherein: (i) Ar¹ comprises three or more rings fused together, each ring is an optionally substituted aryl ring or an optionally substituted heteroaryl ring; (ii) R₁ and B have the same definitions as previously described.

Ar¹ can be, for example, a heteroaryl group comprising in the heteroaromatic ring(s) one or more N heteroatoms, or two or more N heteroatoms, or three or more N heteroatoms,

or four or more N heteroatoms, or five or more N heteroatoms, or six or more N heteroatoms. Ar¹ can be, for example, a heteroaryl group comprising one or more imine moieties, or two or more imine moieties, or three or more imine moieties, or four or more imine moieties, or five or more imine moieties, or six or more imine moieties.

In some embodiments, B is hydrogen and Ar¹ is represented by, for example,



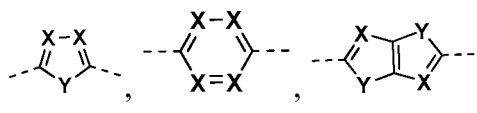
occurrence is independently selected from —N= and $\text{—C(R}_2\text{)=}$.

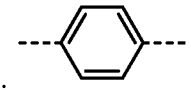
R₂ at each occurrence can comprise, for example, an end group or a substituent and optionally one or more conjugation side groups linking the end group (or substituent) and the aromatic group that R₂ is attached to. When R₂ comprises at least one conjugation side group, the end group (or substituent) can be linked to the aromatic group via said conjugation side group. When R₂ comprises no conjugation side group, the end group (or substituent) can be linked directly to the aromatic group by a single bond.

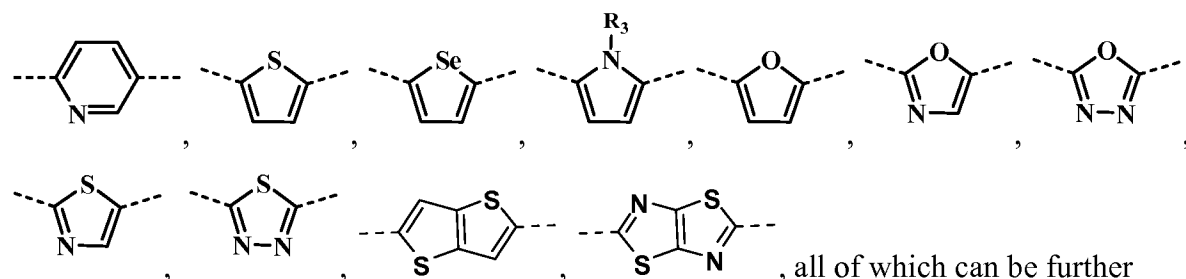
The end group or substituent described herein can be, for example, selected from hydrogen, halogen, cyano, nitro, an optionally substituted alkyl group and an optionally substituted heteroalkyl group. The end group or substituent can be, for example, hydrogen, cyano, an optionally substituted linear or branched C₁-C₂₄, C₁-C₁₂ or C₁-C₆ alkyl group, or an optionally substituted linear or branched C₁-C₂₄, C₁-C₁₂ or C₁-C₆ heteroalkyl group. The end

group or substituent can be, for example, unsubstituted or substituted with one or more halogens. The end group or substituent can be, for example, a linear or branched fluoroalkyl group or a linear or branched fluoroalkoxide group. In some particular embodiments, R_2 comprises at least one conjugation side group, and the end group or substituent is selected from hydrogen, cyano, a linear or branched alkyl such as $-CH_3$, and a linear or branched fluoroalkyl such as $-CF_3$.

The optional conjugation side group described herein can be, for example, independently selected from an optionally substituted aryl group, an optionally substituted heteroaryl group, an optionally substituted ethynylene, and ethynylene. The conjugation side group, can be, for example, an optionally substituted C_5 - C_{24} or C_5 - C_{12} aryl group, or an optionally substituted C_5 - C_{24} or C_5 - C_{12} heteroaryl group. In some embodiments, each

conjugation side group is independently selected from , $\text{---}\text{X}=\text{X}\text{---}$ and $\text{---}\equiv\text{---}$; wherein Y is O, S, Se, Te, $N(R_3)$, $C(R_3)_2$, $Si(R_3)_2$. Particular

embodiments of the conjugation side group include the following: ,

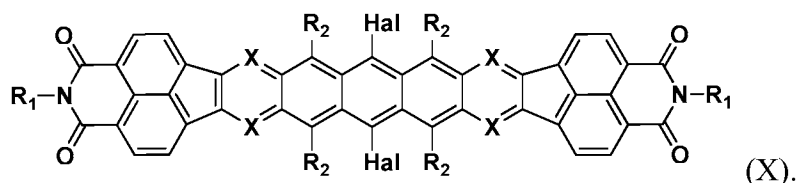
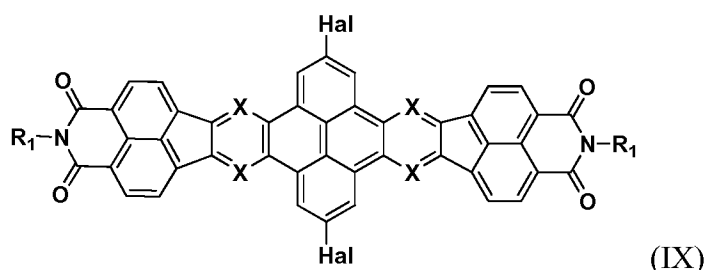
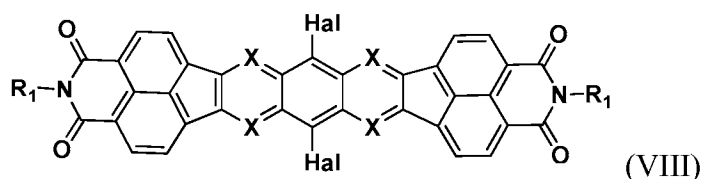


all of which can be further substituted with, for example, an optionally substituted linear or branched C_1 - C_{24} , C_1 - C_{12} or C_1 - C_6 alkyl group including fluoroalkyl, or an optionally substituted linear or branched C_1 - C_{24} , C_1 - C_{12} or C_1 - C_6 heteroalkyl group including fluoroalkoxide.

R_3 can be, for example, hydrogen, cyano, an optionally substituted linear or branched C_1 - C_{24} , C_1 - C_{12} or C_1 - C_6 alkyl group, or an optionally substituted linear or branched C_1 - C_{24} , C_1 - C_{12} or C_1 - C_6 heteroalkyl group. R_3 can be, for example, unsubstituted or substituted with one or more halogens. R_3 can be, for example, a linear or branched fluoroalkyl group or a linear or branched fluoroalkoxide group. Particular embodiments of R_3 include hydrogen, cyano, a linear or branched alkyl such as $-CH_3$, and a linear or branched fluoroalkyl such as $-CF_3$.

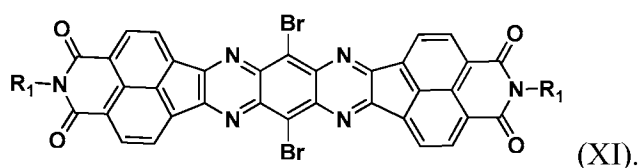
Many embodiments of the Type-A compound described herein relate to a monomer (Type-A monomer) suitable for polymerization or copolymerization, wherein Ar¹ comprises one or more, or two or more polymerizable groups. Polymerizable groups are known in the art and include, for example, halogen atoms such as Br.

In some embodiments, the Type-A monomer is selected from formulae (VIII), (IX) and (X):

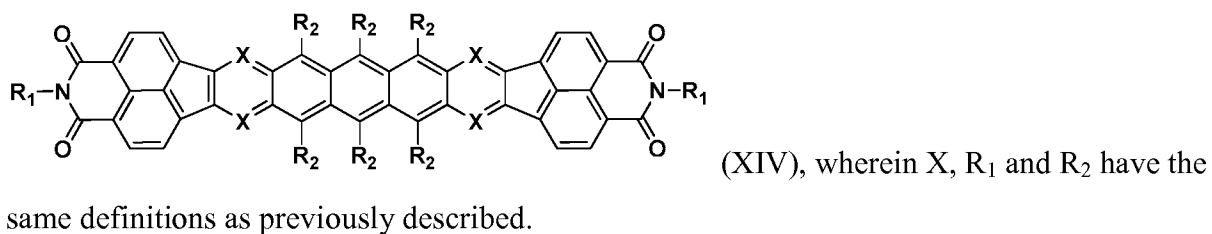
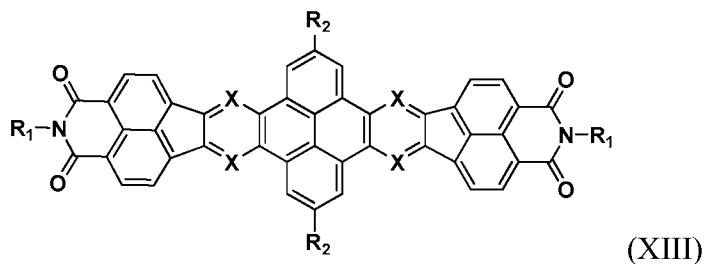
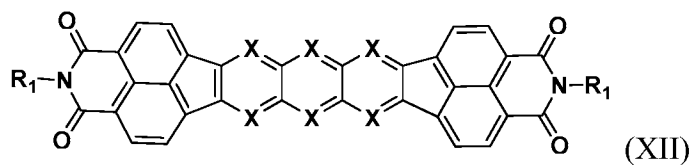


X, R₁, R₂ and the conjugation side group have the same definitions as previously described. Hal at each occurrence can comprise, for example, an halogen and optionally one or more conjugation side groups linking the halogen and the aromatic group that Hal is attached to. The halogen can be, for example, Br. The halogens can be para to each other. When Hal comprises at least one conjugation side group, the halogen can be linked to the aromatic group via said conjugation side group. When Hal comprises no conjugation side group, the halogen can be linked directly to the aromatic group by a single bond.

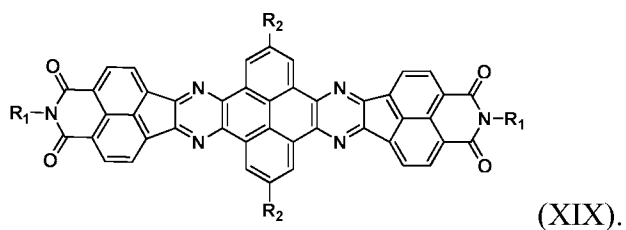
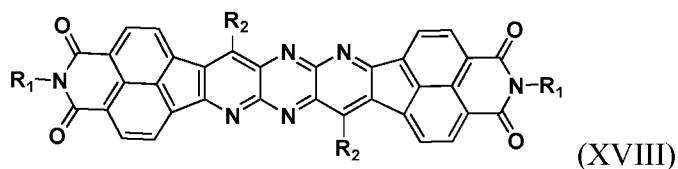
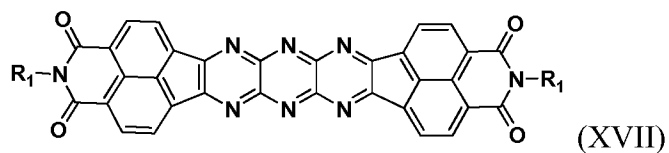
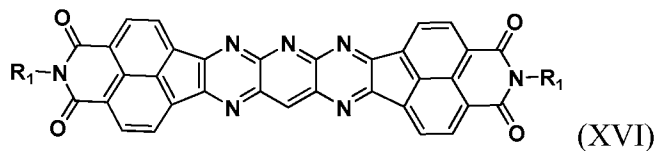
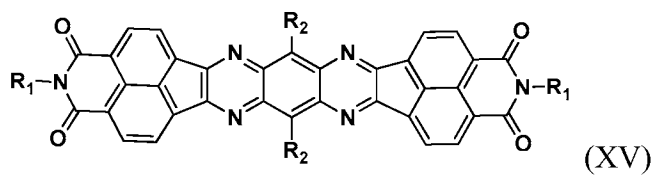
In a particular embodiment, the Type-A monomer is represented by formula (XI):



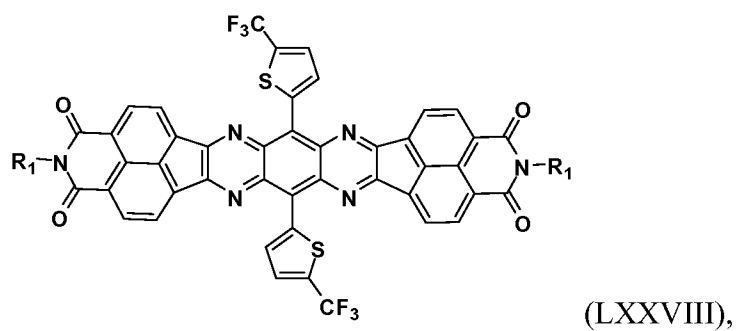
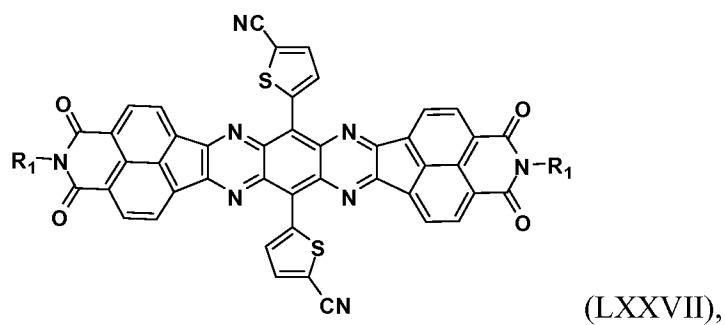
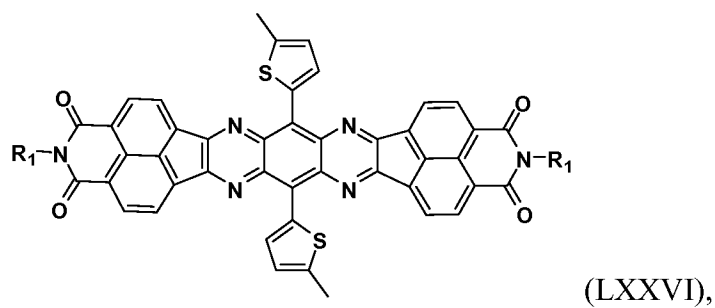
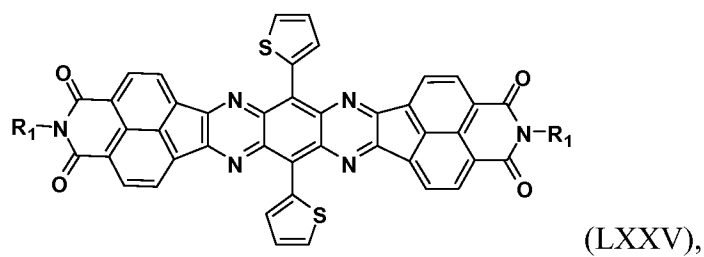
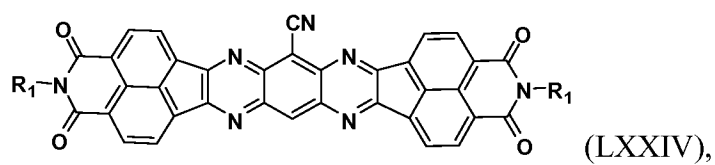
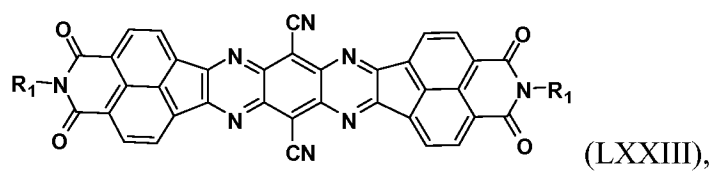
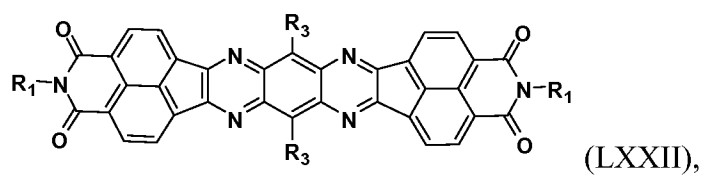
Many embodiments of the Type-A compound described herein relate to a compound selected from formulae (XII), (XIII) and (XIV):

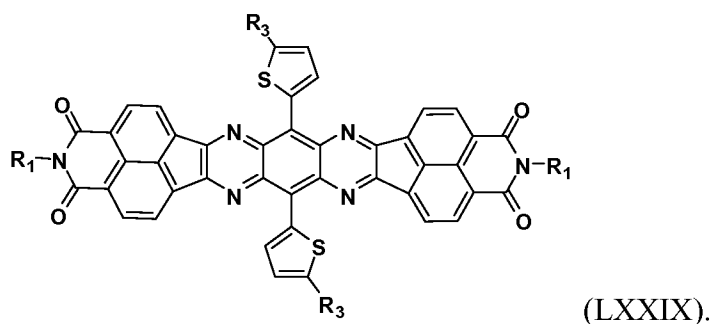


In some embodiments, the Type-A compound is selected from:

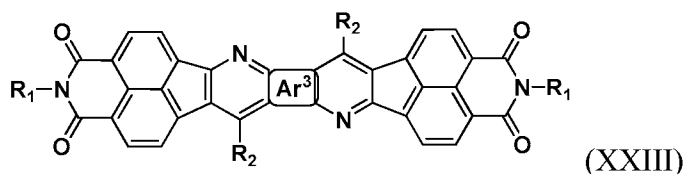
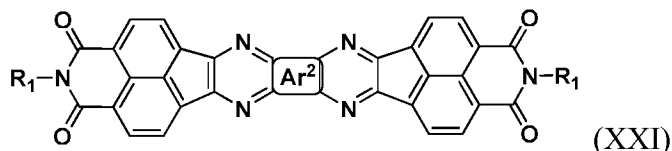


In some embodiments, the Type-A compound is selected from



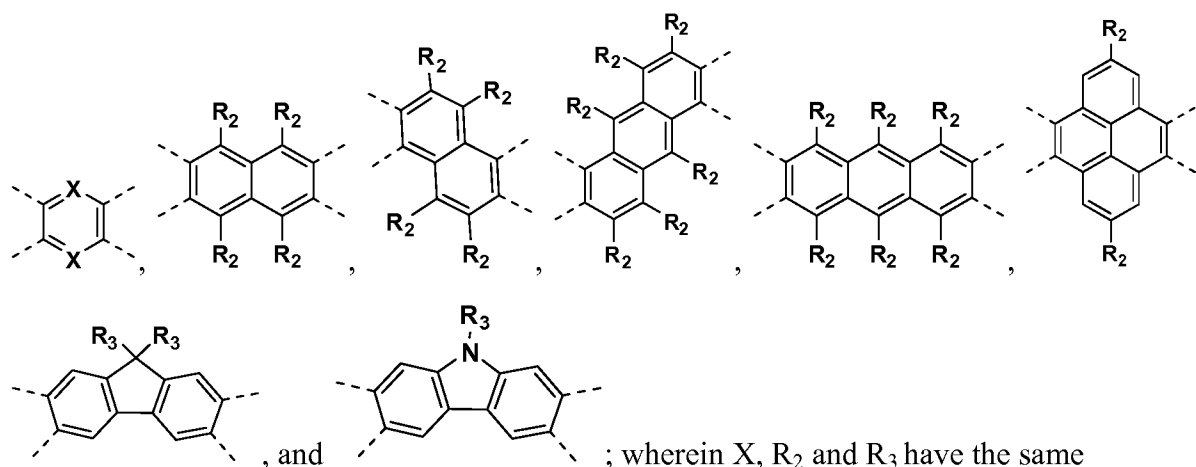


In some embodiments, the Type-A compound can be represented by:



wherein independently each of Ar^2 and Ar^3 comprises an optionally substituted aryl ring or an optionally substituted heteroaryl ring, or two or more of said rings fused together; and wherein R_1 and R_2 have the same definitions as previously described.

Ar^2 and Ar^3 can be independently selected from, for example, the following:

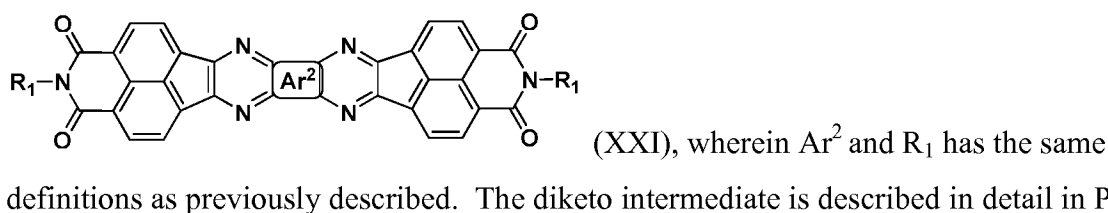
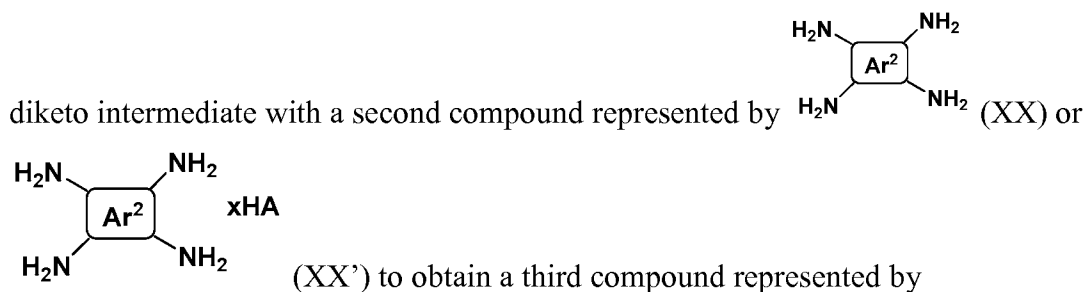


definitions as previously described.

The molecule weight of the Type-A compound can be, for example, 5,000 or less, or 3,000 or less, or 2,000 or less, or 1,000 or less. The lower end of the molecular weight can be, for example, at least 500.

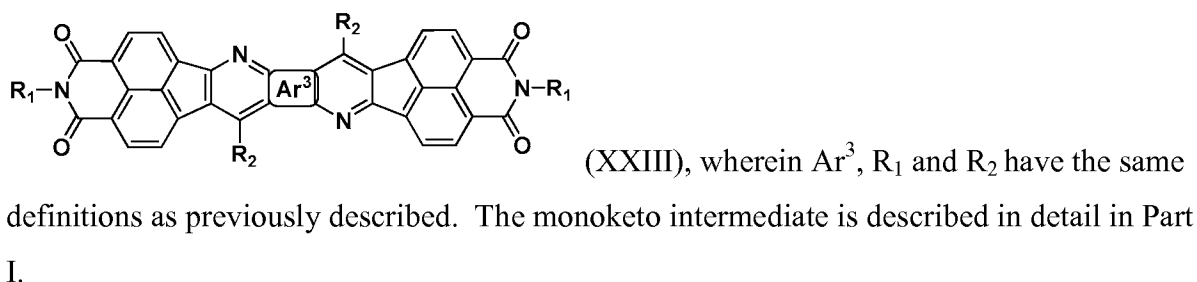
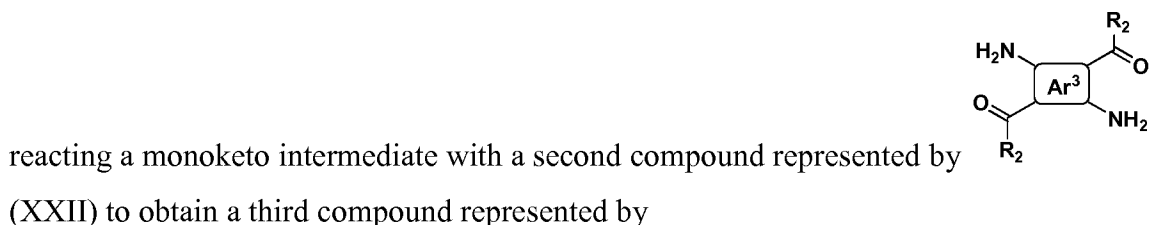
METHODS FOR MAKING TYPE-A COMPOUND

The Type-A compound described herein can be made by, for example, reacting a



In one embodiment, Ar² comprises a six-membered ring not fused with another ring, compound (XX) and compound (XX') comprise two pairs of ortho-positioned primary amine groups on said ring. In another embodiment, Ar² comprises two or more rings fused together, and compound (XX) and compound (XX') comprise two pairs of ortho-positioned primary amine groups, with each pair linked to a different ring. HA can be, for example, hydrochloric acid (HCl), hydrobromic acid (HBr), hydroiodic acid (HI) or acetic acid (HOAc), sulfuric acid (H₂SO₄) or phosphoric acid (H₃PO₄); x can 1, 2, 3, or 4.

Further, the Type-A compound described herein can be made by, for example,



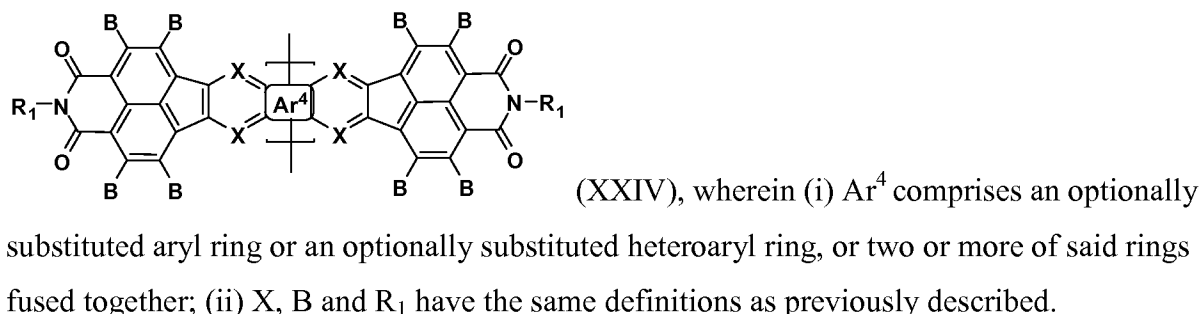
In one embodiment, Ar³ comprises a six-membered ring not fused with another ring, and compound (XXII) comprises two pairs of ortho-positioned groups on said ring, with each pair comprising a primary amine group and a ketone group. In another embodiment, Ar³ comprises two or more rings fused together, and compound (XXII) comprises two pairs of

ortho-positioned groups, with each pair comprising a primary amine group and a ketone group, wherein each pair is linked to a different ring.

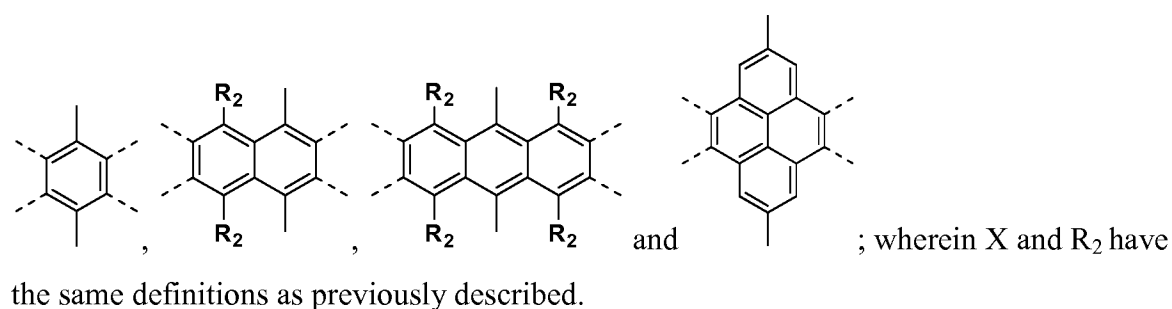
PART III – TYPE-A OLIGOMERS AND POLYMERS

STRUCTURE OF TYPE-A POLYMER

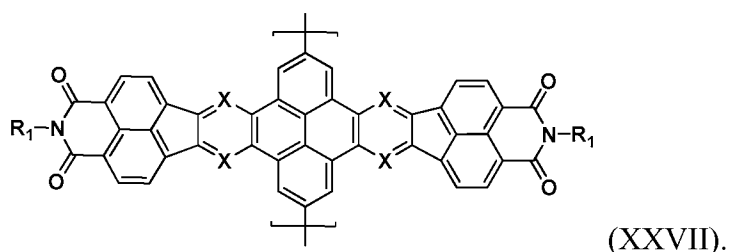
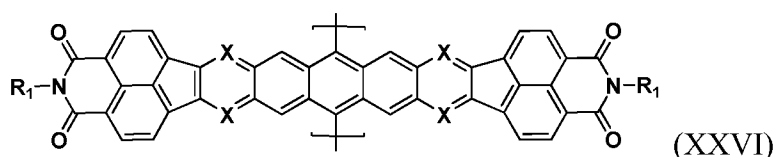
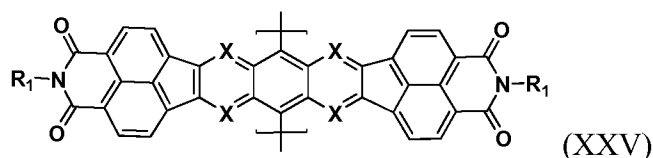
Many embodiments described herein relate to a Type-A polymer comprising one or more first repeating units RU1, wherein RU1 is represented by formula (XXIV):



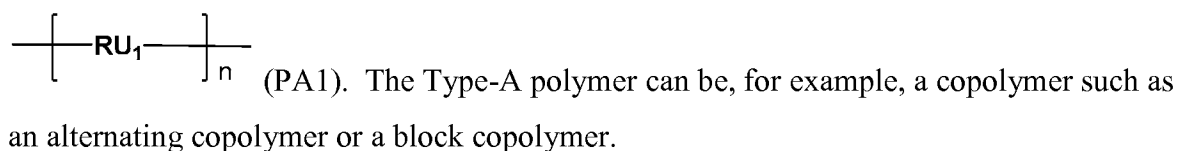
For example, in some embodiments Ar⁴ is represented by the following:



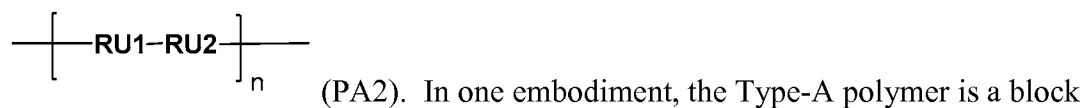
In some embodiments, the one or more first repeating units RU1 are independently selected from formulae (XXV), (XXVI) and (XXVII)



The Type-A polymer can be, for example, a homopolymer represented by

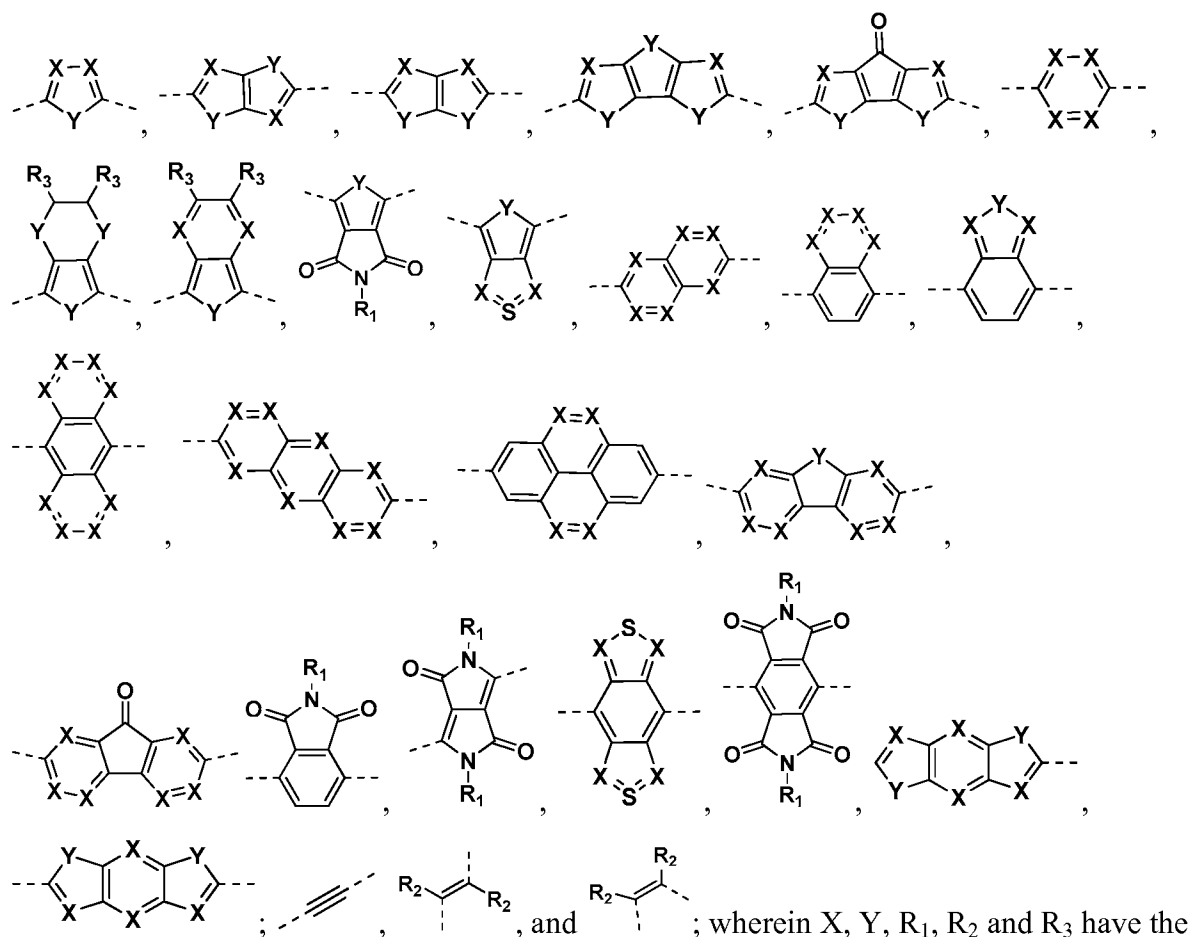


In one embodiment, the Type-A polymer is an alternating copolymer represented by



copolymer represented by $\left(\text{RU}_1 \right)_m \left(\text{RU}_2 \right)_n$ (PA3). The copolymer can comprise, for example, at least two different RU1 repeating units.

In some embodiments, the Type-A polymer is a copolymer comprising one or more second repeating units RU2 selected from

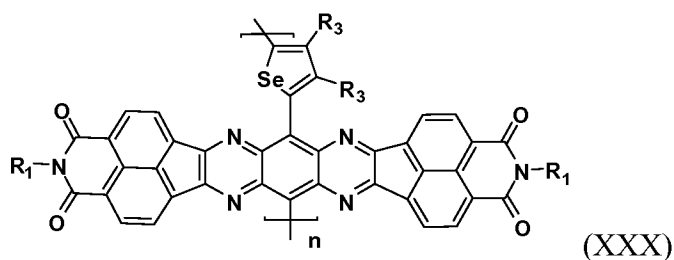
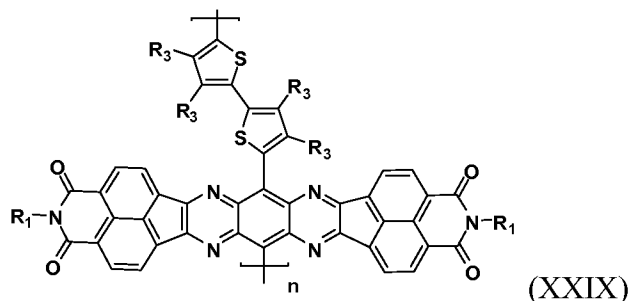
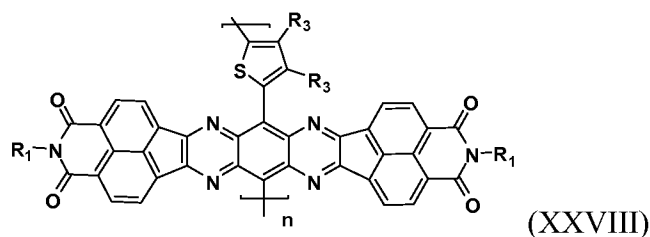


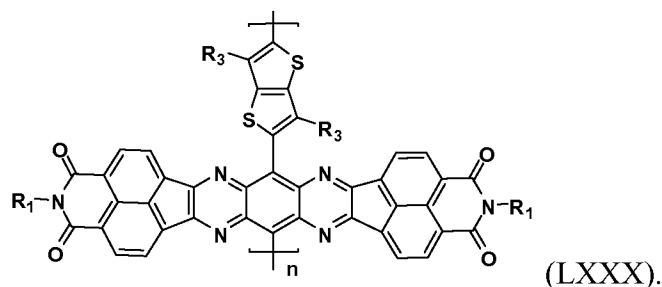
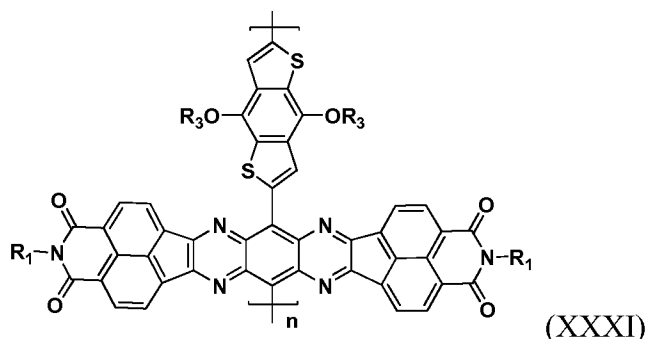
In some embodiments, RU2 comprises at least one thiophene, selenophene, or thiazole ring. In some embodiments, RU2 comprises at least two or at least three rings fused together, optionally with at least one of said rings being a thiophene, selenophene, or thiazole

ring. Particular embodiments of RU2 include optionally substituted thiophene, optionally substituted selenophene, optionally substituted thienothiophene and optionally substituted benzobisthiophene.

In one embodiment, the copolymer is an alternating copolymer, with the alternating section comprising at least one RU1 repeating unit and at least one RU2 repeating unit. In another embodiment, the copolymer is an alternating copolymer, with the alternating section comprising at least one RU1 repeating unit and at least two RU2 repeating units, said at least two RU2 units can be same or different. In a further embodiment, the copolymer is an alternating copolymer, with the alternating section comprising at least one RU1 repeating unit and at least three RU2 repeating units, said at least three RU2 units can be same or different. In an additional embodiment, the copolymer is an alternating copolymer, with the alternating section comprising at least two RU1 repeating units, said at least two RU1 units can be same or different.

In some embodiments, the Type-A polymer is selected from the following:

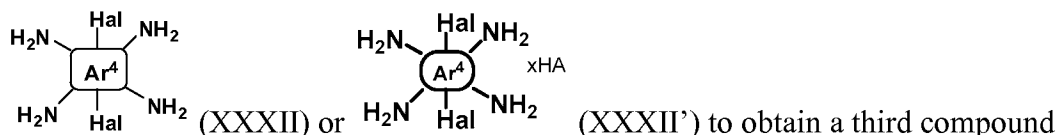




In these embodiments, n is a positive number, representing an average number of repeating units as known in the art of polymer chemistry. The weight average molecule weight (M_w) of the Type-A polymer can be, for example, 5,000 or more, or 10,000 or more, or 20,000 or more, or 50,000 or more, or 100,000 or more. The upper end of the molecular weight (M_w) range can be, for example, 2,000,000 or less, or 1,000,000 or less.

METHODS FOR MAKING TYPE-A POLYMER

The Type-A monomer for the Type-A polymer described herein can be made by, for example, reacting a diketo intermediate with a second compound represented by



represented by (XXXIII), wherein Ar^4 , R_1 , X , Hal and HA have the same definitions as previously described. The diketo intermediate is described in detail in Part I. In one particular embodiment, Hal consists of Br . In one particular embodiment, X consists of N .

In one embodiment, Ar^4 comprises a six-membered ring not fused with another ring, and compound (XXXII) or (XXXII') comprises two pairs of ortho-positioned primary amine groups on said ring. In another embodiment, Ar^4 comprises two or more rings fused together,

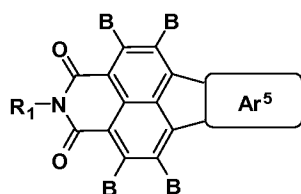
and compound (XXXII) or (XXXII') comprises two pairs of ortho-positioned primary amine groups, with each pair linked to a different ring.

From the Type-A monomer, the Type-A polymer can be made by, for example, Pd catalyzed coupling of the Type-A monomer with a di-tin derivative of RU2. The Type-A polymer can also be by Pd catalyzed coupling of any halogenated derivative of the RU1 with a di-tin derivative of RU2. Further, the halogenated derivative of the RU1 can also be used to make Type-A Compound by Pd catalyzed coupling with mono-tin derivative of RU2.

PART IV – TYPE-B COMPOUND

STRUCTURE OF TYPE-B COMPOUND

Many embodiments described herein relate to a Type-B compound represented by formula (XXXIV):

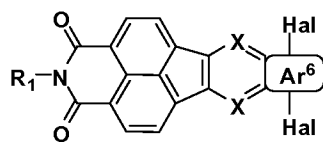


(XXXIV), wherein: (i) Ar⁵ comprises two or more rings fused together, each ring is an optionally substituted aryl ring or an optionally substituted heteroaryl ring; (ii) R₁ and B have the same definitions as previously described.

Ar⁵ can be, for example, a heteroaryl group comprising in the heteroaromatic ring(s) one or more N heteroatoms, or two or more N heteroatoms, or three or more N heteroatoms, or four or more N heteroatoms. Ar⁵ can be, for example, a heteroaryl group comprising one or more imine moieties, or two or more imine moieties, or three or more imine moieties, or four or more imine moieties.

Many embodiments of the Type-B compound described herein relate to a monomer (Type-B monomer) suitable for polymerization or copolymerization, wherein Ar⁵ comprises one or more, or two or more polymerizable groups. Polymerizable groups are known in the art and include, for example, halogen atoms such as Br.

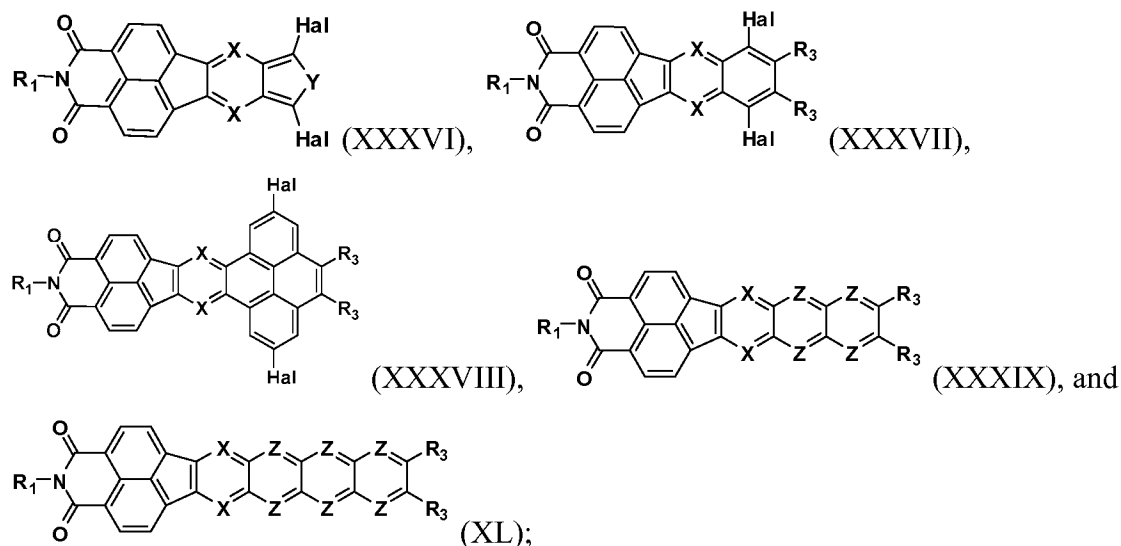
In some embodiments wherein B is hydrogen, the Type-B monomer compound is represented by formula (XXXV):



(XXXV), wherein: (i) Ar⁶ comprises an optionally substituted aryl

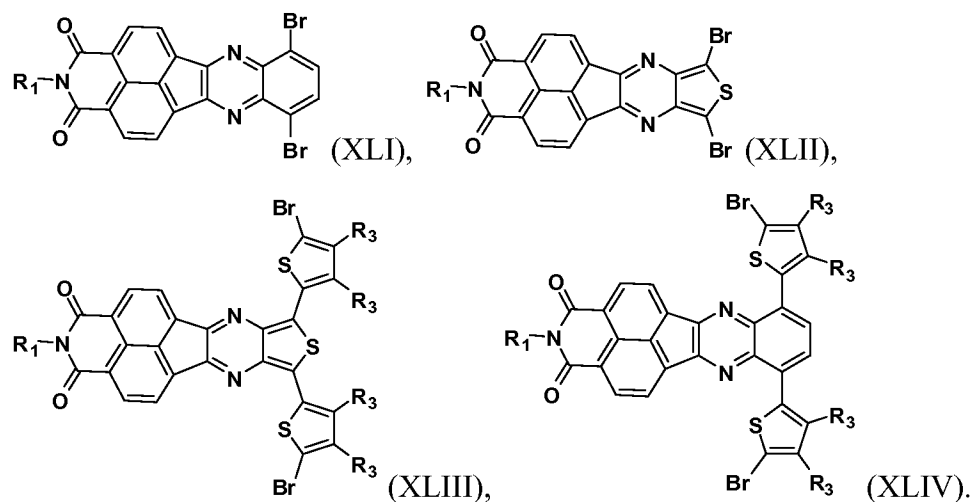
ring or an optionally substituted heteroaryl ring, or two or more of said rings fused together;
(ii) Hal and X have the same definitions as previously described.

In some embodiments, the Type-B monomer is selected from formulae (XXXVI), (XXXVII), (XXXVIII), (XXXIX) and (XL):

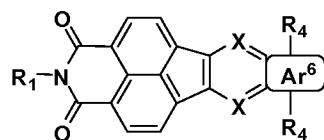


wherein: (i) Z at each occurrence is independently selected from X and ; (ii) Hal, X, Y and R₁ have the same definitions as previously described.

Particular embodiments of the Type-B monomer described herein include the following:



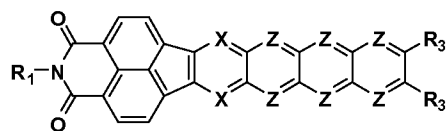
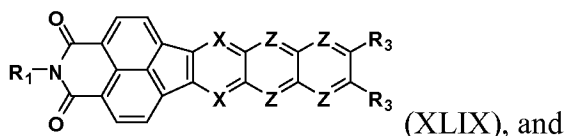
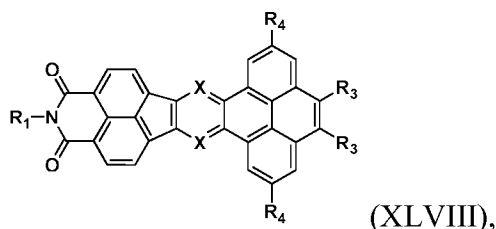
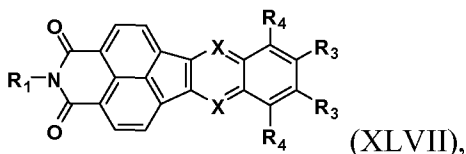
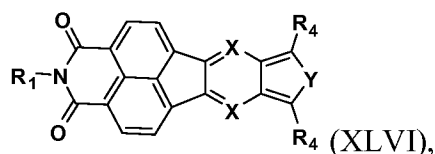
Many embodiments of the Type-B compound described herein relate to a compound represented by formula (XLV):



(XLV), wherein: (i) R_4 at each occurrence comprises an end group and one or more conjugation side groups linking the end group and the aromatic group that R_4 is attached to; (ii) Ar^6 , X, R_1 , and the end group and the conjugation side group have the same definitions as previously described.

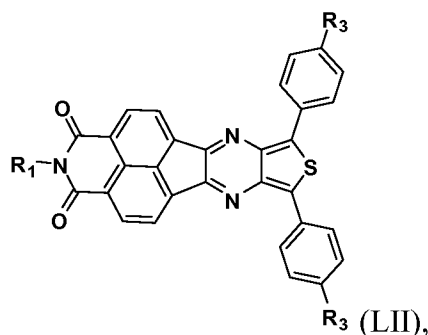
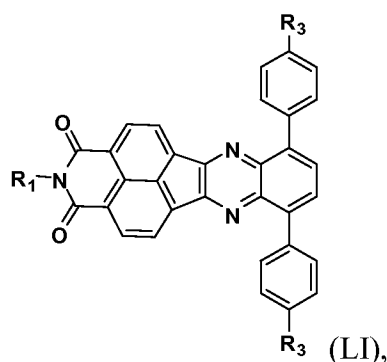
In some embodiments, R_4 can be a linear conjugated group comprising at least one, at least two or at least three conjugation side groups connected to each other with an end group attached. In some embodiments, the end group is selected from hydrogen, a linear or branched alkyl including $-CH_3$, and a linear or branched fluoroalkyl including $-CF_3$.

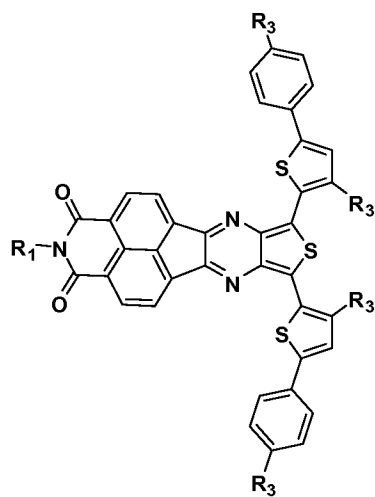
In some embodiments, the Type-B compound is selected from formulae (XLVI), (XLVII), (XLVIII), (XLIX) and (L):



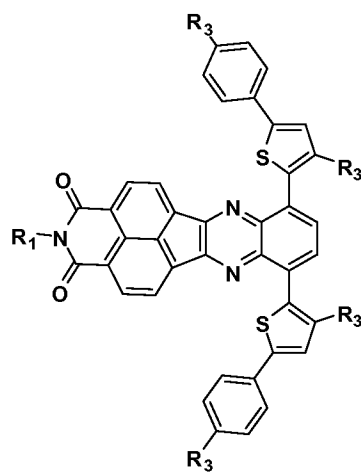
(L); wherein X, Y, Z, R_1 and R_4 have the same definitions as previously described.

Particular embodiments of the Type-B compound described herein include the following:

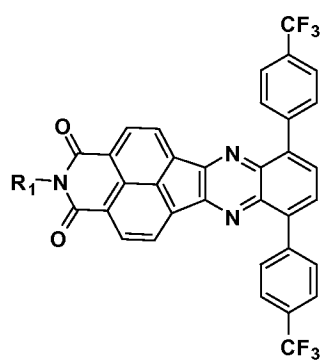




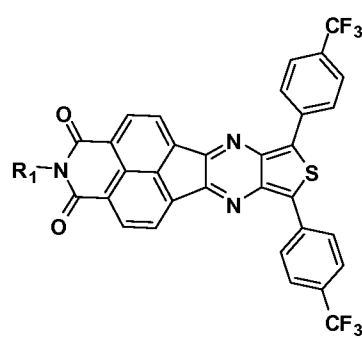
(LIII),



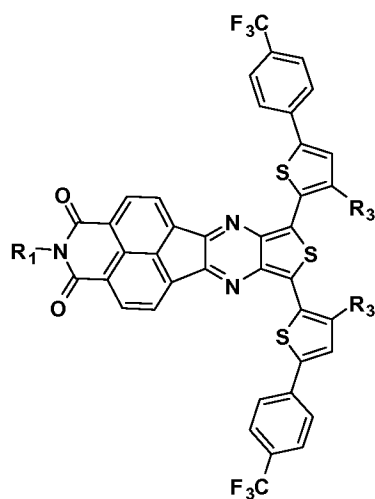
(LIV),



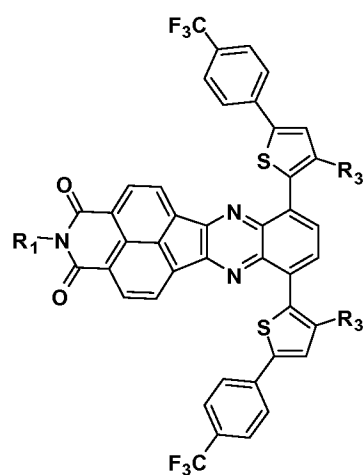
(LXXXI),



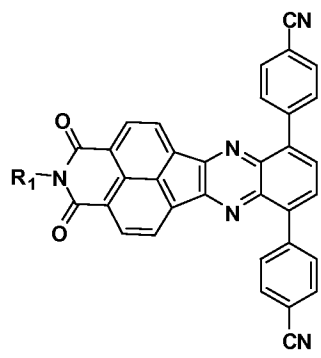
(LXXXII),



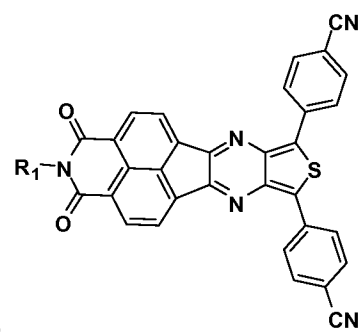
(LXXXIII),



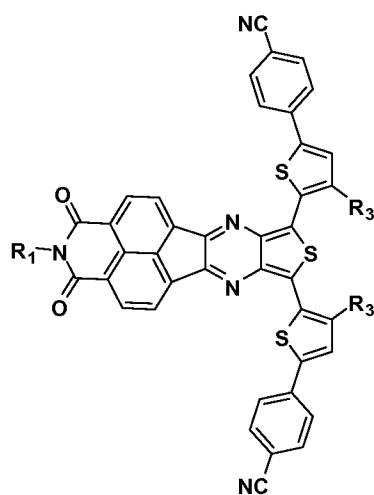
(LXXXIV),



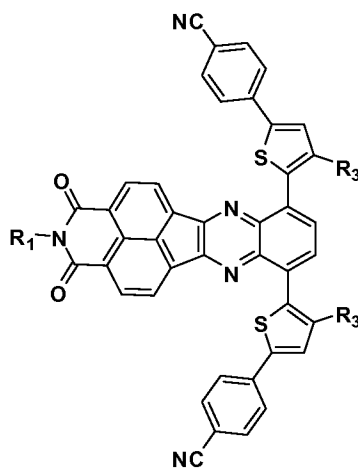
(LXXXV),



(LXXXVI),



(LXXXVII),

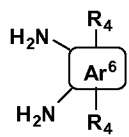


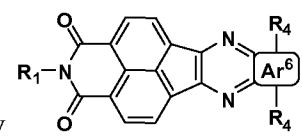
(LXXXVIII).

The molecule weight of the Type-B compound can be, for example, 5,000 or less, or 3,000 or less, or 2,000 or less, or 1,000 or less. The lower end of the molecular weight can be, for example, at least 500.

METHODS FOR MAKING TYPE-B COMPOUND

The Type-B compounds described herein can be made by, for example, reacting a

diketo intermediate with a second compound represented by  (LVII) to obtain a

third compound represented by  (LVIII), wherein Ar⁶, R₁ and R₄ have the same definitions as previously described. The diketo intermediate is described in detail in Part I.

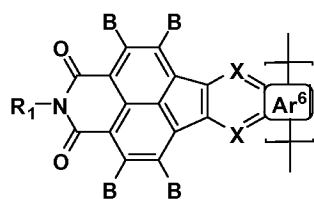
In one embodiment, Ar⁶ comprises a six-membered ring optionally fused with another ring, and compound (LVII) comprises one pair of ortho-positioned primary amine groups on said six-membered ring. In another embodiment, Ar⁶ comprises a five-membered ring, and compound (LVII) comprises one pair of ortho-positioned primary amine groups on said five-membered ring.

PART V – TYPE-B OLIGOMERS AND POLYMERS

STRUCTURE OF TYPE-B POLYMER

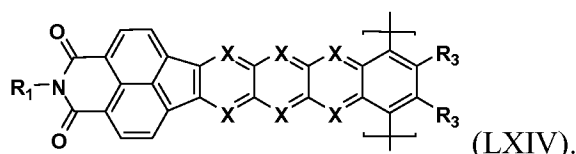
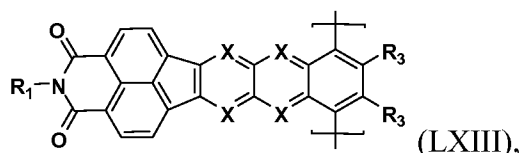
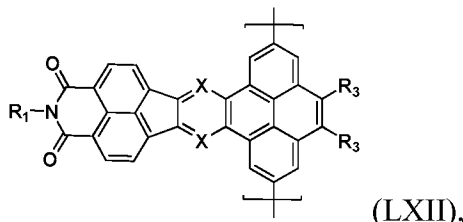
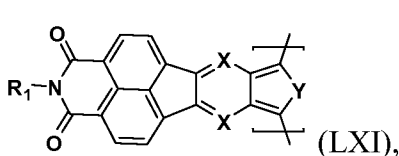
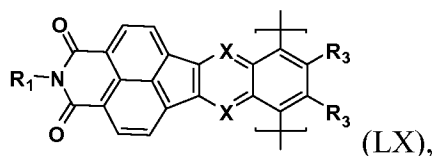
Many embodiments described herein relate to a Type-B polymer of structure comprising one or more first repeating units RU3, wherein RU3 is represented by formula

(LIX):

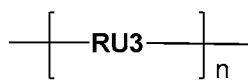


(LIX), wherein (i) Ar⁶ comprises an optionally substituted aryl ring or an optionally substituted heteroaryl ring, or two or more of said rings fused together; (ii) X, B and R₁ have the same definitions as previously described.

In some embodiments, the one or more first repeating units RU3 are selected from formulae (LX), (LXI), (LXII), (LXIII) and (LXIV)

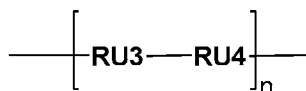


The Type-B polymer can be, for example, a homopolymer represented by

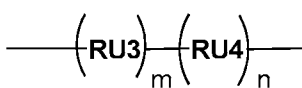


(PB1). The Type-B polymer can be, for example, a copolymer such as an alternating copolymer or a block copolymer. The copolymer can comprises, for example, at least two different RU3 repeating units.

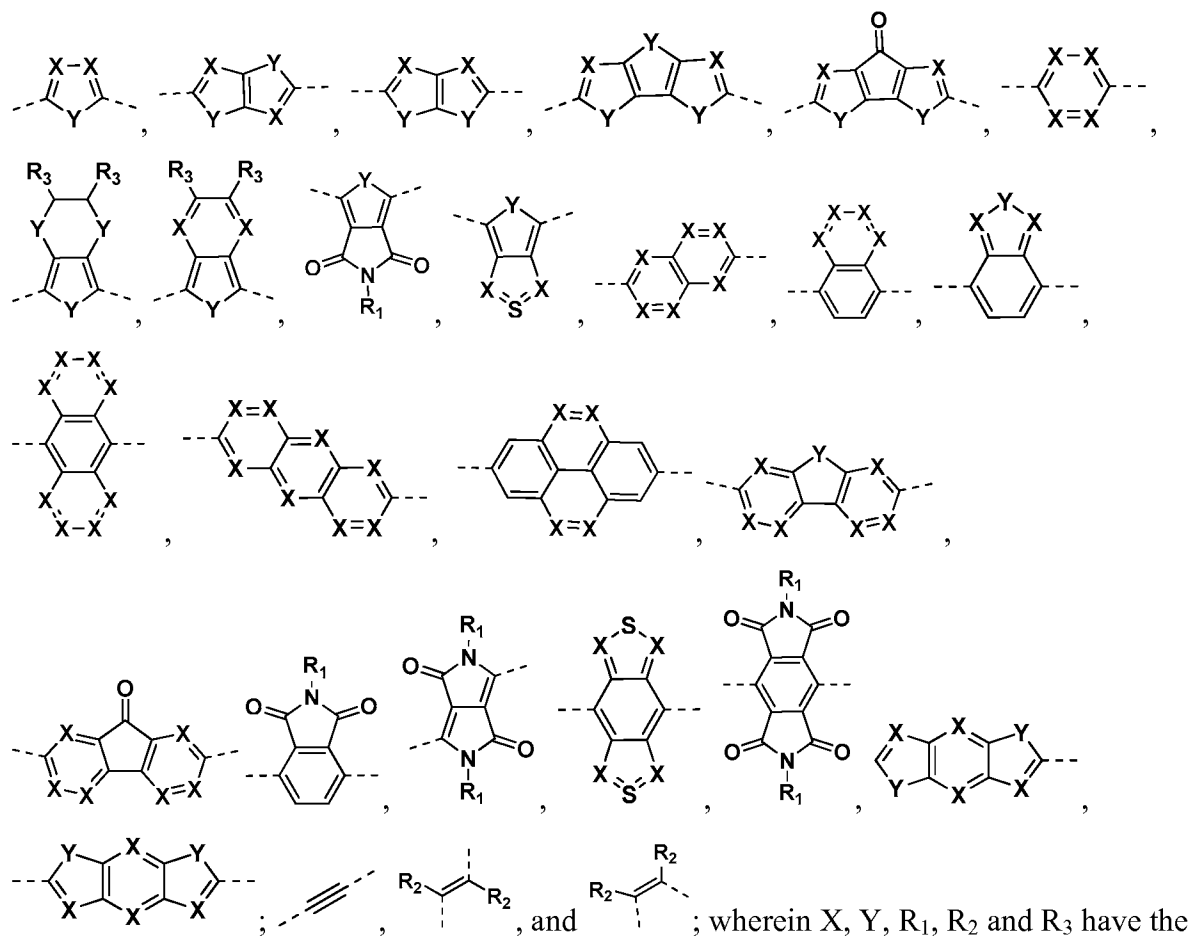
In one embodiment, the Type-B polymer is an alternating copolymer represented by



(PB2). In one embodiment, the Type-B polymer is a block

copolymer represented by  (PB3). The copolymer can comprises, for example, at least two different RU3 repeating units.

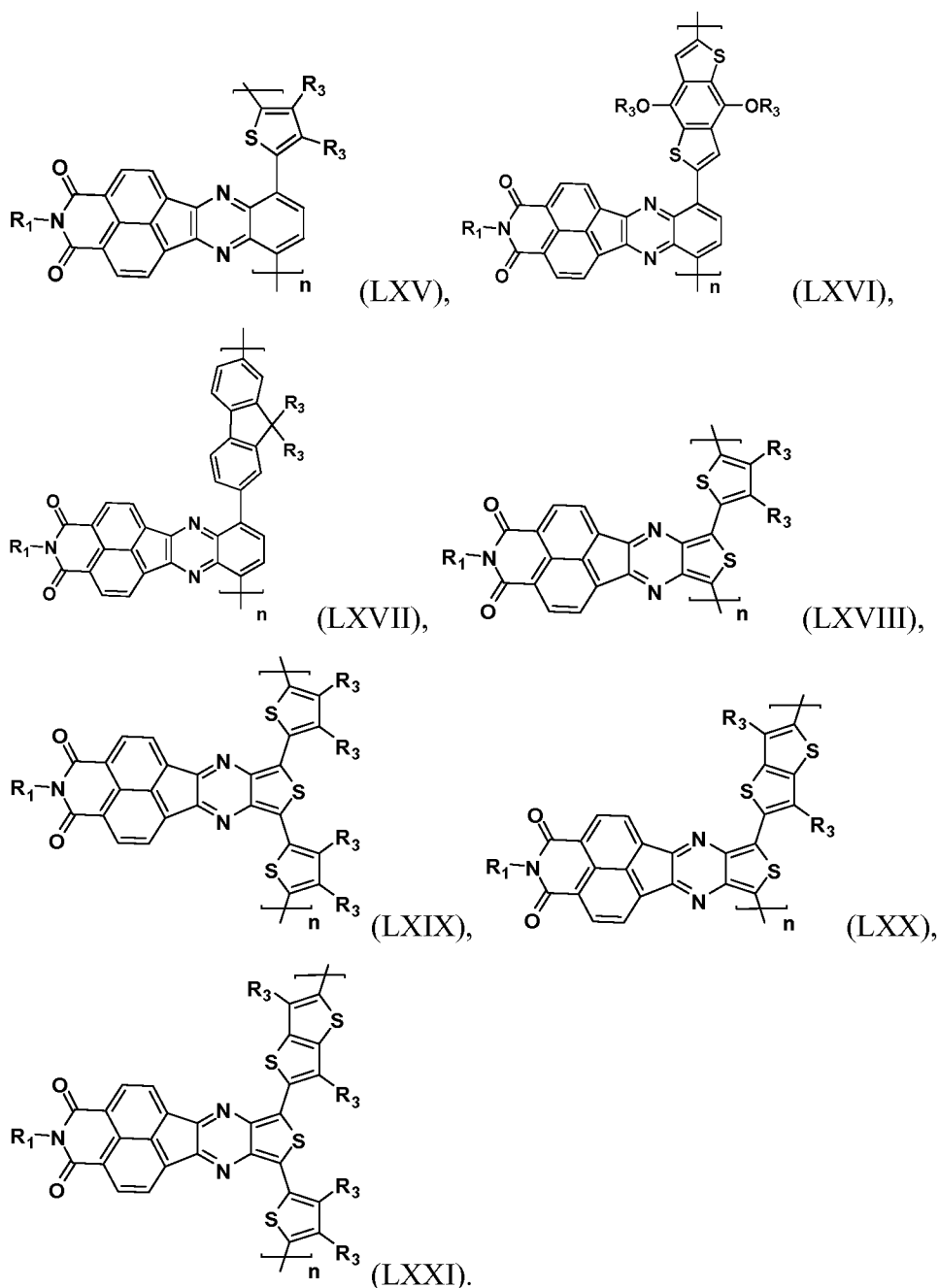
In some embodiments, the Type-B polymer is a copolymer comprising one or more second repeating units RU4 selected from



In some embodiments, RU4 comprises at least one thiophene or selenophene ring. In some embodiments, RU4 comprises at least two or at least three rings fused together, optionally with at least one of said rings being a thiophene or selenophene ring. Particular embodiments of RU4 include optionally substituted thiophene, optionally substituted selenophene, optionally substituted benzobisthiophene, and optionally substituted fluorene.

In one embodiment, the copolymer is an alternating copolymer, with the alternating section comprising at least one RU3 repeating unit and at least one RU4 repeating unit. In another embodiment, the copolymer is an alternating copolymer, with the alternating section comprising at least one RU3 repeating unit and at least two RU4 repeating units, said at least two RU4 units can be same or different. In a further embodiment, the copolymer is an alternating copolymer, with the alternating section comprising at least one RU3 repeating unit and at least three RU4 repeating units, said at least three RU4 units can be same or different. In an additional embodiment, the copolymer is an alternating copolymer, with the alternating section comprising at least two RU3 repeating units, said at least two RU3 units can be same or different.

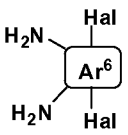
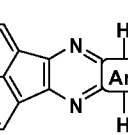
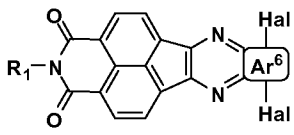
In some embodiments, the Type-B polymer is selected from the following



The weight average molecule weight (M_w) of the Type-B polymer can be, for example, 5,000 or more, or 10,000 or more, or 20,000 or more, or 50,000 or more, or 100,000 or more. The upper end of the molecular weight (M_w) range can be, for example, 2,000,000 or less, or 1,000,000 or less.

METHODS FOR MAKING TYPE-B POLYMER

The Type-B monomer for the Type-B polymer described herein can be made by, for

example, reacting a diketo intermediate with a second compound represented by  (LV) or  (LV') to obtain a third compound represented by  (LVI), wherein Ar⁶, R₁, Hal and HA have the same definitions as previously described. The diketo intermediate is described in detail in Part I. In some embodiments, x is 1 or 2. In a particular embodiment, Hal consists of Br.

In one embodiment, Ar⁶ comprises a six-membered ring optionally fused with another ring, and compound (LV) comprises one pair of ortho-positioned primary amine groups on said six-membered ring. In another embodiment, Ar⁶ comprises a five-membered ring optionally fused with another ring, and compound (LV) comprises one pair of ortho-positioned primary amine groups on said five-membered ring.

From the Type-B monomer, the Type-B polymer can be made by, for example, Pd catalyzed coupling of the Type-B monomer with a di-tin derivative of RU4. The Type-A polymer can also be by Pd catalyzed coupling of any halogenated derivative of the RU3 with a di-tin derivative of RU4. Further, the halogenated derivative of the RU3 can also be used to make Type-B Compound by Pd catalyzed coupling with mono-tin derivative of RU4.

PART VI - DEVICES

ORGANIC ELECTRONIC DEVICES

The compounds and polymers described herein have advantageous electronic structures and solid morphologies for applications in organic electronic and optoelectronic devices. The electronic structures and the solid morphologies of the disclosed materials can also be fine tuned through variation of the chemical structures. Therefore, also provided are organic electronic devices and optoelectronic devices comprising one or more of the disclosed materials or formulations described herein such as organic field effect transistors (OFETs), thin film transistors (TFTs), logic circuits, integrated circuits, radio frequency identification tags (RFID), flat displays, organic photovoltaics (OPVs), solar cells, light emitting diodes (LEDs), light emitting transistor, etc. Also provided are the uses of the

materials described herein as charge transporting, semiconducting, photoconducting, and/or light emitting components in electronic or optoelectronic devices.

In such devices, the disclosed materials are generally present as a thin film. In some embodiments, the disclosed materials have good solubility in common organic solvents; therefore they can be processed using solution processing techniques including spin coating, casting, dip coating, inkjet printing, screen printing, spray coating, doctor blade coating, roll coating, bar coating, die coating and dispense methods, and may also be employed in thermal evaporation or solution processes for making organic electronic devices. The solution can be prepared by dissolving the disclosed materials into a solvent or mixed solvents such as chloroform, dichloromethane, toluene, chlorobenzene, dichlorobenzene, trichlorobenzene, xylene, trifluoroacetic acid, formic acid, acetic acid, etc. at room temperature or at high temperature. The thickness of the thin films is not particularly specified and can be adjusted to fit the need of different applications.

TRANSISTORS

Many embodiments of the devices described herein relate to a field-effect transistor comprising at least one charge transporting material selected from Type-A compound, Type-A polymer, Type-B compound and Type-B polymer.

In some embodiment, the field-effect transistor comprises a thin-film of the charge transporting material described herein. The thin film can be deposited from a solution of the charge transporting material. The thin-film can be fabricated by spin coating. The thin-film can be fabricated by vacuum vapor deposition.

The field-effect transistor can be a n-channel transistor, or an ambipolar transistor. The electron mobility of the field-effect transistor can be, for example, $1 \times 10^{-5} \text{ cm}^2/\text{Vs}$ or higher, or $1 \times 10^{-4} \text{ cm}^2/\text{Vs}$ or higher, or $1 \times 10^{-3} \text{ cm}^2/\text{Vs}$ or higher, or $1 \times 10^{-2} \text{ cm}^2/\text{Vs}$ or higher, or $0.1 \text{ cm}^2/\text{Vs}$ or higher. The on/off current ratio of the field-effect transistor can be, for example, at least 10^4 , or at least 10^5 , or at least 10^6 , or about 10^4 - 10^7 , or about 10^5 - 10^6 .

The organic thin film transistors described herein typically have a configuration such that a semiconductor layer including the compounds and/or polymers described herein is formed therein while also contacting the source electrode, drain electrode and insulating layer of the transistor.

The organic thin film transistor is typically thermally annealed. Annealing is performed while the film is set on a substrate, and is believed (without wishing to be bound by theory) to allow for at least partial self-ordering and/or π -stacking of the compounds

and/or polymers to occur in the solid state. The annealing temperature is determined depending on the property of the material, but is preferably from room temperature to 300 °C, and more preferably from 50 to 300 °C. In many embodiments, thermal annealing is carried out at least 150 °C, or preferably above 170 °C, or above 200 °C. When the annealing temperature is too low, the organic solvent remaining in the organic film cannot be well removed therefrom. In contrast, when the annealing temperature is too high, the organic film can be thermally decomposed. Annealing is preferably performed in a vacuum, or under nitrogen, argon or air atmosphere. In some embodiments annealing is performed in an atmosphere including a vapor of an organic solvent capable of dissolving the material so that the molecular motion of the material is accelerated, and thereby a good organic thin film can be prepared. The annealing time is properly determined depending on the aggregation speed of the material.

An insulating (dielectric) layer is used in the organic thin film transistors comprising the materials described herein, situated between the gate electrode and the organic thin film comprising the material. Various insulating materials can be used for the insulating layer. Specific examples of the insulating materials include inorganic insulating materials such as silicon oxide, silicon nitride, aluminum oxide, aluminum nitride, titanium oxide, tantalum oxide, tin oxide, vanadium oxide, barium strontium titanate, barium zirconate titanate, lead zirconium titanate, lead lanthanum titanate, strontium titanate, barium titanate, barium magnesium fluoride, bismuth tantalate niobate, hafnium oxide, and trioxide yttrium; organic insulating materials such as polymer materials, e.g., polyimide, polyvinyl alcohol, polyvinyl phenol, polystyrene, polyester, polyethylene, polyphenylene sulfide, unsubstituted or halogen-atom substituted polyparaxylylene, polyacrylonitrile, and cyanoethylpullulan; etc. These materials can be used alone or in combination. Among these materials, materials having a high dielectric constant and a low conductivity are preferably used.

Suitable methods for forming such an insulating layer include dry processes such as CVD methods, plasma CVD methods, plasma polymerization methods, and vapor deposition methods; wet processes such as spray coating methods, spin coating methods, dip coating methods, inkjet coating methods, cast coating methods, blade coating methods, and bar coating methods; etc.

In order to improve the adhesion between the insulating layer and organic semiconductor layer, to promote charge transport, and to reduce the gate voltage and leak current, an organic thin film (intermediate layer) can be employed between the insulating layer and organic semiconductor layer. The materials for use in the intermediate layer are not

particularly limited as long as the materials do not chemically affect the properties of the organic semiconductor layer, and for example, molecular films of organic materials, and thin films of polymers can be used therefor. Specific examples of the materials for use in preparing the molecular films include coupling agents such as octadecyltrichlorosilane, octyltrichlorosilane, octyltrimethoxysilane, hexamethyldisilazane (HMDS), and octadecylphosphonic acid. Specific examples of the polymers for use in preparing the polymer films include the polymers mentioned above for use in the insulating layer. Such polymer films can serve as the insulating layer as well as the intermediate layer.

The materials of the electrodes (such as gate electrodes, source electrodes and drain electrodes) of the organic thin film transistor described herein are not particularly limited as long as the materials are electrically conductive. Specific examples of the materials include metals such as platinum, gold, silver, nickel, chromium, copper, iron, tin, antimony, lead, tantalum, indium, aluminum, zinc, tungsten, titanium, calcium, and magnesium; alloys of these metals; electrically conductive metal oxides such as indium tin oxide (ITO); inorganic or organic semiconductors, whose electroconductivity is improved by doping or the like, such as silicon single crystal, polysilicon, amorphous silicon, germanium, graphite, carbon nanotube, polyacetylene, polyparaphenylene, polythiophene, polypyrrole, polyaniline, polythienylenevinylene, polyparaphenylenevinylene, and complexes of polyethylenedioxythiophene (PEDOT) and polystyrene sulfonic acid.

SOLAR CELLS

Solar cells described herein can be fabricated by, for example, first spin-coating a buffer layer, such as a PEDOT:PSS buffer layer, on top of an electrode and substrate, such as ITO-coated glass substrates (e.g., 10 Ω /sq, Shanghai B. Tree Tech. Consult Co., Ltd., Shanghai, China). Spin coating is known in the art and the spin coating can be adapted to the needs. One example is to spin coat at 1500 rpm for 60 s and dry at 150°C for 10 min under vacuum. The thickness of the buffer layer (e.g., PEDOT) can be, for example, around 10 nm to 100 nm, or about 40 nm.

The active layer of the solar cells comprising the compounds and/or polymers described herein can comprise a mixed “heterojunction” active layer that is a phase separated blend of the materials described herein and an electron donor material. The electron donor materials can be a variety of organic materials (small molecules, oligomers, polymers, or polymer composites) that have a LUMO energy level that is at least about 0.2 to 0.6 eV more positive than the LUMO energy level of the compounds described herein, and a HOMO

energy level that is more positive than the HOMO energy level of the compounds described herein.

In many embodiments of the solar cells described herein, a composite or composition comprising a solution or dispersion of one or more of the material described herein and one or more donor materials (for example P3HT or poly[(4,4'-bis(3-(2-ethyl-hexyl)dithieno[3,2-b:2',3'-d]silole)-2,6-diyl-alt-(2,5-bis(3-(2-ethyl-hexyl)thiophen-2yl)thiazolo[5,4-d]thiazole)] (PSEHTT, see CN102782011A, EP2493960A1, US20120273732, and Subramaniyan *et al.*, *Adv. Energy Mater.* **2011**, *1*, 854-860.) is spin-coated on top of the PEDOT:PSS layer to form a layer comprising the one or more material described herein and one or more electron donating materials.

The active layer of the solar cells comprising the compounds and/or polymers described herein can comprise a mixed "heterojunction" active layer that is a phase separated blend of the materials described herein and an electron acceptor material. The electron acceptor material can comprise a variety of organic materials (small molecules, oligomers, polymers, or polymers) that have a LUMO energy level that is at least about 0.2 to 0.6 eV more negative than the LUMO energy level of the polymers described herein, and a HOMO energy level that is more negative than the HOMO energy level of the polymers described herein. In many embodiments, the electron acceptor material can be a fullerene or a modified fullerene (e.g., C₆₁-phenyl-butyric acid methyl ester, PC₆₁BM, or C₇₁-phenyl-butyric acid methyl ester, PC₇₁BM). In other embodiments, the electron acceptor material can be an electron accepting semiconducting organic small molecule, oligomer, or polymer having appropriate LUMO and HOMO energies (at least about 0.2-0.6 eV more negative than the LUMO energy level and a more negative HOMO energy level than the HOMO energy level of the polymers described herein). Examples of such electron acceptor materials can include small molecules, oligomers, polymers, or polymers having highly electron deficient functional groups, such as for example naphthalene diimide, perylene diimide, rylene, phthalimide, and related derivatives comprising electron accepting groups.

In some embodiments of the solar cells described herein, a composition comprising a solution or dispersion of one or more of materials described herein and one or more acceptor materials (for example fullerene derivatives) is spin-coated on top of the buffer layer, such as PEDOT:PSS layer, for example at a suitable speed as known in the art, e.g., at 1000 rpm for 30 seconds, to form a layer comprising the one or more materials described herein and one or more electron accepting materials. In some embodiments, the solution or dispersion is

applied using a hot solvent, and dried under vacuum immediately after the deposition the polymers.

The coated device precursor can then be annealed, for example on a hot plate at in a glove box, to form the active layer. The active layer can also be spin-coated in air and dried in a vacuum oven without thermal annealing. The solvents for dissolving the mixture of the material described herein and the electron donors, or the mixture of the material described herein and the electron acceptors, can be chloroform, chlorobenzene, 1,2-dichlorobenzene, etc. The solvents for the blend can be a single solvent such as chloroform, chlorobenzene, 1,2-dichlorobenzene or a mixture of two or three different solvents, the second (third) solvent can be 1,8-diiodooctane, 1,8-dibromooctane, 1,8-octanedithiol, etc. Optionally, the solvents can be heated so as to increase the solubility of the material described herein and/or the electron donors or the electron acceptors, as an aid to film formation.

Thermal annealing is believed to induce at least partial phase separation between the material described herein and the electron donors, or between the material described herein and the electron acceptors, forming the “heterojunctions” on the nanometer scale that are believed to be the site of light-induced charge separation.

After cooling down, the solar cell precursors comprising the active material-coated substrates can be taken out of the glove box and loaded in a thermal evaporator (e.g., BOC Edwards, 306) for the deposition of the cathode. The cathode consisting of, for example, 1.0 nm LiF and 80 nm aluminum layers, can be sequentially deposited through a shadow mask on top of the active layers in a vacuum of, for example, 8×10^{-7} torr. Each substrate can contain, for example, a plurality of (e.g. 5) solar cells with an active area of, for example, 4 mm².

Solar cells described herein can also be fabricated by, for example, first spin-coating a buffer layer, such as a ZnO, on top of an electrode and substrate, such as ITO-coated glass substrates (e.g., 10 Ω /sq, Shanghai B. Tree Tech. Consult Co., Ltd., Shanghai, China). Spin coating is known in the art and the spin coating can be adapted to the needs. One example is to spin coat at 1500 rpm for 60 s and dry at 200°C for 60 min in air. The thickness of the buffer layer (e.g., ZnO) can be, for example, around 10 nm to 100 nm, or about 30 nm.

The active layer of the solar cells comprising the compounds and/or polymers described herein can comprise a mixed “heterojunction” active layer that is a phase separated blend of the materials described herein and an electron donor material. The electron donor materials can be a variety of organic materials (small molecules, oligomers, polymers, or polymer composites) that have a LUMO energy level that is at least about 0.2 to 0.6 eV more

positive than the LUMO energy level of the compounds described herein, and a HOMO energy level that is more positive than the HOMO energy level of the compounds described herein.

In many embodiments of the solar cells described herein, a composite or composition comprising a solution or dispersion of one or more of the materials described herein and one or more donor materials (for example P3HT or poly[(4,4'-bis(3-(2-ethyl-hexyl)dithieno[3,2-*b*:2',3'-*d*]silole)-2,6-diyl-alt-(2,5-bis(3-(2-ethyl-hexyl)thiophen-2yl)thiazolo[5,4-*d*]thiazole)] (PSEHTT, see CN102782011A, EP2493960A1, US20120273732, and Subramaniyan *et al.*, *Adv. Energy Mater.* **2011**, *1*, 854-860.) is spin-coated on top of the ZnO layer to form a layer comprising the one or more material described herein and one or more electron donating materials.

The active layer of the solar cells comprising the compounds and/or polymers described herein can comprise a mixed "heterojunction" active layer that is a phase separated blend of the materials described herein and an electron acceptor material. The electron acceptor material can comprise a variety of organic materials (small molecules, oligomers, polymers, or polymers) that have a LUMO energy level that is at least about 0.2 to 0.6 eV more negative than the LUMO energy level of the polymers described herein, and a HOMO energy level that is more negative than the HOMO energy level of the polymers described herein. In many embodiments, the electron acceptor material can be a fullerene or a modified fullerene (e.g., C₆₁-phenyl-butyric acid methyl ester, PC₆₁BM, or C₇₁-phenyl-butyric acid methyl ester, PC₇₁BM). In other embodiments, the electron acceptor material can be an electron accepting semiconducting organic small molecule, oligomer, or polymer having appropriate LUMO and HOMO energies (at least about 0.2-0.6 eV more negative than the LUMO energy level and a more negative HOMO energy level than the HOMO energy level of the polymers described herein). Examples of such electron acceptor materials can include small molecules, oligomers, polymers, or polymers having highly electron deficient functional groups, such as for example naphthalene diimide, perylene diimide, rylene, phthalimide, and related derivatives comprising electron accepting groups.

In some embodiments of the solar cells described herein, a composition comprising a solution or dispersion of one or more of materials described herein and one or more acceptor materials (for example fullerene derivatives) is spin-coated on top of the buffer layer, such as ZnO layer, for example at a suitable speed as known in the art, e.g., at 1000 rpm for 30 seconds, to form a layer comprising the one or more materials described herein and one or more electron accepting materials. In some embodiments, the solution or dispersion is

applied using a hot solvent, and dried under vacuum immediately after the deposition the polymers.

The coated device precursor can then be annealed, for example on a hot plate in a glove box, to form the active layer. The active layer can also be spin-coated in air and dried in a vacuum oven without thermal annealing. The solvents for dissolving the mixture of the material described herein and the electron donors, or the mixture of the material described herein and the electron acceptors, can be chloroform, chlorobenzene, 1,2-dichlorobenzene, etc. The solvents for the blend can be a single solvent such as chloroform, chlorobenzene, 1,2-dichlorobenzene or a mixture of two or three different solvents, the second (third) solvent can be 1,8-diiodooctane, 1,8-dibromooctane, 1,8-octanedithiol, etc. Optionally, the solvents can be heated so as to increase the solubility of the material described herein and/or the electron donors or the electron acceptors, as an aid to film formation.

Thermal annealing is believed to induce at least partial phase separation between the material described herein and the electron donors, or between the material described herein and the electron acceptors, forming the “heterojunctions” on the nanometer scale that are believed to be the site of light-induced charge separation.

After cooling down, the solar cell precursors comprising the active material-coated substrates can be taken out of the glove box and loaded in a thermal evaporator (e.g., BOC Edwards, 306) for the deposition of the anode. The anode consisting of, for example, 10.0 nm MoO₃ and 100 nm Ag, can be sequentially deposited through a shadow mask on top of the active layers in a vacuum of, for example, 8×10^{-7} torr. Each substrate can contain, for example, a plurality of (e.g. 5) solar cells with an active area of, for example, 4 mm².

WORKING EXAMPLES

PART I

EXAMPLE 1A – Synthesis of Diketone Intermediates

Materials and Methods:

Unless stated otherwise, starting materials were purchased and used without further purification.

^1H NMR and ^{13}C NMR spectra were recorded on a Bruker AV500 at 500 MHz using either deuteriochloroform (CDCl_3) or deuteriotrifluoroacetic acid (CF_3COOD) as the solvent.

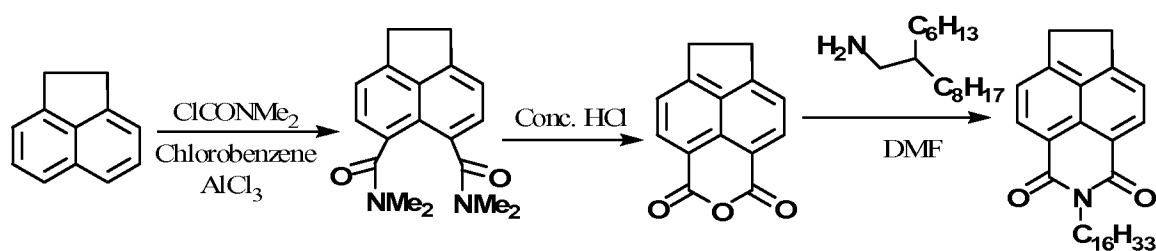
Mass spectra were obtained from Bruker AutoFlex II Matrix-Assisted LASER Desorption Ionization - Time of Flight Mass Spectrometer (MALDI-TOF) using benzo[α]pyrene as a matrix recorded in a (+)-reflector mode.

Thermogravimetric analysis of the molecules was conducted on a TA Instruments model Q50TGA. A heating rate of $10^\circ\text{C}/\text{min}$ under a flow of N_2 was used with runs conducted from room temperature to 800°C .

Cyclic voltammetry was done on an EG&G Princeton Applied Research potentiostat/galvanostat (model 273A). Data were analyzed by using a Model 270 Electrochemical Analysis System Software on a PC computer. A three-electrode cell was used, using platinum wire electrodes as both counter and working electrode. Silver/silver ion (Ag in 0.1 M AgNO_3 solution, Bioanalytical System, Inc.) was used as a reference electrode. Ferrocene/ferrocenium (Fc/Fc^+) was used as an internal standard. All solutions were purged with N_2 for 20 min before each experiment.

UV-Vis absorption spectra were collected on a Perkin-Elmer model Lambda 900 UV/Vis/near-IR spectrophotometer.

The photoluminescence (PL) emission spectra were obtained with a Photon Technology International (PTI) Inc. model QM2001-4 spectrofluorimeter.



Synthesis of N5,N5,N6,N6-tetramethyl-1,2-dihydroacenaphthylene-5,6-dicarboxamide (Troost *et al.*, *J. Am. Chem. Soc.* 1971, 93, (3), 737-745). Under N_2 , 1,2-dihydroacenaphthylene (12 g, 77.9 mmol) and dimethylcarbamoyl chloride were dissolved in 120 mL of chlorobenzene. The solution was then cooled to 0°C followed by adding 28 g of

AlCl₃ portion-wise. The mixture was slowly heated to 80 °C. After stirring at 80 °C for 4 hours, the solution was cooled back to 0 °C and additional 14 g of dimethylcarbamoyl chloride and 19 g of AlCl₃ were added. The dark solution was refluxed for additional 2-4 hours. The solution was cooled to room temperature and poured into 800 mL of cold aqueous hydrochloric acid solution (5%). The organic phase was extracted with chloroform, washed subsequently with sodium bicarbonate solution and water, and dried over sodium sulfate. After removal of the solvents in *vacuo*, the residue solid materials were dissolved in hot ethanol. Crystals formed in 12 hours and were collected by filtration (more crystals formed from the mother liquid. Crystals can also form directly from hot chlorobenzene solution). Yield: 15.4 mg (66.7%). ¹H NMR (CDCl₃, 500.046 MHz): δ = 7.40 (d, 2H, ³J = 7.0 Hz, Np), 7.33 (d, 2H, ³J = 7.0 Hz, Np), 3.43 (s, 4H, CH₂), 3.11 (s, 9H, CH₃), 2.89 (s, 9H, CH₃).

Synthesis of 1,2-dihydroacenaphthylene dicarboxylic acid anhydride.

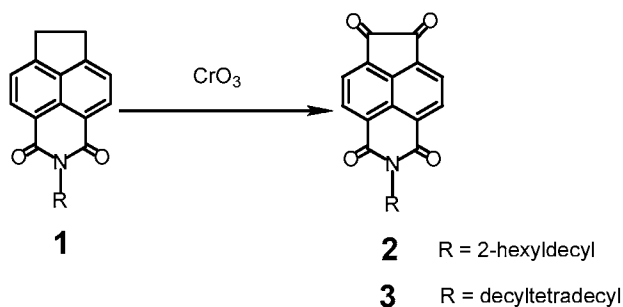
N5,N5,N6,N6-tetramethyl-1,2-dihydroacenaphthylene-5,6-dicarboxamide (4.0 g, 13.5 mmol) was suspended in 10 mL of concentrated hydrochloric acid. The mixture was heated to reflux for 4-5 hours. The solution was then cooled to 0 °C. The off-white precipitate was collected by filtration and washed with cold water. The crude materials were recrystallized from hot acetic anhydride solution to afford pure product as light brown needles. Yield (2.08 g, 68.7%). ¹H NMR (CDCl₃, 500.046 MHz): δ = 8.54 (d, 2H, ³J = 7.0 Hz, Np), 7.65 (d, 2H, ³J = 7.0 Hz, Np), 3.45 (s, 4H, CH₂).

Synthesis of N-hexyldecyl-1,2-dihydroacenaphthylene dicarboxylic acid imide.

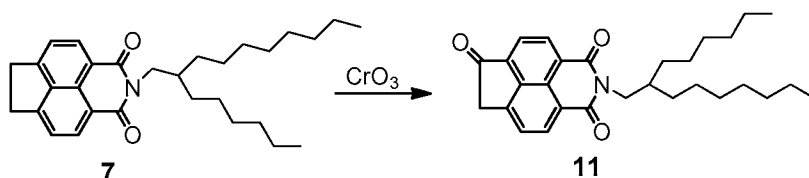
Under N₂, 1,2-dihydroacenaphthylene dicarboxylic acid anhydride (1.2 g, 5.36 mmol) and 2-hexyldecan-1-amine (1.5 g, 6.22 mmol) were dissolved in 15 mL of DMF. The solution was slowly heated to 90 °C for 12 hours and to 110 °C for additional 12 hours. After cooling back to room temperature, water was added to quench the reaction. The organic phase was extracted with chloroform, washed subsequently with water and brine, dried over sodium sulfate. After removal of the solvents, the crude materials were further purified by column chromatography with hexanes: chloroform (2v:1v) as the eluent. Yield (1.56, 65.1%). ¹H NMR (CDCl₃, 500.046 MHz): δ = 8.51 (d, 2H, ³J = 7.0 Hz, Np), 7.58 (d, 2H, ³J = 7.0 Hz, Np), 4.14 (d, ³J = 7.0 Hz, 4H, Hexyldecyl-CH₂), 3.59 (s, 4H, CH₂), 2.01 (m, 1H, hexyldecyl-CH), 1.5-1.2 (m, 24 H, hexyldecyl-CH₂), 0.87 (m, 6H, hexyldecyl-CH₃).

Synthesis of N-decyltetradecyl-1,2-dihydroacenaphthylene dicarboxylic acid imide. N-decyltetradecyl-1,2-dihydroacenaphthylene dicarboxylic acid imide was prepared similarly as N-hexyldecyl-1,2-dihydroacenaphthylene dicarboxylic acid imide by using 1,2-

dihydroacenaphthylene dicarboxylic acid anhydride (1.2 g, 5.36 mmol) and 2-decyltetradecan-1-amine (2.20 g, 6.22 mmol). Yield (2.40, 69.1%). ^1H NMR (CDCl_3 , 500.046 MHz): δ = 8.48 (d, 2H, 3J = 7.0 Hz, Np), 7.58 (d, 2H, 3J = 7.0 Hz, Np), 4.14 (d, 3J = 7.0 Hz, 4H, CH_2), 3.59 (s, 4H, CH_2), 2.01 (m, 1H, CH), 1.5-1.2 (m, 40 H, CH_2), 0.87 (m, 6H, CH_3).



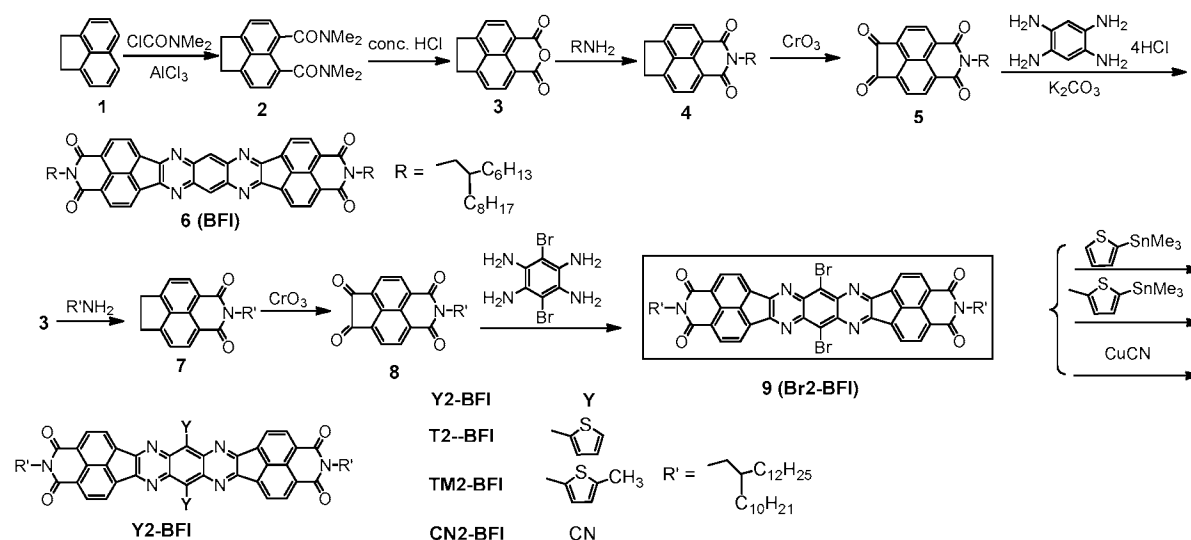
Compound 3. At 110 °C, compound **1** (3.0 g, 5.36 mmole) was dissolved in 150 mL of acetic anhydride. After cooling back to room temperature, CrO_3 (1.6 g, 16.0 mmole) was added in portions. The solution was slowly warmed up to 50-80 °C and kept stirring for 4 hours. The dark green suspension was slowly poured onto 200 g of crushed ice. The crude material was extracted with CHCl_3 , washed subsequently with water and brine. After removal of all the solvents, the solid materials were further purified by thin film chromatography using Hexanes, CH_3Cl and methanol mixed solvents as the eluent to afford a yellow solid. Yield: 1.0 g (32%). ^1H NMR (CDCl_3 , 500.046 MHz): δ 8.84 (d, 2H, 3J = 7.5 Hz, naphthalene-H), 8.38 (d, 2H, 3J = 7.5 Hz, naphthalene-H), 4.19 (d, 3J = 6.0 Hz, 2H, CH_2), 2.02 (m, 1H, CH), 1.5-1.2 (m, 4H, CH_2), 2.14 (m, 6H, Me); ^{13}C NMR (125 MHz, CDCl_3): δ 186.2, 162.9, 143.8, 132.2, 126.7, 126.2, 122.9, 45.1, 36.6, 31.9, 31.6, 30.0, 29.7, 29.7, 29.6, 29.4, 29.3, 26.4, 22.7, 14.1; HRMS (m/z): $[\text{M}]^+$ calcd. for $\text{C}_{38}\text{H}_{53}\text{NO}_4$, 587.83; found, 587.44.



Compound 11. At 110 °C, compound **7** (3.0 g, 5.36 mmole) was dissolved in 150 mL of acetic anhydride. After cooling back to room temperature, CrO_3 (1.6 g, 16.0 mmole) was added in portions. After stirring over night at room temperature, the dark green suspension was slowly poured onto 200 g of crushed ice. The crude material was extracted with CHCl_3 , washed subsequently with water and brine. After removal of all the solvents, the solid materials were further purified by thin film chromatography using hexanes, CH_3Cl and methanol mixed solvents as the eluent to afford an orange solid. Yield: 0.27 g (8.7%). ^1H

NMR (CDCl₃, 500.046 MHz): δ 8.71 (d, 1H, 3J = 7.2 Hz, Np), 8.62 (d, 1H, 3J = 7.2 Hz, Np), 8.17 (d, 1H, 3J = 7.0 Hz, Np), 7.78 (d, 1H, 3J = 7.0 Hz, Np), 4.16 (d, 3J = 8.0 Hz, 2H, CH₂), 4.02 (s, 2H, CH₂), 2.03 (m, 1H, CH), 1.5-1.2 (m, 24H, CH₂), 0.87 (m, 6H, Me). HRMS (m/z): [M]⁺ calcd. for C₂₉H₃₇NO₃, 447.28; found, 447.12.

EXAMPLE 1B – Synthesis of Diketone Intermediates



Synthesis of N5,N5,N6,N6-tetramethyl-1,2-dihydroacenaphthylene-5,6-dicarboxamide (Compound 2) (Trost *et al.*, *J. Am. Chem. Soc.* 1971, 93, (3), 737-745).

Under N₂, 1,2-dihydroacenaphthylene (Compound 1, 12 g, 77.9 mmol) and dimethylcarbamoyl chloride (22 g, 206 mmol) were dissolved in 120 mL of chlorobenzene. The solution was then cooled to 0 °C followed by adding AlCl₃ (28 g, 209 mmol) portionwise. The mixture was slowly heated to 80 °C. After stirring at 80 °C for 12 hours, the solution was cooled back to 0 °C and additional 14 g (130 mmol) of dimethylcarbamoyl chloride and 19 g (144 mmol) of AlCl₃ were added. The dark solution was refluxed for additional 12 hours. The solution was cooled to room temperature and poured into 800 mL of cold aqueous hydrochloric acid solution (5%). The organic phase was extracted with chloroform, washed subsequently with sodium bicarbonate solution and water, and dried over sodium sulfate. After removal of chloroform, crystals formed in 12 hs from chlorobenzene solution. Yield: 15.4 g (66.7%). ¹H NMR (CDCl₃, 500 MHz): δ = 7.40 (d, 2H, 3J = 7.0 Hz, Np), 7.33 (d, 2H, 3J = 7.0 Hz, Np), 3.43 (s, 4H, CH₂), 3.11 (s, 6H, CH₃), 2.89 ppm (s, 6H, CH₃).

Synthesis of 1,2-dihydroacenaphthylene dicarboxylic acid anhydride (Compound 3). Compound 2 (4.0 g, 13.5 mmol) was suspended in 10 mL of concentric hydrochloric acid.

The mixture was heated to reflux for 4-5 hours. The solution was then cooled to 0 °C. The off-white precipitate was collected by filtration and washed with cold water. The crude materials were recrystallized from hot acetic anhydride solution to afford pure product as needles. Yield (2.08 g, 68.7%). ¹H NMR (CDCl₃, 25 °C, 500 MHz): δ = 8.54 (d, 2H, ³J = 7.0 Hz, Np), 7.65 (d, 2H, ³J = 7.0 Hz, Np), 3.45 ppm (s, 4H, CH₂).

Synthesis of N-hexyldecyl-1,2-dihydroacenaphthylene dicarboxylic acid imide (Compound 4). Under N₂, Compound 3 (1.2 g, 5.4 mmol) and 2-hexyldecan-1-amine (1.5 g, 6.2 mmol) were dissolved in 15 mL of DMF. The solution was slowly heated to 90 °C for 12 hours and to 110 °C for additional 12 hours. After cooling back to room temperature, water was added to quench the reaction. The organic phase was extracted with chloroform, washed subsequently with water and brine, dried over sodium sulfate. After removal of the solvents, the crude materials were further purified by column chromatography with hexanes: chloroform (2:1 v/v) as the eluent. Yield (1.56, 65.1%). ¹H NMR (CDCl₃, 25 °C, 500 MHz): δ = 8.51 (d, 2H, ³J = 7.0 Hz, Np), 7.58 (d, 2H, ³J = 7.0 Hz, Np), 4.14 (d, 2H, ³J = 7.0 Hz, CH₂), 3.59 (s, 4H, CH₂), 2.01 (m, 1H, CH), 1.5-1.2 (m, 24 H, CH₂), 0.87 ppm (m, 6H, CH₃). HRMS (m/z): [M]⁺ calcd. for C₃₀H₄₁NO₂, 447.65; found, 448.35.

Synthesis of Compound 5. At 110 °C, compound 4 (1.0 g, 2.2 mmol) was dissolved in 100 mL of acetic anhydride. After cooling back to room temperature, CrO₃ (600 mg, 6.1 mmol) was added in portions. The solution was slowly warmed up to 50-80 °C and kept stirring for 4 hours. The dark green suspension was slowly poured onto 100 g of crushed ice. The crude material was extracted with CHCl₃, washed subsequently with water and brine. After removal of all the solvents, the solid materials were further purified by thin film chromatography using hexanes: CHCl₃ (3:2 v/v) with a few drops of methanol as the eluent to afford a yellow solid. Yield: 210 mg (19.8%). ¹H NMR (CDCl₃, 25 °C, 500 MHz): δ 8.83 (d, 2H, ³J = 7.5 Hz, Np), 8.37 (d, 2H, ³J = 7.5 Hz, Np), 4.20 (d, ³J = 6.0 Hz, 2H, CH₂), 2.10 (m, 1H, CH), 1.5-1.2 (m, 24H, CH₂), 2.14 ppm (m, 6H, Me); HRMS (m/z): [M]⁺ calcd. for C₃₀H₃₇NO₄, 475.62; found, 475.12.

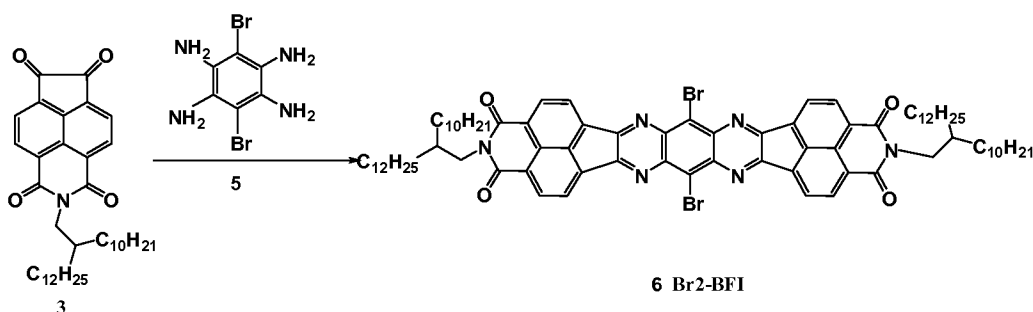
Synthesis of N-decyltetradecyl-1,2-dihydroacenaphthylene dicarboxylic acid imide (Compound 7). Under N₂, compound 3 (1.2 g, 5.4 mmol) and 2-decyltetradecyl-1-amine (2.2 g, 6.2 mmol) were dissolved in 25 mL of DMF. The solution was slowly heated to 90 °C for 12 hours and to 110 °C for additional 12 hours. After cooling back to room temperature, water was added to quench the reaction. The organic phase was extracted with chloroform, washed subsequently with water and brine, dried over sodium sulfate. After

removal of the solvents, the crude materials were further purified by column chromatography with hexanes: chloroform (2:1 v/v) as the eluent Yield (2.4 g, 80.0%). ^1H NMR (CDCl_3 , 25 °C, 500 MHz): δ = 8.51 (d, 2H, ^3J = 7.0 Hz, Np), 7.58 (d, 2H, ^3J = 7.0 Hz, Np), 4.14 (d, 2H, ^3J = 7.0 Hz, CH_2), 3.59 (s, 4H, CH_2), 2.01 (m, 1H, CH), 1.5-1.2 (m, 40H, CH_2), 0.87 ppm (m, 6H, CH_3). HRMS (m/z): $[\text{M}]^+$ calcd. for $\text{C}_{38}\text{H}_{57}\text{NO}_2$, 559.86; found, 560.46.

Synthesis of Compound 8. At 110 °C, compound 7 (3.0 g, 5.4 mmol) was dissolved in 150 mL of acetic anhydride. After cooling back to room temperature, CrO_3 (1.6 g, 16.0 mmol) was added in portions. The solution was slowly warmed up to 50-80 °C and kept stirring for 4 hours. The dark green suspension was slowly poured onto 200 g of crushed ice. The crude material was extracted with CHCl_3 , washed subsequently with water and brine. After removal of all the solvents, the solid materials were further purified by thin film chromatography using hexanes: CHCl_3 (3:2 v/v) with a few drops of methanol as the eluent to afford a yellow solid. Yield: 1.0 g (31.7%). ^1H NMR (CDCl_3 , 25 °C, 500 MHz): δ = 8.84 (d, 2H, ^3J = 7.5 Hz, Np), 8.38 (d, 2H, ^3J = 7.5 Hz, Np), 4.19 (d, ^3J = 6.0 Hz, 2H, CH_2), 2.02 (m, 1H, CH), 1.5-1.2 (m, 40H, CH_2), 2.14 ppm (m, 6H, Me); ^{13}C NMR (125 MHz, CDCl_3): δ 186.2, 162.9, 143.8, 132.2, 126.7, 126.2, 122.9, 45.1, 36.6, 31.9, 31.6, 30.0, 29.7, 29.7, 29.6, 29.4, 29.3, 26.4, 22.7, 14.1; HRMS (m/z): $[\text{M}]^+$ calcd. for $\text{C}_{38}\text{H}_{53}\text{NO}_4$, 587.83; found, 587.44.

PART II

EXAMPLE 2A – Synthesis of Compound/Monomer Br2-BFI



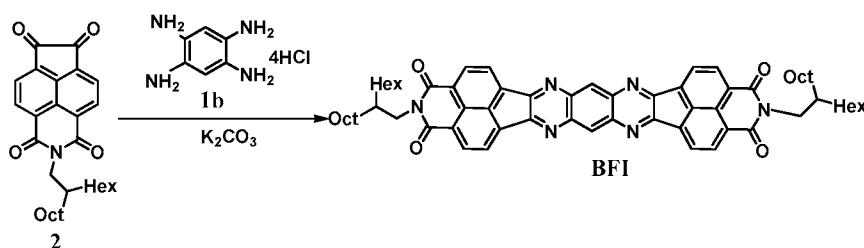
Compound 6. 3,6-dibromobenzene-1,2,4,5-tetraamine (Compound 5) was prepared according to the reported procedure (Hong, D.-J. et al. *Chem. Commun.* 2010, 46, (27), 4896). Compound 5 (0.23 g, 0.77 mmole) was dissolved in 15 mL of chlorobenzene followed by adding 1.0 g of compound 3 (1.7 mmole). The mixture was slowly heated to 100 °C and kept stirred for 24 hours. After cooling back to room temperature, the volatile materials were removed under high vacuum. The solid materials left were further purified through preparative thin film chromatography. The product was isolated as an orange red

solid. Yield: 0.65 g, 54.6%. ^1H NMR (CDCl_3 , 500.046 MHz): δ 8.50 (d, $^3J = 7.0$ Hz, 4H, NP), 8.39 (d, $^3J = 7.5$ Hz, NP, 4H), 3.91 (d, $J = 6.5$ Hz, 4H, CH_2), 1.88 (m, 2H, CH), 1.4-1.2 (m, 40 H, CH_2), 0.90 (m, 12H, CH_3); ^{13}C NMR (125 MHz, CDCl_3): δ 162.9, 155.1, 138.6, 136.4, 134.6, 132.5, 129.2, 125.0, 124.9, 124.0, 123.9, 44.8, 34.0, 32.2 (2C), 31.8, 30.3, 30.0, 29.9 9 (2C), 29.6, 26.6, 22.9, 14.4; HRMS (m/z): $[\text{M}]^+$ calcd. for $\text{C}_{82}\text{H}_{106}\text{Br}_2\text{N}_6\text{O}_4$, 1399.56; found, 1399.55.

EXAMPLE 2B – Synthesis of Compound/Monomer Br2-BFI

Compound **8** (1.0 g, 1.7 mmol) was added to 3,6-dibromobenzene-1,2,4,5-tetraamine (0.77 mmol) in acetic acid prepared according to the reported procedure (E. Wang, et al, *Org. Lett.* **2010**, 12, 4470.) The mixture was slowly heated to 100 °C and kept stirred for 24-48 hours. After cooling back to room temperature, the volatile materials were removed under high vacuum. The solid materials left were further purified through preparative thin film chromatography with CHCl_3 : methanol (50:1 v/v) as the eluent ($R_f = 0.24$). The product was isolated as an orange red solid. Yield: 0.65 g, 54.6%. ^1H NMR (CDCl_3 , 25 °C, 500 MHz): δ = 8.46 (d, 4H, $^3J = 7.0$ Hz, Np), 8.35 (d, 4H, $^3J = 7.0$ Hz, Np), 3.87 (d, 4H, $J = 7.0$ Hz, CH_2), 1.82 (m, 2H, CH), 1.4-1.2 (m, 80 H, CH_2), 0.86 ppm (m, 12H, CH_3); ^{13}C NMR (125 MHz, CDCl_3): δ = 162.9, 155.1, 138.6, 136.4, 134.6, 132.5, 129.2, 125.0, 124.9, 123.9, 44.8, 34.0, 32.2 (2C), 31.8, 30.3, 30.0, 29.9 9 (2C), 29.6, 26.6, 22.9, 14.4 ppm; HRMS (m/z): $[\text{M}]^+$ calcd. for $\text{C}_{82}\text{H}_{106}\text{Br}_2\text{N}_6\text{O}_4$, 1399.56; found, 1399.55; elemental analysis calcd for $\text{C}_{82}\text{H}_{106}\text{Br}_2\text{N}_6\text{O}_4$: C 70.37%, H 7.63%, N 6.00%; found C 70.35%, H 7.58%, N 6.14%.

EXAMPLE 3A – Synthesis and Characteristics of Compound BFI



1,2,4,5-benzenetetraamine tetrahydrochloride (compound **1b**) was purchased from Aldrich and used as received. Inside a reaction tube, compound **2** (100 mg, 0.21 mmole), 1,2,4,5-benzenetetraamine tetrahydrochloride (compound **1b**, 27 mg, 0.095 mmole) and K_2CO_3 (26 mg, 0.19 mmole) were suspended in 15 mL of ethanol. The mixture was slowly warmed up to 78 °C and a yellow precipitate formed within 2 hours. The suspension was kept stirring over night to 48 hours at the same temperature. After cooling back to room

temperature, the solid was collected by filtration and followed by washing with 3×10 mL of ethanol and 3×10 mL of CHCl_3 . The crude product was further purified by crystallization from hot chlorobenzene solution. Yield: 69 mg (71%). ^1H NMR (CDCl_3 , 500 MHz): δ = 8.94 (s, 2H, Ph), 8.70 (d, 2H, 3J = 7.0 Hz, Nh), 8.52 (d, 2H, 3J = 7.5 Hz, Nh), 4.17 (d, 4H, 3J = 7.5 Hz, CH_2), 2.02 (m, 1H, CH), 1.4-1.2 (m, 24H, CH_2), 0.9 (m, 6H, Me).

BFI exhibited an intense absorption band with an absorption maximum at $\lambda_{\text{max}} = 395$ nm in a dilute chlorobenzene solution, which was slightly blue shifted (15 nm) as thin film on the glass substrate. The optical band gap estimated from the absorption edge was 2.46 eV. When excited at 395 nm, BFI emitted bright yellow green lights with three bands at $\lambda_{\text{max}} = 483$ nm, 516 nm and 552 nm, respectively.

The electron affinity of BFI was evaluated by cyclic voltammetry. BFI showed two quasi-reversible reduction waves at $E_{1/2} = -1.08$ V and -1.2 V vs SCE, respectively. No apparent oxidation was observed during an anodic scan in the range up to 1.2 V vs. SCE. Based on the onsets of reduction waves, the LUMO energy level of BFI was estimated to be -3.60 eV.

The BFI molecules were readily self-assembled into single crystalline 1D nanostructures. The nanowires (NWs) of BFI were also grown from hot chlorobenzene solution (0.5 mg/mL). The solution was heated to reflux and slowly cooled to room temperature without disturbing it.

Figure 1A and 1B show the transmission electron microscopy (TEM) and selected area electron diffraction (SAED) images (inset) of BFI. The sharp spots in the SAED pattern indicates that the NWs formed through the solution phase method are single-crystalline. The nanocrystals can be prepared in large quantity and high density as shown in the scanning electron microscopy (SEM) images (Figure 1C and 1D) suggesting that these NWs are suitable for fabricating solution processed organic NW electronics. According to single crystal x-ray diffraction, BFI has a fairly planar backbone. The BFI molecules adopt a slipped π - π stacking with a close intermolecular distance of 3.26 Å between the neighboring molecules. Between the BFI stacks, the BFI molecules are assembled by strong hydrogen bonding. In these hydrogen bonds, the oxygen on the carbonyl group and the ortho-carbon on the naphthalene ring of the neighboring molecule function as the hydrogen acceptor (A) and donor (D), respectively. The $\text{H}\cdots\text{O}$ distance is measured to be 2.44 Å and the $\text{C-H}\cdots\text{O}$ angle to be 140.1° . The strong π - π stacking and hydrogen bonding are beneficial to the high crystallinity and high charge carrier mobility.

BFI showed excellent thermal properties. Thermal gravimetric analysis (TGA) shows that BFI was thermally stable up to 400 °C. No apparent thermal transition was observed for BFI based on differential scanning calorimetry (DSC) scans in the temperature range of 30 to 300°C. BFI's excellent thermal stability is highly advantageous for applications in durable and robust organic electronics.

EXAMPLE 3B – Synthesis and Characteristics of Compound BFI

Inside a reaction tube, compound **5** (100 mg, 0.21 mmol), 1,2,4,5-benzenetetraamine tetrahydrochloride (27 mg, 0.095 mmol, bought from Sigma-Aldrich and used as received) and K₂CO₃ (26 mg, 0.19 mmol) were suspended in 15 mL of ethanol. The mixture was slowly warmed up to 78 °C and a yellow precipitate formed within 2 hours. The suspension was kept stirring over night at the same temperature. After cooling back to room temperature, the solid was collected by filtration and followed by washing with 3×10 mL of ethanol and 3×10 mL of CHCl₃. The crude product was further purified by crystallization from hot solution in chlorobenzene. Yield: 69 mg (60.3%). ¹H NMR (CDCl₃, 25 °C, 500 MHz): δ = 9.19 (s, 2H, Ph), 8.72 (d, 4H, ³J = 7.0 Hz, Np), 8.56 (d, 4H, ³J = 7.0 Hz, Np), 4.15 (d, 4H, ³J = 7.5 Hz, CH₂), 1.96 (m, 2H, CH), 1.4-1.2 (m, 48H, CH₂), 0.85 ppm (m, 12H, Me). ¹³C NMR (125 MHz, 25 °C, CDCl₃/CF₃COOD): δ 163.9, 155.4, 139.4 136.8, 129.6, 125.2, 125.1, 124.8, 45.6, 37.1, 32.2, 32.1, 31.9, 30.3, 30.0, 29.8, 29.6, 26.7, 26.6, 22.9, 14.3 ppm (2C); HRMS (m/z): [M]⁺ calcd. for C₆₆H₇₆N₆O₄, 1017.35; found, 1017.46.

EXAMPLE 4 – Transistors Based on Compound BFI

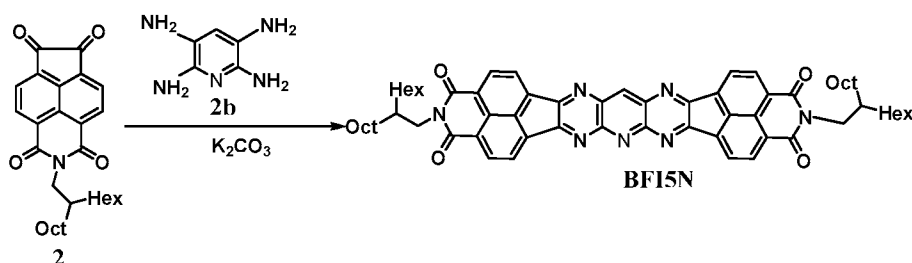
Field-effect transistors were fabricated on a heavily n-doped silicon substrate with thermally grown silicon dioxide gate insulator (200 nm; capacitance density, C_i = 17 nF/cm²). Photolithographically defined gold patterns (40 nm) with chromium adhesive layer (2 nm) acted as the source and drain electrodes in the bottom-contact/bottom-gate transistors, forming the channel width (W) of 800 μm and length (L) of 40 μm (W/L = 20). The substrates were cleaned by ultrasonication with acetone and isopropyl alcohol and dried by flow of nitrogen. The surface of a silicon dioxide substrate was further cleaned by plasma and treated with octyltrichlorosilane (OTS8) to form a hydrophobic self-assembled monolayer (SAM). BFI was deposited from a solution in trifluoroacetic acid (TFA) with 1–5 vol% of methanesulfonic acid (MSA) or in hot 1,2-dichlorobenzene. The films were immersed in methanol to remove trace of acid solvents and dried overnight under vacuum at room

temperature. The devices were annealed at various temperatures under argon environment. Electrical characteristics of the devices were measured using an HP4145B semiconductor parameter analyzer under nitrogen atmosphere.

The charge carrier mobilities were calculated from transfer curves using the standard saturation equation of metal-oxide-semiconductor field-effect transistors:

$I_{ds} = (\mu W Co / 2L)(V_g - V_t)^2$. (Kang, S.-M.; Leblebici, Y. *CMOS Digital Integrated Circuits: Analysis and Design*, McGraw-Hill, New York, 1996.) The electron mobility of $0.046 \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1}$ was obtained, with an on/off current ratio of 10^6 . The transistor characteristic curves of an n-channel field-effect transistor based on BFI are shown in Figure 3.

EXAMPLE 5 – Synthesis and Characteristics of Compound BFI5N



2,3,5,6-tetraaminopyridine (compound 2b) was synthesized according to reported procedures (CN101531632A, example 1). Inside a reaction tube, compound 2 (100 mg, 0.21 mmole) and 2b (26 mg, 0.19 mmole) were suspended in 5 mL of ethanol. The mixture was slowly warmed up to 78°C . Compound 2b (12.3 mg, 0.09 mmole) was added in three portions. The yellow suspension was kept stirring over night at the same temperature. After cooling back to room temperature, the solid was collected by filtration and followed by washing with $3 \times 10 \text{ mL}$ of ethanol and $3 \times 10 \text{ mL}$ of CHCl_3 . The crude product was further purified by crystallization from hot solution in chlorobenzene. Yield: 58 mg (54%). ^1H NMR ($\text{CDCl}_3/\text{CF}_3\text{COOD}$, 500 MHz): $\delta = 10.25$ (s, 1H, py), 9.00 (dd, 4H, Nh), 8.92 (d, 2H, $3J = 7.5 \text{ Hz}$, Nh), 8.74 (d, 2H, $3J = 7.0 \text{ Hz}$, Nh), 4.27 (d, 4H, $3J = 7.5 \text{ Hz}$, CH_2), 2.04 (m, 1H, CH), 1.4–1.2 (m, 24H, CH_2), 0.9 (m, 6H, Me); ^{13}C NMR (CF_3COOD , 125.7 MHz): 167.9, 167.8, 166.1, 161.4, 152.3, 147.6, 141.2, 138.0, 136.9, 136.6, 136.0, 135.8, 129.7, 129.1, 128.5, 127.8, 127.7, 48.7, 39.2, 33.8, 33.7, 33.6, 31.8, 31.5, 31.4, 31.2, 28.4, 24.4, 24.4, 14.7, 14.7.

BFI5N exhibited an intense absorption with an absorption maximum (λ_{max}) at 395 nm in a dilute chlorobenzene solution, which was slightly blue shifted (15 nm) as thin film on the glass substrate. The optical band gap estimated from the absorption edge was 2.46 eV.

Unlike highly emissive BFI, BFI5N was completely non-luminescent both in dilute solution and as thin film.

The electron affinity of BFI5N was characterized by cyclic voltammetry. BFI5N showed an unresolved irreversible reduction wave at $E_{1/2} = -1.25$ V vs. SCE. No apparent oxidation was observed during an anodic scan in the range up to 1.2 V vs. SCE. The LUMO energy level of BFI5N calculated from the reduction onset was -3.45 eV.

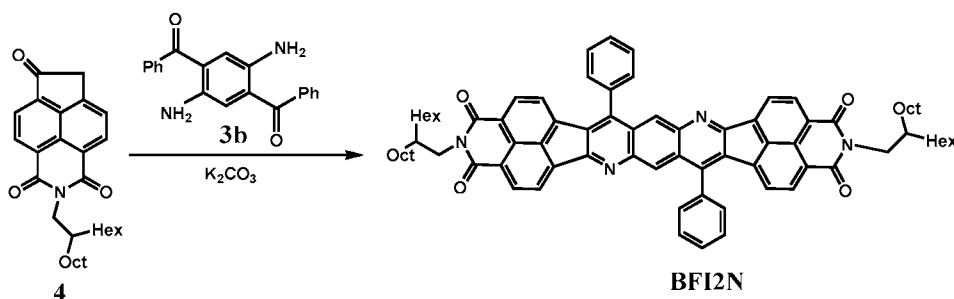
BFI5N showed excellent thermal properties. Thermal gravimetric analysis (TGA) shows that BFI5N was thermally stable up to 403 °C. No apparent thermal transition was observed for BFI5N based on differential scanning calorimetry (DSC) scans in the temperature range of 20 to 300 °C. The excellent thermal stability of BFI5N is highly advantageous for durable and robust organic electronics.

EXAMPLE 6 – Transistors Based on Compound BFI5N

Field-effect transistors were fabricated on a heavily n-doped silicon substrate with thermally grown silicon dioxide gate insulator (200 nm; capacitance density, $C_i = 17$ nF/cm²). Photolithographically defined gold patterns (40 nm) with chromium adhesive layer (2 nm) acted as the source and drain electrodes in the bottom-contact/bottom-gate transistors, forming the channel width (W) of 800 μm and length (L) of 40 μm (W/L = 20). The substrates were cleaned by ultrasonication with acetone and isopropyl alcohol and dried by flow of nitrogen. The surface of a silicon dioxide substrate was further cleaned by plasma and treated with octyltrichlorosilane (OTS8) to form a hydrophobic self-assembled monolayer (SAM). BFI5N was deposited from a solution in trifluoroacetic acid (TFA) with 1–5 vol% of methanesulfonic acid (MSA) or in hot 1,2-dichlorobenzene. The films were immersed in methanol to remove trace of acid solvents and dried overnight under vacuum at room temperature. The devices were annealed at various temperatures under argon environment. Electrical characteristics of the devices were measured using an HP4145B semiconductor parameter analyzer under nitrogen atmosphere.

The charge carrier mobilities were calculated from transfer curves using the standard saturation equation of metal-oxide-semiconductor field-effect transistors:
$$I_{ds} = (\mu W C_o / 2L)(V_g - V_t)^2$$
 (Kang, S.-M.; Leblebici, Y. *CMOS Digital Integrated Circuits: Analysis and Design*, McGraw-Hill, New York, 1996.) The electron mobility of 0.010 cm² V⁻¹ s⁻¹ was obtained for transistors based on BFI5N (Figure 3b).

EXAMPLE 7 – Synthesis and Characteristics of Compound BFI2N



Compound 3b was synthesized according to reported procedure (Liu, S. et al. *Dyes and Pigments*, 81, 2009, 218–223). Inside a reaction tube, compound 4 (100 mg, 0.22 mmole) and diphenyl phosphate (433 mg, 1.74 mmole) and (2,5-diamino-1,4-phenylene)bis(phenylmethanone) (compound 3b, 34 mg, 0.11 mmole) were mixed with 3 mL of toluene. The mixture was slowly warmed up to 110 °C and kept stirring over night. After cooling back to room temperature, the dark red solution was precipitated into 80 mL of methanol and triethylamine mixed solvents (1:1). A red solid formed which was collected and washed with 3×20 mL of methanol. The solid was further purified by column chromatography with CHCl₃ as the eluent solvent. Yield: 63 mg (65%). ¹H NMR (CDCl₃, 300.13 MHz): δ = 8.27 (m, 4H), 7.95–7.75 (m, 12H), 7.50 (br, 2H), 6.98 (d, 2H, 3J = 7.5 Hz), 4.09 (d, 4H, 3J = 7.2 Hz, CH₂), 1.90 (m, 2H, CH), 1.4–1.1 (m, 48H, CH₂), 0.83 (t, 12H, Me); ¹³C NMR (CF₃COOD, 125.7 MHz): 163.4, 163.2, 159.8, 144.1, 143.8, 138.4, 138.2, 134.7, 134.2, 132.4, 130.9, 129.9, 129.7, 129.3, 129.1, 128.5, 127.7, 124.6, 123.1, 122.8, 122.1, 120.8, 44.7, 36.9, 32.1, 32.1, 32.0, 31.9, 30.3, 30.0, 29.8, 29.6, 26.8, 26.7, 22.9, 14.3.

BFI2N exhibited an intense absorption with an absorption maximum (λ_{max}) at 395 nm with two relatively weak low-energy absorption bands in a dilute chlorobenzene solution, which became less structured as thin film on the glass substrate. The optical band gap estimated from the absorption edge was 2.20 eV. BFI2N was highly emissive in dilute solution with three emission band at λ_{max} = 615 nm, 558 nm, 520 nm. BFI2N thin film showed a broad structure-less red emission centered at λ_{max} = 600 nm.

The electron affinity of BFI2N was characterized by cyclic voltammetry. BFI2N showed an unresolved irreversible reduction wave at $E_{1/2}$ = -1.20 V vs. SCE. No apparent oxidation was observed during an anodic scan in the range up to 1.2 V vs. SCE. The LUMO energy level of BFI2N calculated from the reduction onset was -3.55 eV.

BFI2N showed excellent thermal properties. Thermal gravimetric analysis (TGA) shows that BFI2N was thermally stable up to 446 °C. No apparent thermal transition was observed for BFI2N based on differential scanning calorimetry (DSC) scans in the

temperature range of 20 to 300°C. The excellent thermal stability of BFI2N is highly advantageous for durable and robust organic electronics.

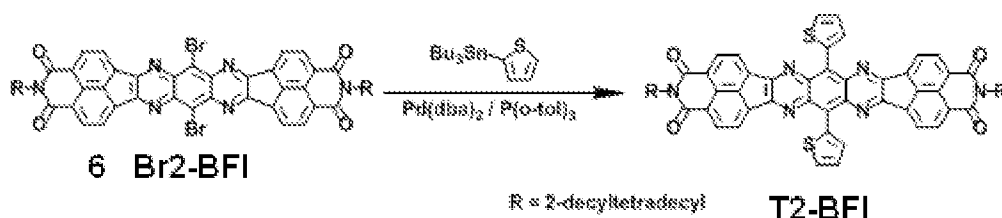
EXAMPLE 8 – Transistors Based on Compound BFI2N

Field-effect transistors were fabricated on a heavily n-doped silicon substrate with thermally grown silicon dioxide gate insulator (200 nm; capacitance density, $C_i = 17 \text{ nF/cm}^2$). Photolithographically defined gold patterns (40 nm) with chromium adhesive layer (2 nm) acted as the source and drain electrodes in the bottom-contact/bottom-gate transistors, forming the channel width (W) of 800 μm and length (L) of 40 μm (W/L = 20). The substrates were cleaned by ultrasonication with acetone and isopropyl alcohol and dried by flow of nitrogen. The surface of a silicon dioxide substrate was further cleaned by plasma and treated with octyltrichlorosilane (OTS8) to form a hydrophobic self-assembled monolayer (SAM). BFI2N was deposited onto the substrate by spin-coating from a solution in chloroform. The devices were annealed at various temperatures under argon environment. Electrical characteristics of the devices were measured using an HP4145B semiconductor parameter analyzer under nitrogen atmosphere.

The charge carrier mobilities were calculated from transfer curves using the standard saturation equation of metal-oxide-semiconductor field-effect transistors:

$I_{ds} = (\mu W C_o / 2L)(V_g - V_t)^2$. (Kang, S.-M.; Leblebici, Y. *CMOS Digital Integrated Circuits: Analysis and Design*, McGraw-Hill, New York, 1996.) The electron mobility of $1.4 \times 10^{-4} \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1}$ was obtained for transistors based on BFI2N (Figure 3b).

EXAMPLE 9A – Synthesis and Characteristics of Compound T2-BFI



Under protection of argon, compound 6 (200 mg, 0.14 mmole), tributylstannanylthiophene (128 mg, 0.34 mmole), Pd(dba)_2 (3 mg) and P(o-tol)_3 (6 mg) were charged into a reaction tube and dissolved in 10 mL of degassed toluene. The solution was slowly warmed up to 110 °C and kept stirring for 2 days. After cooling back to room temperature, the volatile materials were removed under high vacuum. The solids left were further purified through column chromatography with chloroform and methanol as the eluent

solvents. The pure product was isolated as a blue solid. Yield: 135 mg, 67%. ^1H NMR (CDCl_3 , 500 MHz): δ = 8.43 (d, 3J = 7.0 Hz, 4H, Np), 8.28 (dd, 2H, Th), 8.12 (d, 3J = 7.0 Hz, 4H, Np), 7.82 (dd, 2H, Th), 7.36 (q, 2H, Th), 3.77 (d, 4H, CH_2), 1.83 (m, 1H, CH), 1.4-1.2 (m, 80 H, CH_2). 0.83 (m, 12H, Me); ^{13}C NMR (CDCl_3 , 500 MHz): 163.1, 152.7, 136.8, 136.2, 135.7, 135.6, 133.7, 132.5, 131.7, 131.1, 126.4, 125.0, 124.3, 123.2, 44.6, 37.0, 32.2, 31.8, 30.3, 29.9, 26.7, 22.9.

T2-BFI exhibited two absorption bands in dilute chloroform solution, one intense absorption with an absorption maximum (λ_{max}) at 410 nm which is due to the π - π^* transition of the traazabenzodifluoranthene diimide moiety, and a weak low energy absorption at λ_{max} = 550 nm which mainly arises from charge transfer from the central electron donating dithienylbenzene moiety to the naphthalene imide group. The low energy band was red-shifted and relatively more intense going from dilute solution to thin film due to more efficient charge transfer and stronger intermolecular interaction in the solid state. The optical band gap estimated from the absorption edge was 1.55 eV.

The electron affinity of T2-BFI was characterized by cyclic voltammetry. T2-BFI showed a two quasi-reversible reduction wave at $E_{1/2}$ = -1.10 V and -1.35 V vs. SCE, respectively. No apparent oxidation was observed during an anodic scan in the range up to 1.3 V vs. SCE. The LUMO energy level of T2-BFI calculated from the reduction onset was -3.70 eV.

T2-BFI showed excellent thermal properties. Thermal gravimetric analysis (TGA) shows that T2-BFI was thermally stable up to 400 °C. No apparent thermal transition was observed for T2-BFI based on differential scanning calorimetry (DSC) scans in the temperature range of 30 to 300 °C. The excellent thermal stability of T2-BFI is highly advantageous for applications in durable and robust organic electronics.

EXAMPLE 9B – Synthesis and Characteristics of Compound T2-BFI

Under protection of argon, Br2-BFI (200 mg, 0.14 mmol), tributylstannanylthiophene (128 mg, 0.34 mmol), $\text{Pd}(\text{dba})_2$ (3 mg) and $\text{P}(o\text{-tol})_3$ (6 mg) were charged into a reaction tube and dissolved in 10 mL of degassed toluene. The solution was slowly warmed up to 110 °C and kept stirring for 2 days. After cooling back to room temperature, the volatile materials were removed under high vacuum. The solids left were further purified through column chromatography with chloroform and methanol (200:1 v/v) as the eluent solvents (R_f = 0.28). The pure product was isolated as a blue solid. Yield: 135 mg, 67%. ^1H NMR (CDCl_3 , 25 °C,

500 MHz): δ = 8.43 (d, 4H, 3J = 7.0 Hz, Np), 8.28 (d, 2H, 3J = 3.5 Hz, Th), 8.12 (d, 4H, 3J = 7.0 Hz, Np), 7.83 (d, 2H, 3J = 5.0 Hz, Th), 7.36 (q, 2H, Th), 3.77 (d, 4H, 3J = 4.0 Hz, CH₂), 1.83 (m, 2H, CH), 1.4-1.2 (m, 80 H, CH₂). 0.83 ppm (m, 12H, Me); ^{13}C NMR (CDCl₃, 25 °C, 500 MHz): 163.1, 152.7, 136.8, 136.2, 135.7, 135.6, 133.7, 132.5, 131.7, 131.1, 126.4, 125.0, 124.3, 123.2, 44.6, 37.0, 32.2, 31.8, 30.3, 29.9, 26.7, 22.9, 14.4 ppm; HRMS (m/z): [M]⁺ calcd. for C₉₀H₁₁₂N₆O₄S₂, 1406.02; found, 1405.71; elemental analysis calcd for C₉₀H₁₁₂N₆O₄S₂: C 76.88%, H 8.03%, N 5.98%; found C 76.70%, H 7.99%, N 5.97%.

EXAMPLE 10 – Transistors Based on Compound T2-BFI

Field-effect transistors were fabricated on a heavily n-doped silicon substrate with thermally grown silicon dioxide gate insulator (200 nm; capacitance density, C_i = 17 nF/cm²). Photolithographically defined gold patterns (40 nm) with chromium adhesive layer (2 nm) acted as the source and drain electrodes in the bottom-contact/bottom-gate transistors, forming the channel width (W) of 800 μm and length (L) of 40 μm (W/L = 20). The substrates were cleaned by ultrasonication with acetone and isopropyl alcohol and dried by flow of nitrogen. The surface of a silicon dioxide substrate was further cleaned by plasma and treated with octyltrichlorosilane (OTS8) to form a hydrophobic self-assembled monolayer (SAM). T2-BFI was deposited onto the substrate by spin-coating from a solution in chloroform. The devices were annealed at various temperatures under argon environment. Electrical characteristics of the devices were measured using an HP4145B semiconductor parameter analyzer under nitrogen atmosphere.

The charge carrier mobilities were calculated from transfer curves using the standard saturation equation of metal-oxide-semiconductor field-effect transistors:
 $I_{ds} = (\mu W C_o / 2L)(V_g - V_t)^2$. (Kang, S.-M.; Leblebici, Y. *CMOS Digital Integrated Circuits: Analysis and Design*, McGraw-Hill, New York, 1996.) The electron mobility of 0.12 cm² V⁻¹ s⁻¹ was obtained for transistors based on T2-BFI (*Angew. Chem. Int. Ed.* **2013**, 52, 5513-5517).

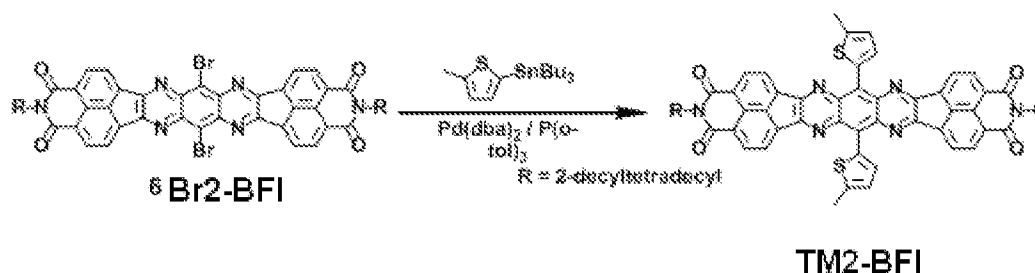
EXAMPLE 11 – Solar cells based on T2-BFI

Solar cells with device structure of ITO/PEDOT:PSS/active layer/LiF/Al were fabricated. ITO substrates (10 $\Omega/\square$, Shanghai B. Tree Tech. Consult Co., Ltd, Shanghai, China) were cleaned sequentially with acetone, deionized water and isopropyl alcohol in an ultrasonic bath, and blown with nitrogen until dried. A 40 nm PEDOT:PSS (Clevios P VP AI

4083) layer was spin-coated on top of the ITO and dried at 150 °C for 10 min under vacuum. The active layer was then spin-coated from poly[(4,4'-bis(3-(2-ethyl-hexyl)dithieno[3,2-*b*:2',3'-*d*]silole)-2,6-diyl-alt-(2,5-bis(3-(2-ethyl-hexyl)thiophen-2-yl)thiazolo[5,4-*d*]thiazole)] (PSEHTT):T2-BFI (1:4 *wt/wt*) blend solution to make a thin film of ~90 nm thickness and thermally annealed at 150 °C for 10 min in a glovebox. The substrates were then loaded in a thermal evaporator (BOC Edwards, 306) to deposit a cathode composed of 1.0 nm LiF and 90 nm Al under high vacuum (8×10^{-7} Torr). Five solar cells, each with an active area of 4 mm², were fabricated per ITO substrate. PSEHTT was synthesized according to CN102782011A, EP2493960A1, US20120273732, and Subramaniyan *et al.*, *Adv. Energy Mater.* **2011**, 1, 854-860.

The current density–voltage (*J*–*V*, shown in Figure 7a) curves of solar cells were measured using a HP4155A semiconductor parameter analyzer under laboratory ambient air conditions. An AM1.5 illumination at 100 mW/cm² was provided by a filtered Xe lamp and calibrated by using an NREL-calibrated Si diode. The external quantum efficiency (EQE, shown in Figure 7b) was measured using a QEX10 solar cell quantum efficiency measurement system (PV Measurements, Inc.) and was calibrated with a NREL-certified Si diode before measurement. The resulting photovoltaic parameters include an open circuit voltage (*V*_{oc}) of 0.79 V, a short-circuit current density (*J*_{sc}) of 5.14 mAcm⁻², and a fill factor (FF) of 0.44. A maximum power conversion efficiency of 1.80% (average of 1.74 ± 0.06 %) was achieved (*Angew. Chem. Int. Ed.* **2013**, 52, 5513-5517).

EXAMPLE 12A – Synthesis and Characteristics of Compound TM2-BFI



Under protection of argon, compound 6 (200 mg, 0.14 mmole), trimethyl(5-methylthiophen-2-yl)stannane (74 mg, 0.28 mmole), Pd(dba)₂ (3 mg) and P(*o*-tol)₃ 96 mg were charged into a reaction tube and dissolved in 10 mL of degassed toluene. The solution was slowly warmed up to 110 °C and kept stirring for 2 days. After cooling back to room temperature, the volatile materials were removed under high vacuum. The solids left were

further purified through column chromatography with chloroform and methanol as the eluent solvents. The pure product was isolated as a blue solid. Yield: 147 mg, 71%. ^1H NMR (CDCl_3 , 500 MHz): δ = 8.22 (d, 3J = 6.0 Hz, 4H, Np), 8.13 (d, 3J = 3.0 Hz, d, 2H, Th), 7.84 (dd, 4H, Np), 6.87 (d, 3J = 2.0 Hz, 2H, Th), 3.42 (br, 4H, CH_2), 2.73 (s, 6H, ThMe), 1.68 (br, 2H, CH), 1.4-1.0 (m, 48H, CH_2), 0.90 (t, 12H, Me).

TM2-BFI exhibited two absorption bands in dilute chloroform solution similar to T2-BFI, one intense absorption with an absorption maximum (λ_{max}) at 411 nm which is due to the π - π^* transition of the traazabenzodifluoranthene diimide moiety, and a weak low energy absorption at λ_{max} = 585 nm which mainly arises from charge transfer from the central electron donating dithienylbenzene moiety to the naphthalene imide group. Comparably, the low energy absorption band was strongly red-shifted relative to that of T2-BFI due to the electron donating effect of the methyl groups. As a thin film, the low energy absorption, which was relatively more intense than in solution, was strongly red shifted. The optical band gap estimated from the absorption edge was 1.60 eV.

The electron affinity of TM2-BFI was characterized by cyclic voltammetry. TM2-BFI showed an unresolved quasi-reversible reduction wave at $E_{1/2}$ = -1.25 V vs. SCE. No apparent oxidation was observed during an anodic scan in the range up to 1.2 V vs. SCE. The LUMO energy level of TM2-BFI calculated from the reduction onset was -3.59 eV.

TM2-BFI showed excellent thermal properties. Thermal gravimetric analysis (TGA) shows that TM2-BFI was thermally stable up to 400 °C. No apparent thermal transition was observed for TM2-BFI based on differential scanning calorimetry (DSC) scans in the temperature range of 20 to 300 °C. The excellent thermal stability of TM2-BFI is highly advantageous for applications in durable and robust organic electronics.

EXAMPLE 12B – Synthesis and Characteristics of Compound TM2-BFI

Under protection of argon, Br2-BFI (200 mg, 0.14 mmol), trimethyl(5-methylthiophen-2-yl)stannane (74 mg, 0.28 mmol), $\text{Pd}(\text{dba})_2$ (3 mg) and $\text{P}(o\text{-tol})_3$ (6 mg) were charged into a reaction tube and dissolved in 10 mL of degassed toluene. The solution was slowly warmed up to 110 °C and kept stirring for 2 days. After cooling back to room temperature, the volatile materials were removed under high vacuum. The solids left were further purified through column chromatography with chloroform and methanol (400:1 v/v) as the eluent solvents (R_f = 0.29). The pure product was isolated as a blue solid. Yield: 147 mg, 71%. ^1H NMR (CDCl_3 , 25 °C, 500 MHz): δ = 8.11 (d, 4H, 3J = 6.0 Hz, Np), 8.06 (d, 2H,

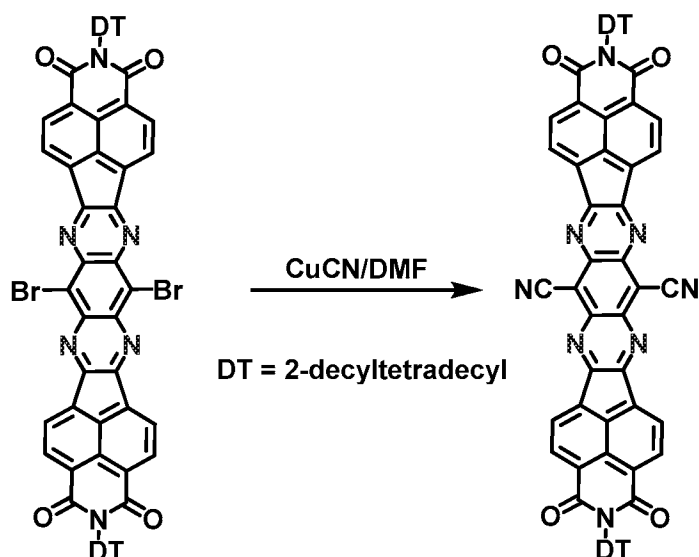
$^3J = 3.0$ Hz, Th), 7.71 (d, 4H, $^3J = 6.0$ Hz, Np), 6.78 (d, 2H, $^3J = 2.0$ Hz, Th), 3.28 (br, 4H, CH₂), 2.65 (s, 6H, Me), 1.59 (m, 2H, CH), 1.4-1.0 (m, 80H, CH₂), 0.85 ppm (m, 12H, Me). ^{13}C NMR (CDCl₃, 25 °C, 500 MHz): 162.8, 151.5, 146.3, 136.5, 135.8, 135.6, 135.4, 132.1, 131.9, 130.3, 125.0, 124.5, 123.7, 122.7, 44.1, 36.9, 32.2, 31.7, 30.3, 30.0, 29.9, 29.6, 26.6, 22.9, 15.7, 14.4 ppm; HRMS (m/z): [M]⁺ calcd. for C₉₂H₁₁₆N₆O₄S₂, 1434.07; found, 1433.81; elemental analysis calcd for C₉₂H₁₁₆N₆O₄S₂: C 77.05%, H 8.15%, N 5.86%; found C 77.23%, H 8.16%, N 5.91%.

EXAMPLE 13 – Transistors Based on Compound TM2-BFI

Field-effect transistors were fabricated on a heavily n-doped silicon substrate with thermally grown silicon dioxide gate insulator (200 nm; capacitance density, $C_i = 17$ nF/cm²). Photolithographically defined gold patterns (40 nm) with chromium adhesive layer (2 nm) acted as the source and drain electrodes in the bottom-contact/bottom-gate transistors, forming the channel width (W) of 800 μm and length (L) of 40 μm (W/L = 20). The substrates were cleaned by ultrasonication with acetone and isopropyl alcohol and dried by flow of nitrogen. The surface of a silicon dioxide substrate was further cleaned by plasma and treated with octyltrichlorosilane (OTS8) to form a hydrophobic self-assembled monolayer (SAM). TM2-BFI was deposited onto the substrate by spin-coating from a solution in chloroform. The devices were annealed at various temperatures under argon environment. Electrical characteristics of the devices were measured using an HP4145B semiconductor parameter analyzer under nitrogen atmosphere.

The charge carrier mobilities were calculated from transfer curves using the standard saturation equation of metal-oxide-semiconductor field-effect transistors:
$$I_{ds} = (\mu W C_o / 2L)(V_g - V_t)^2$$
 (Kang, S.-M.; Leblebici, Y. *CMOS Digital Integrated Circuits: Analysis and Design*, McGraw-Hill, New York, 1996.) The electron mobility of 0.028 cm² V⁻¹ s⁻¹ and hole mobility of 0.00036 cm² V⁻¹ s⁻¹ were obtained for transistors based on TM2-BFI.

EXAMPLE 14A – Synthesis and Characteristics of Compound CN2-BFI



Under protection of argon, compound 6 (200 mg, 0.14 mmol), CuCN (62.3 mg, 0.7 mmol) were charged into a reaction tube and suspended in 20 mL of degassed DMF. The mixture was slowly warmed up to 110 °C to 130 °C and kept stirring for 2 days. After cooling back to room temperature, the volatile materials were removed under high vacuum. The solids left were further purified through column chromatography with chloroform and methanol as the eluent solvents. The pure product was isolated as a yellow solid. Yield: 83mg, 46%. ¹H NMR (CDCl₃, 500 MHz): δ = 8.77 (d, ³J = 7.0 Hz, 4H, Np), 8.70 (d, ³J = 7.0 Hz, Np), 4.15 (d, ³J = 7.5 Hz, 4H, CH₂), 2.0 (Br, 12H, CH), 1.45-1.0 (m, 48H, CH₂), 0.90 (t, 12H, Me).

CN2-BFI exhibited two absorption bands in dilute chloroform solution similar to BFI. The optical band gap estimated from the absorption edge was 2.50 eV.

The electron affinity of CN2-BFI was characterized by cyclic voltammetry. CN2-BFI showed an quasi-reversible reduction wave at $E_{1/2} = -0.35$ V vs. SCE. No apparent oxidation was observed during an anodic scan in the range up to 1.2 V vs. SCE. The LUMO energy level of CN2-BFI calculated from the reduction onset was -4.3 eV.

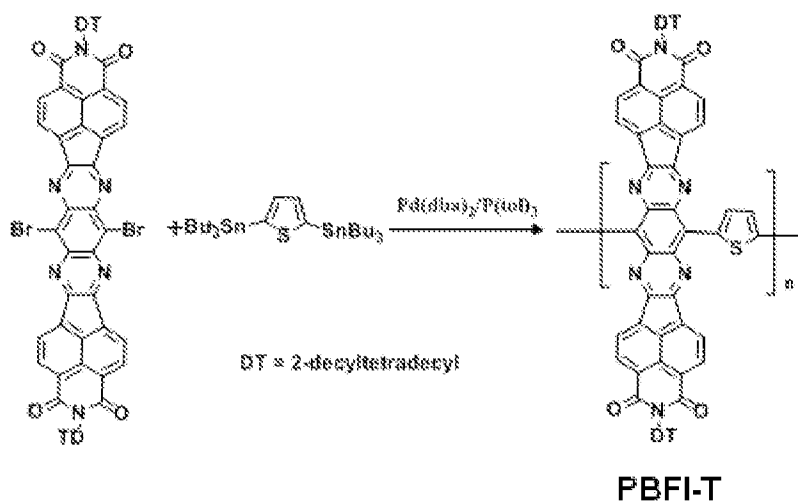
CN2-BFI showed excellent thermal properties. Thermal gravimetric analysis (TGA) shows that CN2-BFI was thermally stable up to 420 °C. No apparent thermal transition was observed for CN2-BFI based on differential scanning calorimetry (DSC) scans in the temperature range of 20 to 300 °C. The excellent thermal stability of CN2-BFI is highly advantageous for applications in durable and robust organic electronics.

EXAMPLE 14B – Synthesis and Characteristics of Compound CN2-BFI

Under protection of argon, Br₂-BFI (200 mg, 0.14 mmol), CuCN (62.3 mg, 0.7 mmol) were charged into a reaction tube and suspended in 20 mL of degassed DMF. The mixture was slowly warmed up to 110 °C to 130 °C and kept stirring for 2 days. After cooling back to room temperature, the volatile materials were removed under high vacuum. The solids left were further purified through column chromatography with chloroform and methanol (50:1 v/v) as the eluent solvents (*R_f* = 0.34). The pure product was isolated as a yellow solid. Yield: 83 mg, 46%. ¹H NMR (CDCl₃, 25 °C, 500 MHz): δ = 8.74 (d, ³J = 7.5 Hz, 4H, Np), 8.66 (d, 4H, ³J = 7.5 Hz, Np), 4.11 (d, ³J = 7.0 Hz, 4H, CH₂), 1.97 (br, 2H, CH), 1.45-1.0 (m, 80H, CH₂), 0.86 ppm (t, 12H, Me); ¹³C NMR (CDCl₃, 25 °C, 500 MHz): 163.1, 157.7, 141.4, 137.6, 134.0, 132.9, 126.2, 125.3, 117.0, 112.9, 45.2, 37.0, 32.2, 31.9, 30.3, 29.0, 29.6, 26.7, 22.9, 14.4 ppm; HRMS (*m/z*): [*M*]⁺ calcd. for C₈₄H₁₀₆N₈O₄, 1290.83; found, 1290.88; elemental analysis calcd for C₈₄H₁₀₆N₈O₄: C 78.10%, H 8.27%, N 8.67%; found C 78.37%, H 8.59%, N 8.02%.

PART III

EXAMPLE 15 – Synthesis and Characteristics of Polymer PBFI-T



Compound 6 (Br₂-BFI) (100 mg, 0.07 mmole) and 2,5-bis(tributylstannyl)thiophene (47.3 mg, 0.07 mmole) were dissolved in 12 mL of anhydrous toluene and purged with Ar for 10 min. A solution of Pd(dba)₂ (3 mg) and P(o-tol)₃ (6 mg) was added to the monomer solution. Pd(dba)₂, P(o-tol)₃ and 2,5-bis(tributylstannyl)thiophene were purchased from Aldrich and used as received.

The mixture was slowly heated to 110 °C and kept stirring at the temperature for 3 days. After cooling back to room temperature, the volatile materials were evaporated and the solids were dissolved in 6 mL of toluene and precipitated into 100 mL of methanol and concentric HCl mixed solvents (20v:1v). The green solid was collected by filtration and further purified by successive Soxhlet extraction with methanol, acetone and hexanes. Yield: (75 mg, 79.5%). GPC (at 60 °C in Chlorobenzene, against polystyrene standards) $M_w = 175,000$, PDI = 3.68.

Polymer PBFI-T exhibited good solubility in common organic solvent including chloroform, dichloromethane, chlorobenzene, dichlorobenzene, toluene, etc. As a result, it is suitable for solution processing (e.g., drop casting, spin coating, etc.) of thin films.

Polymer PBFI-T exhibited two absorption bands in a dilute chloroform solution: one intense high energy absorption at around $\lambda_{\max} = 378$ nm and a relatively weak low energy absorption band at $\lambda_{\max} = 700$ nm. There was no significant change for the high energy absorption band from the dilute solution to the thin films, but the low energy absorption was strongly red shifted due to more efficient intra- and inter-molecular charge transfer and inter-chain interaction. The optical band gap estimated from the absorption edge was 1.24 eV.

The electron affinity of PBFI-T was evaluated by cyclic voltammetry. BFI showed an unresolved quasi-reversible reduction waves at $E_{1/2} = -1.10$ V vs SCE. No apparent oxidation was observed during an anodic scan up to 1.2 V vs. SCE. Based on the onsets of reduction waves, the LUMO energy level of PBFI-T was estimated to be -3.80 eV.

The thermal behavior of BFI was investigated by thermogravimetric analysis (TGA) and differential scanning calorimetry (DSC). No apparent thermal transition was observed based on DSC scans in the temperature range of 30 to 300°C. TGA shows that BFI was thermally stable up to 450 °C. The excellent thermal stability of PBFI-T is highly advantageous for fabricating durable and robust organic electronics.

The x-ray diffraction patterns of a thin film of PBFI-T drop-casted on the glass substrate show strong first Bragg reflection indexed to the (100) plane and its weak second order (200) reflection at 3.35° and 6.5°, respectively indicative an edge-on-edge lamella packing (Figure 2).

EXAMPLE 16 – Transistors Based on Polymer PBFI-T

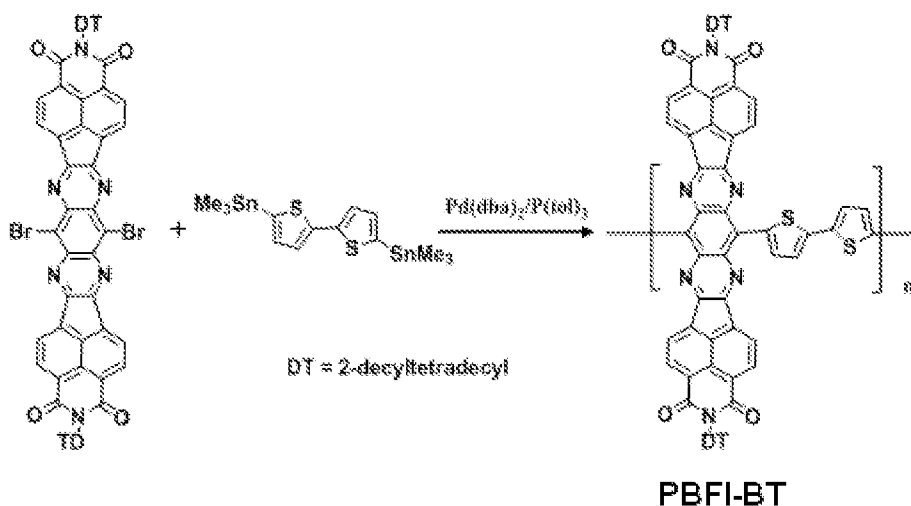
A heavily n-doped silicon substrate with a thermally grown silicon dioxide layer (200 nm; capacitance density, $C_i = 17$ nF/cm²) acted as a gate electrode and a gate insulator, respectively. The substrates were cleaned by ultrasonication in acetone and isopropyl alcohol

(30 min each) and dried by a flow of nitrogen gas. The surface of a silicon dioxide substrate was further cleaned by air-plasma (4 min) and further hydrophobically modified by either a monolayer of octyltrichlorosilane (OTS8), or a thin film of polymer insulators such as an amorphous fluoro-polymer (CYTOP) or cross-linked benzocyclobutene (BCB). A thin film of PBFI-T was deposited onto the modified substrate by simple spin-coating from a solution in dichloromethane (DCM) with a 10 vol% of 1,2-dichlorobenzene (ODCB). The thin films were annealed at various temperatures for 10 min on a hot-plate under argon environment. Source-drain electrodes (40 nm) were deposited onto the polymer films by vacuum thermal evaporation of gold or silver through a shadow mask, defining a channel width (W) of 1000 μm and a length (L) of 100 μm . Current-voltage (I-V) characteristics of the transistors were measured under nitrogen atmosphere by using a Signatone probe station and an HP4145B semiconductor parameter analyzer controlled by locally written LabView codes through a GPIB interface.

The charge carrier mobilities were calculated from transfer curves using the standard saturation equation of metal-oxide-semiconductor field-effect transistors:

$I_{ds} = (\mu W C_o / 2L)(V_g - V_t)^2$. (Kang, S.-M.; Leblebici, Y. *CMOS Digital Integrated Circuits: Analysis and Design*, McGraw-Hill, New York, 1996.) The electron mobility of $0.3 \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1}$ was obtained (The average saturation mobility of the devices with 100 nm-thick silver electrodes was $0.18 \pm 0.04 \text{ cm}^2/\text{Vs}$.), with an on/off current ratio of 10^5 . The transistor characteristic curves of an n-channel field-effect transistor based on PBFI-T are shown in Figure 3A and 3B. The electron mobility was slightly dependent on the annealing temperature (150–300 °C) and the electrode metal (Figure 4). Mobility was higher than, for example, mobilities reported in Examples 8 and 10.

Complementary Invertors using PBFI-T as the n-channel component. Complementary inverters were fabricated by connecting n-channel PBFI-T OFETs with p-channel PSOxTT (see WO 2011/051292) OFETs. PSOxTT thin film was deposited by spin-coating from a solution in 1,2-dichlorobenzene (4–8 mg/mL) onto an OTS8-treated substrate. A voltage sweeping step was set to 0.1 V for the complementary inverter characterization. The current–voltage curves of constituent PBFI-T and PSOxTT OFETs (Figure 5) showed comparable on-current and off-current, suggesting the operation of the inverter would be symmetric. By having same device architectures (i.e., 200 nm-thick SiO_2 with OTS8 and gold electrodes with W/L=10) for both transistors, the complementary inverters showed ideal switching characteristics with trip voltage at the half of supply voltage (V_{DD}) and voltage gain of 107 when V_{DD} =80 V (Figure 6).

EXAMPLE 17 – Synthesis and Characteristics of Polymer PBFI-BT

PBFI-BT was synthesized and purified similarly to PBFI-T by using compound 6 (Br2-BFI) (200 mg, 0.14 mmol), 2,2'-bis(trimethylstannyl)-4,4'-bithiophene (69 mg, 0.14 mmol), 30 mL of toluene, Pd(dba)₂ (6 mg) and P(o-tol)₃ (12 mg). Yield: (141, 71.1%). Pd(dba)₂, P(o-tol)₃ and 2,2'-bis(trimethylstannyl)-4,4'-bithiophene were purchased from Aldrich and used as received.

PBFI-BT exhibited similar absorption as PBFI-T, and showed one intense high energy absorption band and one broad low energy absorption band. The low energy band of PBFI-BT was more strongly red-shifted compare to that of PBFI-T and showed at about $\lambda_{\max}$ = 1000 nm for dilute chloroform solution and at about 1100 nm for the thin film. The optical band gap of PBFI-BT was estimated to be 0.95 eV.

PBFI-BT showed a quasi-reversible reduction at $E_{1/2}$ = -1.08 V and a relatively weak oxidation wave at E_p = 0.8 V. The HOMO and LUMO energy levels estimated from the oxidation and reduction onsets were -5.16 eV and -3.70 eV, respectively.

PBFI-BT also exhibited good thermal stability. No thermal transition up to 300 °C was observed during a DSC scan. TGA showed that PBFI-BT was thermally stable up to 450 °C.

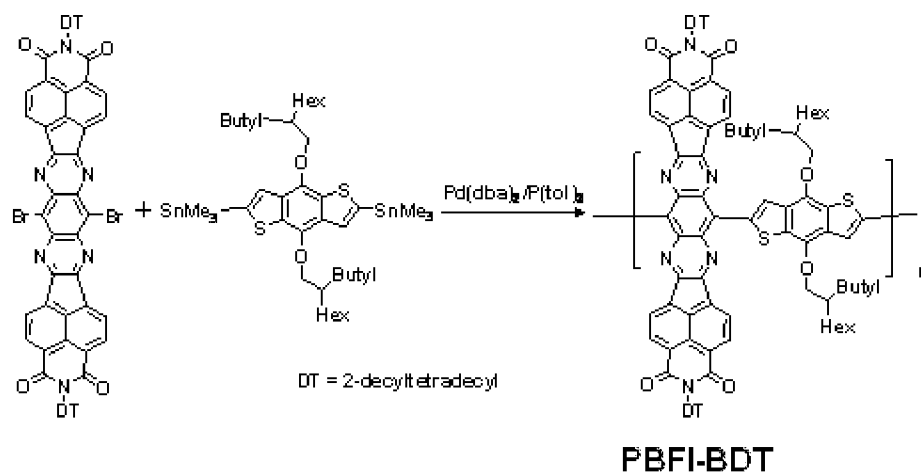
EXAMPLE 18 – Transistors Based on Polymer PBFI-BT

A heavily n-doped silicon substrate with a thermally grown silicon dioxide layer (200 nm; capacitance density, C_i = 17 nF/cm²) acted as a gate electrode and a gate insulator, respectively. The substrates were cleaned by ultrasonication in acetone and isopropyl alcohol (30 min each) and dried by a flow of nitrogen gas. The surface of a silicon dioxide substrate was further cleaned by air-plasma (4 min) and treated with octyltrichlorosilane (OTS8) by

spin-coating from a chloroform solution (4 mM). The polymer semiconductor was deposited onto the substrate by drop casting from a suspension (10 mg/mL) in dichloromethane with 5–10 vol% of 1,2-dichlorobenzene. The thin films were annealed at various temperatures for 10 minutes on a hot-plate under argon environment. Source-drain electrodes (40 nm) were deposited onto the polymer films by vacuum thermal evaporation of gold or silver through a shadow mask, defining a channel width (W) of 1000 μm and a length (L) of 100 μm . Current-voltage (I-V) characteristics of the transistors were measured under nitrogen atmosphere by using a Signatone probe station and an HP4145B semiconductor parameter analyzer controlled by locally written LabView codes through a GPIB interface.

The charge carrier mobilities were calculated from transfer curves using the standard saturation equation of metal-oxide-semiconductor field-effect transistors:
 $I_{ds} = (\mu W C_{ox} / 2L) (V_g - V_t)^2$. (Kang, S.-M.; Leblebici, Y. *CMOS Digital Integrated Circuits: Analysis and Design*, McGraw-Hill, New York, 1996.) The electron mobility of $0.09 \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1}$ was obtained, with an on/off current ratio of 10^5 . The transistor characteristic curves of an ambipolar field-effect transistor based on PBFI-BT are shown in Figures 5C and 5D.

EXAMPLE 19 – Synthesis and Characteristics of Polymer PBFI-BDT



PBFI-BDT was synthesized and purified similarly to PBFI-T by using Compound 6 (Br2-BFI) (200 mg, 0.14 mmol), 2,2'-bis(trimethylstannyl)-4,8-di(2-butylhexyloxy) benzo[1,2-b;4,5-b']dithiophene (126 mg, 0.14 mmol), 30 mL of toluene, $\text{Pd}(\text{dba})_2$ (6 mg) and $\text{P}(\text{o-tol})_3$ (12 mg). Yield: (157, 62.3%). $\text{Pd}(\text{dba})_2$ and $\text{P}(\text{o-tol})_3$ were purchased from Aldrich and used as received. 2,2'-bis(trimethylstannyl)-4,8-di(2-butylhexyloxy) benzo[1,2-b;4,5-b']dithiophene was prepared according to reported procedures (Hundt *et al.*, *Org. Lett.* **2009**,

11, (19), 4422-4425.). GPC (at 60 °C in Chlorobenzene, against polystyrene standards) $M_w = 175,000$, PDI = 4.34.

PBFI-BDT exhibited good solubility in common organic solvents such as chloroform, dichloromethane, chlorobenzene, dichlorobenzene, toluene, etc. As a result, it is suitable for solution processing (e.g., spin coating, drop casting, etc.) of thin films.

PBFI-BDT exhibited similar absorption as PBFI-T and PBFI-BT, and showed an intense high energy absorption band at $\lambda_{max} = 390$ nm and unresolved broad low energy absorption ranging from 550 nm to 1150 nm. The optical band gap calculated from the absorption edge was 0.92 eV.

PBFI-BDT exhibited good thermal stability. No apparent thermal transition was observed during a DSC scan in a temperature range from 30 °C to 300 °C. TGA showed that PBFI-BDT was thermally stable up to 440 °C.

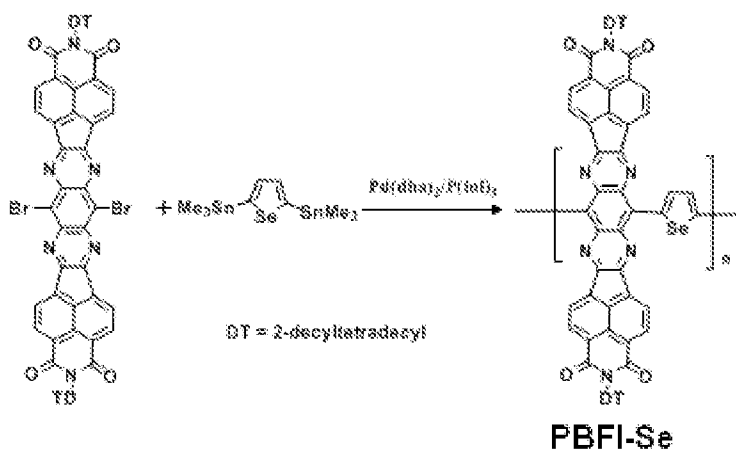
EXAMPLE 20— Transistors Based on Polymer PBFI-BDT

Field-effect transistors were fabricated on a heavily n-doped silicon substrate with thermally grown silicon dioxide gate insulator (200 nm; capacitance density, $C_i = 17$ nF/cm²). Photolithographically defined gold patterns (40 nm) with chromium adhesive layer (2 nm) acted as the source and drain electrodes in the bottom-contact/bottom-gate transistors, forming the channel width (W) of 800 μ m and length (L) of 40 μ m (W/L = 20). The substrates were cleaned by ultrasonication with acetone and isopropyl alcohol and dried by flow of nitrogen. The surface of a silicon dioxide substrate was further cleaned by plasma and treated with octyltrichlorosilane (OTS8) to form a hydrophobic self-assembled monolayer (SAM). PBFI-BDT was deposited onto the substrate by spin-coating from a solution in chloroform. The devices were annealed at various temperatures under argon environment. Electrical characteristics of the devices were measured using an HP4145B semiconductor parameter analyzer under nitrogen atmosphere.

The charge carrier mobilities were calculated from transfer curves using the standard saturation equation of metal-oxide-semiconductor field-effect transistors:

$I_{ds} = (\mu W C_o / 2L)(V_g - V_t)^2$. (Kang, S.-M.; Leblebici, Y. CMOS Digital Integrated Circuits: Analysis and Design, McGraw-Hill, New York, 1996.) An electron mobility of 1.3×10^{-3} cm² V⁻¹ s⁻¹ and a hole mobility of 1.5×10^{-4} cm² V⁻¹ s⁻¹ were obtained for transistors based on PBFI-BDT.

EXAMPLE 21 – Synthesis and Characteristics of Polymer PBFI-Se



PBFI-Se was synthesized and purified similarly to PBFI-T by using compound 6 (Br2-BFI) (200 mg, 0.14 mmole) and 2,5-bis(trimethylstannyl)selenophene (65 mg, 0.14 mmole) Yield: (126 mg, 64.4%). Pd(bda)₂ and P(o-tol)₃ were purchased from Aldrich and used as received. 2,5-bis(trimethylstannyl)selenophene was synthesized according to reported procedures (Chen, C.-H.; et al, *Macromolecules* **2009**, 43, (2), 697-708.). GPC (at 60 °C in Chlorobenzene, against polystyrene standards) Mw = 104,000, PDI = 3.55.

PBFI-Se exhibited good solubility in common organic solvent including chloroform, dichloromethane, chlorobenzene, dichlorobenzene, toluene, etc. As a result, it is suitable for solution processing (e.g., drop casting, spin coating, etc.) of thin films.

PBFI-Se exhibited similar absorption as PBFI-T both in a dilute chloroform solution and as thin films: one intense high energy absorption at around $\lambda_{\text{max}} = 378$ nm and a relatively weak low energy absorption band at $\lambda_{\text{max}} = 900$ nm. There was no significant change for the high energy absorption band from the dilute solution to the thin films, but the low energy absorption was strongly red shifted due to more efficient intra- and inter-molecular charge transfer and inter-chain interaction. The optical band gap estimated from the absorption edge was 1.08 eV.

The thermal behavior of PBFI-Se was investigated by thermogravimetric analysis (TGA) and differential scanning calorimetry (DSC). No apparent thermal transition was observed based on DSC scans in the temperature range of 30 to 300°C. TGA shows that PBFI-Se was thermally stable up to 430 °C. The excellent thermal stability of PBFI-Se is highly advantageous for fabricating durable and robust organic electronics.

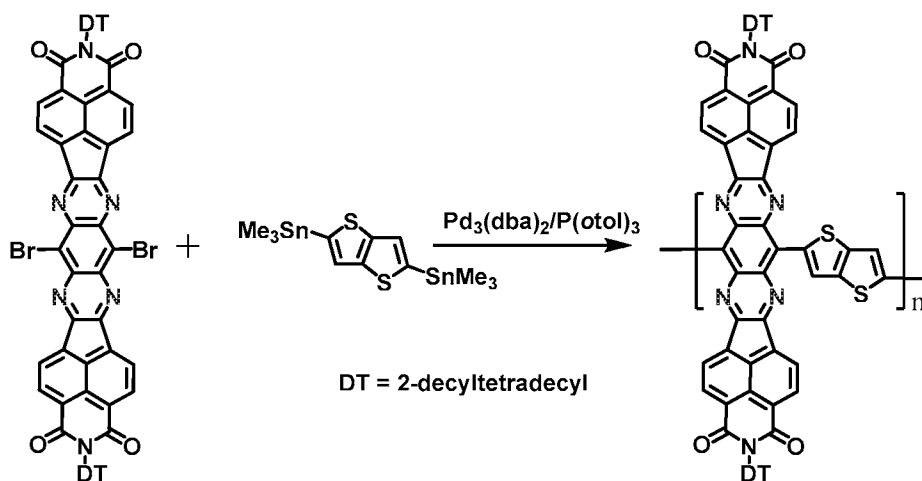
EXAMPLE 22 – Transistors Based on Polymer PBFI-Se

A heavily n-doped silicon substrate with a thermally grown silicon dioxide layer (200 nm; capacitance density, $C_i = 17$ nF/cm²) acted as a gate electrode and a gate insulator,

respectively. The substrates were cleaned by ultrasonication in acetone and isopropyl alcohol (30 min each) and dried by a flow of nitrogen gas. The surface of a silicon dioxide substrate was further cleaned by air-plasma (4 min) and treated with octyltrichlorosilane (OTS8) by spin-coating from a chloroform solution (4 mM). The polymer semiconductor was deposited onto the substrate by spin-coating at 3 krpm for 60 s from a solution (10 mg/mL) in dichloromethane with 5–10 vol% of 1,2-dichlorobenzene. The thin films were annealed at various temperatures for 10 min on a hot-plate under argon environment. Source-drain electrodes (40 nm) were deposited onto the polymer films by vacuum thermal evaporation of gold or silver through a shadow mask, defining a channel width (W) of 1000 μm and a length (L) of 100 μm . Current-voltage (I-V) characteristics of the transistors were measured under nitrogen atmosphere by using a Signatone probe station and an HP4145B semiconductor parameter analyzer controlled by locally written LabView codes through a GPIB interface.

The charge carrier mobilities were calculated from transfer curves using the standard saturation equation of metal-oxide-semiconductor field-effect transistors:
 $I_{\text{ds}} = (\mu W C_{\text{ox}} / 2L)(V_{\text{g}} - V_{\text{t}})^2$. (Kang, S.-M.; Leblebici, Y. *CMOS Digital Integrated Circuits: Analysis and Design*, McGraw-Hill, New York, 1996.) The electron mobility of 0.0053 $\text{cm}^2 \text{V}^{-1} \text{s}^{-1}$ was observed, with an on/off current ratio of 10^5 .

EXAMPLE 23 – Synthesis and Characteristics of Polymer PBFI-TT



PBFI-TT was synthesized and purified similarly to PBFI-T by using compound 6 (Br2-BFI) (100 mg, 0.07 mmole) and 2,5-bis(trimethylstannyl)thieno[3,2-b]thiophene (32.5 mg, 0.07 mmole) Yield: (68 mg, 75%). GPC (at 60 °C in Chlorobenzene, against polystyrene standards) $M_w = 136,000$, PDI = 12.8.

PBFI-TT exhibited good solubility in common organic solvent including chloroform, dichloromethane, chlorobenzene, dichlorobenzene, toluene, etc. As a result, it is suitable for solution processing (e.g., drop casting, spin coating, etc.) of thin films.

PBFI-TT exhibited similar absorption as PBFI-T both in a dilute chloroform solution and as thin films: one intense high energy absorption at around $\lambda_{\text{max}} = 388 \text{ nm}$ and a relatively weak low energy absorption band at $\lambda_{\text{max}} = 700 \text{ nm}$. The optical band gap estimated from the absorption edge was 1.19 eV.

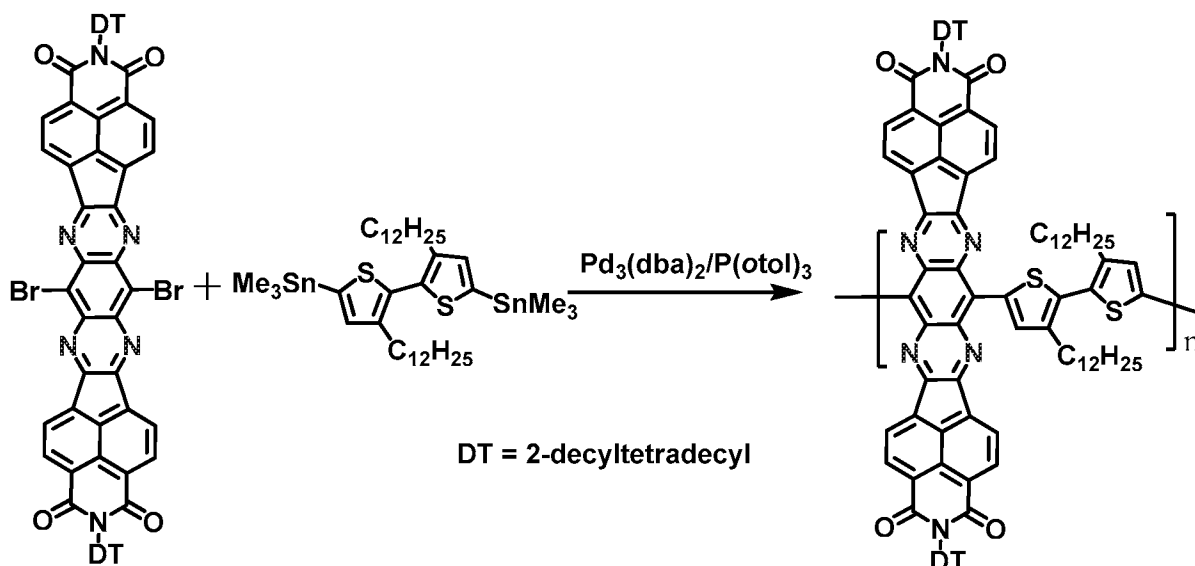
The thermal behavior of PBFI-Se was investigated by thermogravimetric analysis (TGA) and differential scanning calorimetry (DSC). No apparent thermal transition was observed based on DSC scans in the temperature range of 30 to 300°C. TGA shows that PBFI-Se was thermally stable up to 438 °C. The excellent thermal stability of PBFI-TT is highly advantageous for fabricating durable and robust organic electronics.

EXAMPLE 24 – Transistors Based on Polymer PBFI-TT

A heavily n-doped silicon substrate with a thermally grown silicon dioxide layer (200 nm; capacitance density, $C_i = 17 \text{ nF/cm}^2$) acted as a gate electrode and a gate insulator, respectively. The substrates were cleaned by ultrasonication in acetone and isopropyl alcohol (30 min each) and dried by a flow of nitrogen gas. The surface of a silicon dioxide substrate was further cleaned by air-plasma (4 min) and treated with octyltrichlorosilane (OTS8) by spin-coating from a chloroform solution (4 mM). The polymer semiconductor was deposited onto the substrate by spin-coating at 3 krpm for 60 s from a solution (10 mg/mL) in dichloromethane with 5–10 vol% of 1,2-dichlorobenzene. The thin films were annealed at various temperatures for 10 min on a hot-plate under argon environment. Source-drain electrodes (40 nm) were deposited onto the polymer films by vacuum thermal evaporation of gold or silver through a shadow mask, defining a channel width (W) of 1000 μm and a length (L) of 100 μm . Current-voltage (I-V) characteristics of the transistors were measured under nitrogen atmosphere by using a Signatone probe station and an HP4145B semiconductor parameter analyzer controlled by locally written LabView codes through a GPIB interface.

The charge carrier mobilities were calculated from transfer curves using the standard saturation equation of metal-oxide-semiconductor field-effect transistors:

$I_{\text{ds}} = (\mu W C_{\text{ox}} / 2L)(V_{\text{g}} - V_{\text{t}})^2$. (Kang, S.-M.; Leblebici, Y. *CMOS Digital Integrated Circuits: Analysis and Design*, McGraw-Hill, New York, 1996.) The electron mobility of $0.037 \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1}$ was observed, with an on/off current ratio of 10^5 .

EXAMPLE 25 – Synthesis and Characteristics of Polymer PBFI-BTDD

PBFI-BTDD was synthesized and purified similarly to PBFI-BTDD by using compound 6 (Br₂-BFI) (100 mg, 0.07 mmole) and (3,3'-didodecyl-2,2'-bithiophene-5,5'-diyl)bis(trimethylstannane) (116.2 mg, 0.14 mmole) Yield: (167 mg, 68.4%). GPC (at 60 °C in Chlorobenzene, against polystyrene standards) Mw = 73,000, PDI = 2.08.

PBFI-BTDD exhibited good solubility in common organic solvent including chloroform, dichloromethane, chlorobenzene, dichlorobenzene, toluene, etc. As a result, it is suitable for solution processing (e.g., drop casting, spin coating, etc.) of thin films.

The thermal behavior of PBFI-BTDD was investigated by thermogravimetric analysis (TGA) and differential scanning calorimetry (DSC). No apparent thermal transition was observed based on DSC scans in the temperature range of 30 to 300°C. TGA shows that PBFI-BTDD was thermally stable up to 437 °C. The excellent thermal stability of PBFI-BTDD is highly advantageous for fabricating durable and robust organic electronics.

EXAMPLE 26 – Transistors Based on Polymer PBFI-BTDD

A heavily n-doped silicon substrate with a thermally grown silicon dioxide layer (200 nm; capacitance density, $C_i = 17 \text{ nF/cm}^2$) acted as a gate electrode and a gate insulator, respectively. The substrates were cleaned by ultrasonication in acetone and isopropyl alcohol (30 min each) and dried by a flow of nitrogen gas. The surface of a silicon dioxide substrate was further cleaned by air-plasma (4 min) and treated with octyltrichlorosilane (OTS8) by spin-coating from a chloroform solution (4 mM). The polymer semiconductor was deposited onto the substrate by spin-coating at 3 krpm for 60 s from a solution (10 mg/mL) in dichloromethane with 5–10 vol% of 1,2-dichlorobenzene. The thin films were annealed at

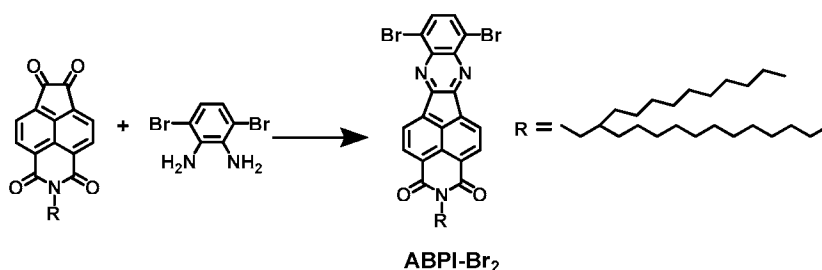
various temperatures for 10 min on a hot-plate under argon environment. Source-drain electrodes (40 nm) were deposited onto the polymer films by vacuum thermal evaporation of gold or silver through a shadow mask, defining a channel width (W) of 1000 μm and a length (L) of 100 μm . Current-voltage (I-V) characteristics of the transistors were measured under nitrogen atmosphere by using a Signatone probe station and an HP4145B semiconductor parameter analyzer controlled by locally written LabView codes through a GPIB interface.

The charge carrier mobilities were calculated from transfer curves using the standard saturation equation of metal-oxide-semiconductor field-effect transistors:

$I_{ds} = (\mu W C_{ox} / 2L)(V_g - V_t)^2$. (Kang, S.-M.; Leblebici, Y. *CMOS Digital Integrated Circuits: Analysis and Design*, McGraw-Hill, New York, 1996.) The electron mobility of $0.024 \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1}$ and a hole mobility of $0.00072 \text{ cm}^2/\text{Vs}$ were obtained

PART IV

EXAMPLE 27– Synthesis of Monomer ABPI-Br₂



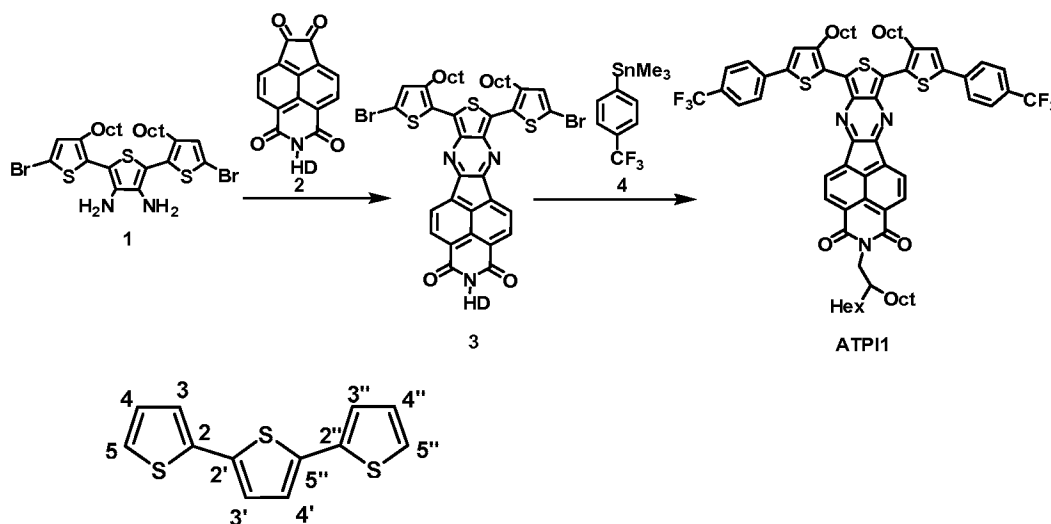
At 0 °C, NaBH₄ (1.6 g, 43.2 mmole) was added in portions to the suspension of 4,7-dibromobenzo[c][1,2,5]thiadiazole (1.0 g, 3.4 mmole, purchased from Sigma-Aldrich) in ethanol. The mixture was allowed to warm up to room temperature. After stirring over night, the reaction was quenched with water. The organic phase was extracted with ether and followed with a standard aqueous work up. The volatile materials were removed in vacuo and the product was isolated as a white solid. Without further purification, the crude material was used in the next step. Yield: 750 mg (82.9%).

Inside a reaction tube, 3,6-dibromobenzene-1,2-diamine (112 mg, 0.42 mmole) and 2-(2-decyltetradecyl)-1H-indeno[6,7,1-def]isoquinoline-1,3,6,7(2H)-tetraone (200 mg, 0.42 mmole, synthesized according to Example 1) were suspended in 5 mL of ethanol. The mixture was heated to reflux and kept stirring at the temperature for 48 hours. After cooling back to room temperature, the yellow precipitate was collected by filtration. The crude materials were purified by column chromatography on silica gel with using hexanes and CHCl₃ mixed solvents as the eluent. Yield: 254 mg (85.8%). ¹H NMR (CDCl₃, 500 MHz): δ

= 8.75 (d, 2H, 3J = 7.0 Hz, Nh), 8.65 (d, 2H, 3J = 7.0 Hz, Nh), 8.00 (s, 2H, Ph), 4.18 (d, 2H, 3J = 7.0 Hz, CH₂), 2.02 (m, 1H, CH), 1.5-1.3 (m, 40H, CH₂), 0.87 (m, 6H, Me). HRMS (m/z): [M]⁺ calcd. for C₄₄H₅₅Br₂N₃O₂, 817.73; found, 818.23.

EXAMPLE 28 – Synthesis of Compound ATP11

Tri-*o*-tolylphosphine, bis(dibenzylideneacetone) palladium (0) (Pd(dba)₂), 4,7-dibromobenzo[c][1,2,5]thiadiazole and 2,5-dibromo-3,4-dinitrothiophene were purchased from Aldrich and used as received. 3',4'-dinitro-3,3''-dioctyl-2,2':5',2''-terthiophene (Beaupre, S. *Chem. Mater.* **2009**, 21, 1504–1513), 2-hexyl-1-decylamine (Guo, X.; et al, *Org. Lett.* **2008**, 10, (23), 5333-5336) and 1,4-dibromobenzene-2,3-diamine (Hong, D.-J.; et al, *Chem. Commun.* **2010**, 46, (27), 4896-4898) were synthesized according to reported procedures.



5,5''-dibromo-3',4'-dinitro-3,3''-dioctyl-2,2':5',2''-terthiophene. At room temperature, 3',4'-dinitro-3,3''-dioctyl-2,2':5',2''-terthiophene (562 mg, 1.0 mmole) was suspended in CHCl₃ and trifluoroacetic acid mixed solvents. N-bromosuccinimide (400 mg, 2.25 mmole) was added in portions. The mixture was kept stirring over night and slowly warmed up to 45 to 50 °C. After stirring for additional 12 hours, the reaction was quenched by water followed by a standard aqueous work-up. The crude materials were purified by column chromatography on silica gel with using hexanes and ethyl acetate mixed solvents as the eluent. Yield: 342 mg (47.6%). ¹H NMR (CDCl₃, 500.046 MHz): δ = 7.02 (s, 2H, Th), 2.54 (t, 4H, CH₂), 1.58 (m, 4H, CH₂), 1.4-1.2 (t, 20H, CH₂), 0.9 (m, 6H, Me).

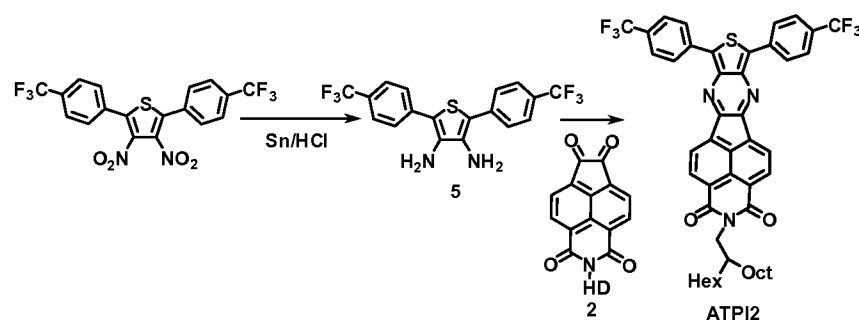
Compound 1 (3',4'-diamino-5,5''-dibromo-3,3''-dioctyl-2,2':5',2''-terthiophene). 5,5''-dibromo-3',4'-dinitro-3,3''-dioctyl-2,2':5',2''-terthiophene (180 mg, 0.25 mmole) was suspended in 6 mL of ethanol and 5.5 mL of HCl mixture under argon. To the mixture, Sn

(1.28 g, 10.7 mmole) was added in portions. After stirring at room temperature over night, the mixture was neutralized with KOH (25%). The organic phase was extracted with ethyl acetate. The crude materials were directly used in the next step without further purification.

Compound 3. Inside a reaction tube, Compound **1** (147 mg, 0.22 mmole) and Compound **2** (105 mg, 0.22 mmole, synthesized according to Example 1) were suspended in 5 mL of ethanol. The mixture was heated to reflux and kept stirring at the temperature for 48 hours. After cooling back to room temperature, the blue precipitate was collected by filtration and further purified through column chromatography on silica gel. Yield: 172 mg (70%). ^1H NMR (CDCl_3 , 300 MHz): δ = 9.50 (d, 2H, 3J = 7.0 Hz, Np), 8.04 (d, 2H, 3J = 7.0 Hz, Np), 6.68 (s, 2H, Th), 4.14 (q, 2H, CH_2), 2.58 (t, 4H, CH_2), 2.01 (m, 1H, CH), 1.61 (m, 4H, CH_2), 1.5-1.2 (m, 44H, CH_2), 1.0-0.8 (m, 12H, Me).

ATPI1. Compound **3** (110 mg, 0.1 mmole), trimethyl(4-trifluoromethyl) phenylstannane (74 mg, 0.24 mmole) and tetrakis(triphenylphosphine)palladium(0) (4.6 mg, 0.004 mmole) were dissolved in degassed toluene. The solution was heated to 100 to 110 $^\circ\text{C}$ and kept stirring for 24 hours. After cooling back to room temperature, the volatile materials were removed in vacuo. The solid residue was further purified by column chromatography on silica gel with hexanes and CHCl_3 mixed solvents as the eluent. The pure product was isolated as a green solid. Yield: 76 mg (61.7%). ^1H NMR (CDCl_3 , 500 MHz): δ = 8.35 (d, 2H, 3J = 7.0Hz, Np), 7.91 (d, 2H, 3J = 7.0Hz, Np), 7.61 (d, 4H, 3J = 8.0Hz, Ph), 7.52 (d, 4H, 3J = 8.0Hz, Ph), 6.91(s, 2H, Th), 3.93 (d, 2H, 3J = 7.0 Hz, CH_2), 2.46 (br, 4H, CH), 1.92 (m, 1H, CH), 1.5-1.2 (m, 48H, CH_2), 1.0-0.8 (m, 12H, Me); ^{13}C NMR (CDCl_3 , 125.7 MHz): 163.4, 151.9, 142.9, 142.3, 137.1, 136.8, 136.2, 136.1, 132.0, 129.0, 127.1, 126.1, 126.1, 126.0, 126.0, 125.1, 123.7, 121.3, 32.2, 32.1, 32.1, 31.9, 31.7, 30.5, 30.4, 30.1, 30.0, 29.9, 29.9, 29.7, 29.6, 26.7, 26.6, 22.9, 14.3, 14.3;

EXAMPLE 29 – Synthesis of Compound ATPI2

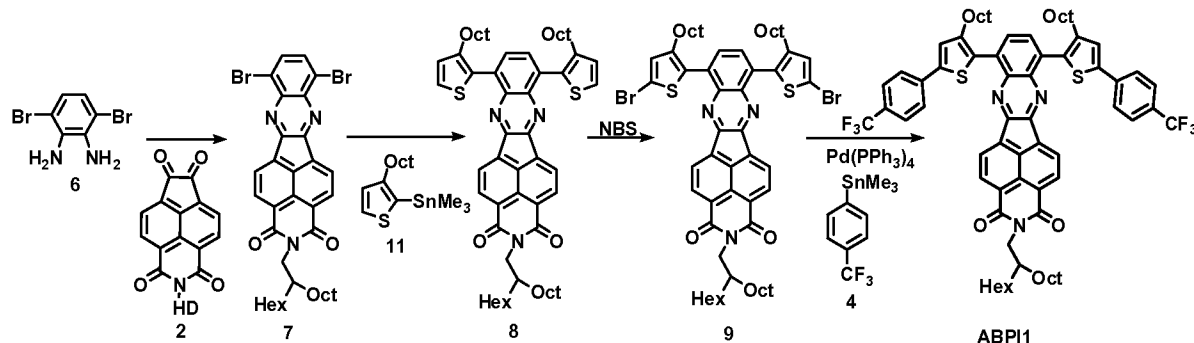


3,4-dinitro-2,5-bis(4-trifluoromethylphenyl)thiophene. The compound was prepared using 2,5-dibromo-3,4-dinitro-thiophene (332 mg, 1.0 mmole), trimethyl(4-trifluoromethyl)phenylstannane (741 mg, 2.4 mmole) and tetrakis(triphenylphosphine)palladium(0) (46 mg, 0.04 mmole). The crude materials were purified by column chromatography on silica gel with using hexanes and CHCl_3 mixed solvents as the eluent. Yield: 347 mg (75.1%). ^1H NMR (CDCl_3 , 500.046 MHz): δ = 7.81 (d, 3J = 8.0 Hz, 4H, Ph), 7.68 (d, 3J = 8.0 Hz, 4H, Ph).

Compound **5** (3,4-diamino-2,5-bis(4-trifluoromethylphenyl)thiophene). The compound was prepared similarly as 3',4'-diamino-5,5''-dibromo-2,2':5',2''-terthiophene, but using 4-dinitro-2,5-bis(4-trifluoromethylphenyl)thiophene (200 mg, 42.3 mmole), Sn (3.3 g, 27.7 mmole), 4.0 mL of ethanol and 5.0 mL of HCl.

ATPI2. ATPI2 was prepared similarly as Compound **3**, but using Compound **5** (170 mg, 0.42 mmole) and Compound **2** (200 mg, 0.42 mmole). The crude materials were purified by column chromatography on silica gel with using hexanes and CHCl_3 mixed solvents as the eluent. Yield: 219 mg (62%). ^1H NMR (CDCl_3 , 300 MHz): δ = 9.50 (d, 2H, 3J = 7.0 Hz, Np), 8.04 (d, 2H, 3J = 7.0 Hz, Np), 6.68 (s, 2H, Th), 4.14 (q, 2H, CH_2), 2.58 (t, 4H, CH_2), 2.01 (m, 1H, CH), 1.61 (m, 4H, CH_2), 1.5-1.2 (m, 44H, CH_2), 1.0-0.8 (m, 12H, Me).

EXAMPLE 30 – Synthesis of Compound ABPI1



Compound **6** and Compound **7** were synthesized according to Example 27.

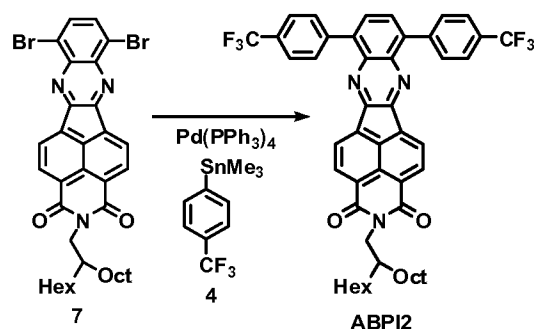
Compound **8**. Under argon protection, Compound **7** (140 mg, 0.20 mmole), trimethyl(3-octyl)thienylstannane (171 mg, 0.47 mmole), $\text{Pd}(\text{dba})_2$ (2.3 mg, 0.004 mmole) and $\text{P}(\text{o-tol})_3$ (4.6 mg, 0.016 mmole) were dissolved in 7 mL of toluene and transferred into a reaction tube. The solution was heated to 100 to 110 °C and kept stirring for 48 hours. After cooling back to room temperature, the volatile materials were removed in vacuo. The solid residue was further purified by column chromatography on silica gel. Yield: 120 mg (64.1%). ^1H NMR (CDCl_3 , 300.000 MHz): δ = 8.67 (d, 2H, 3J = 7.0 Hz, Np), 8.44 (d, 2H, 3J = 7.0 Hz,

Np), 7.87 (s, 2H, Ph), 7.52 (d, 2H, $^3J = 5.0$ Hz, Th), 7.20 (d, 2H, $^3J = 5.0$ Hz, Th), 4.17 (d, 4H, $^3J = 7.2$ Hz, CH₂), 2.63 (t, 4H, CH₂), 2.02 (m, 1H, CH), 1.72 (m, 4H, CH₂), 1.6-1.0 (m, 44H, CH₂), 0.86 (t, 6H, Me), 0.77 (t, 6H, Me).

Compound 9. At room temperature, N-bromosuccinimide (60 mg, 0.34 mmole) was slowly added to a solution of Compound 8 (120 mg, 0.13 mmole) in CHCl₃. The solution was kept stirring over night and then heated to 50 °C for additional 12 hours. When TLC showed that almost all the starting materials were consumed, the reaction mixture was cooled back to room temperature and quenched with water. After a standard aqueous work up, the crude materials were further purified through column chromatography on silica gel. The product was isolated as a red solid. Yield: 123 mg (87.6%). ¹H NMR (CDCl₃, 500 MHz): δ = 8.70 (d, 2H, $^3J = 7.0$ Hz, Np), 8.49 (d, 2H, $^3J = 8.0$ Hz, Np), 7.82 (s, 2H, Ph), 7.14 (s, 2H, Th), 4.16 (d, 2H, $^3J = 7.5$ Hz, CH₂), 2.58 (t, 4H, CH₂), 2.04 (m, 1H, CH), 1.68 (m, 4H, CH₂), 1.5-1.3 (m, 44H, CH₂), 0.87 (t, 6H, Me), 0.77 (t, 6H, Me).

ABPI1. ABPI1 was prepared similarly as ATP11, but using Compound 9 (123 mg, 0.11 mmole), trimethyl(4-trimethyl)phenylstannane (83 mg, 0.27 mmole) and tetrakis(triphenylphosphine)palladium(0) (5.0 mg, 0.004 mmole). The crude materials were purified by column chromatography on silica gel with using hexanes and CHCl₃ mixed solvents as the eluent. Yield: 347 mg (75.1%). ¹H NMR (CDCl₃, 500.046 MHz): δ = 8.69 (d, $^3J = 7.0$ Hz, 2H, Np), 8.47 (d, $^3J = 7.0$ Hz, 2H, Np), 7.94 (s, 2H, Ph), 7.84 (d, $^3J = 7.0$ Hz, 4H, Ph), 7.71 (d, $^3J = 8.0$ Hz, 4H, Ph), 7.51 (s, 2H, Th), 4.16 (d, $^3J = 7.5$ Hz, 2H, CH₂), 2.66 (t, $^3J = 7.5$ Hz, 4H, CH₂), 2.01 (m, 1H, CH), 1.79 (m, 4H, CH₂), 1.5-1.1 (m, 44H, CH₂), 0.86 (t, $^3J = 7.0$ Hz, 6H, CH₃), 0.86 (t, $^3J = 7.0$ Hz, 6H, CH₃); ¹³C NMR (CDCl₃, 125.7 MHz): 164.2, 154.2, 143.7, 142.8, 140.5, 138.3, 137.4, 135.8, 135.0, 134.4, 132.9, 132.6, 129.7, 129.5, 126.8, 126.4, 126.1, 125.7, 124.9, 123.7, 45.2, 37.3, 32.3, 32.3, 32.2, 32.2, 31.0, 30.5, 30.3, 30.2, 30.0, 30.0, 29.7, 29.6, 26.9, 23.1, 23.0, 14.5, 14.5.

EXAMPLE 31– Synthesis of Compound ABPI2



ABPI2. ABPI2 was prepared similarly as ATPI1, but using Compound 7 (110 mg, 0.16 mmole), trimethyl(4-trimethyl)phenylstannane (115 mg, 0.37 mmole) and tetrakis(triphenylphosphine)palladium(0) (7.2 mg, 0.06 mmole). The crude materials were purified by column chromatography on silica gel. Yield: 96 mg (73.6%). ^1H NMR (CDCl_3 , 500.046 MHz): δ =8.69 (d, 3J = 7.5 Hz, 2H, Ph), 8.42 (d, 3J = 7.5 Hz, 2H, Ph), 7.98 (d, 3J = 8.5 Hz, 4H, Np), 7.96 (s, 2H, Ph), 7.89 (d, 3J = 8.5 Hz, 4H, Np), 4.17 (d, 3J = 7.0 Hz, 2H, CH_2), 2.01 (m, 1H, CH), 1.5-1.2 (m, 24H, CH_2), 0.9-0.8 (m, 6H, CH_3); ^{13}C NMR (CDCl_3 , 125.7 MHz): 164.1, 154.2, 142.1, 140.8, 139.6, 137.6, 135.7, 132.9, 131.7, 131.3, 125.7, 125.5, 125.0, 123.5, 45.2, 37.3, 32.3, 32.3, 32.2, 30.5, 30.2, 30.0, 29.7, 27.0, 23.1, 14.5.

EXAMPLE 32 – Characterization of ATPI1, ATPI2, ABPI1 and ABPI2

ATPI1, ATPI2, ABPI1 and ABPI2 showed good solubility in common organic solvents such as chloroform, toluene, dichloromethane, chlorobenzene, etc, which is advantageous for solution processing device fabrication techniques.

The thermogravimetric analyses (TGA) show that all four compounds had similar thermal stabilities. High thermal decomposition temperatures (T_d , 5% weight loss) were found in the range from 390 °C to 410 °C. Differential scanning calorimetry (DSC) was used to further investigate the thermal behaviors of the molecules. Among them, ABPI1 exhibited the highest stability and no apparent transition was observed in the temperature range from 30 °C to 300 °C. The other molecules exhibited one or two thermal transitions during DSC scans from 30 °C to 300 °C. The thermal decomposition temperature (T_d), the melting transition temperature (T_m) and the corresponding recrystallization temperatures (T_c) are summarized in Table 1.

	$T_m/^\circ\text{C}^a$	$T_c/^\circ\text{C}^a$	$T_d/^\circ\text{C}^b$
ATPI1	120	97, 68	391
ATPI2	218	178/176	388
ABPI1	145,201	163,118	413
ABPI2	n/a	n/a	316

Table 1

^a from DSC scans at 20 °C/min under nitrogen.

^b from TGA at 10 °C/min under nitrogen.

All four molecules exhibited two absorption bands in dilute solution: the relatively intense high energy absorption band was mainly in the region from 300 nm to 400 nm, with

the exception of ATPI1, whose high energy absorption band was much broader and extended to 450 nm in chloroform solution; the weak low energy absorption band strongly depended on the main chain structure of the molecules. On one hand, ATPI1 and ATPI2, with a thieno-core, exhibited strongly red-shifted low energy absorption compared to ABPI-based molecules; on the other hand, this band was red-shifted going from ABPI1 and ATPI1 to ABPI2 and ATPI2 because of the extended π -conjugation resulted from the two additional thiophene rings in the main chains. Going from the dilute solution to the thin films, the low energy absorption was red shifted for a few tens of nm, while the high energy absorption was almost the same with the exception of that of ATPI1, which was broad and red-shifted. The optical energy gap estimated from the absorption edge varied from 1.53 eV for ATPI1, 2.05 eV for ATPI2, 2.14 eV for ABPI1, to 2.51 eV for ABPI2, indicating a significant change in the electron structures by variation of the chemical structures. Fusion with the electron-donating thiophene units or extending π -conjugation with thiophene groups favors a narrower energy gap.

The electron affinities of the oligomers were evaluated by cyclic voltammetry. A quasi-reversible reduction wave was observed at -1.05 V to -1.35 V vs. SCE, except that ATPI2 exhibited an irreversible reduction at -1.3 V. The LUMO energy levels estimated from the scan onsets varied from -3.44 eV for ATPI1, -3.74 eV for ATPI2, to 3.62 eV for both ABPI1 and ABPI2. With two additional thiophenes, ATPI1 and ABPI1 also showed an irreversible oxidation event at 0.55 V and 1.05 V vs. SCE, respectively. The HOMO was ca. -5.09 eV for ATPI1 and ca. -5.59 eV for ABPI1. However, no apparent oxidation signal up to 1.0 V (vs. SCE) was detected for ATPI2 and ABPI2 during anodic scans indicating that the HOMO energy levels were significantly decreased (Lower than -5.70 eV) by removing the two thiophene moieties from the main chains. The high electron affinity and large ionization potentials of ATPI2 and ABPI2 are desired for applications in n-channel OFETs since it can increase the hole injection barrier and block the hole transport.

The planar structure and high electron affinity of the resulting molecules are highly advantageous for n-type organic semiconductors. Bottom gate/bottom contact field-effect transistors were fabricated using spin coated ATPI- and ABPI-based thin films as active layer. While ATPI1- and ABPI1-based transistors exhibited ambipolar charge transport, ATPI2- and ABPI2-based transistors exhibited unipolar n-type charge transport.

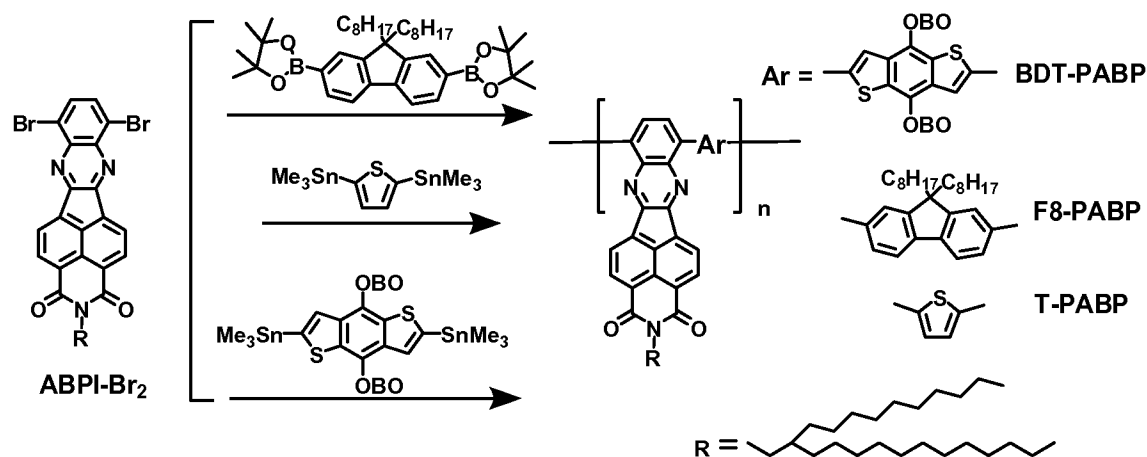
In summary, a family of novel organic semiconductors was designed and synthesized through attaching the naphthalene imide group onto different π -conjugated oligomers. The formed acenaphthoarylenepyrazine imide moieties have a desirable planar structure for

efficient solid state packing. The photophysical and electrochemical properties of the resulting molecules varied with the main chain structures and thus can be tuned.

¹H NMR and ¹³C NMR spectra were recorded on a Bruker AV500 at 500 MHz using either deuteriochloroform (CDCl₃) as the solvent. Mass spectra were obtained from Bruker AutoFlex II Matrix-Assisted LASER Desorption Ionization - Time of Flight Mass Spectrometer (MALDI-TOF) using benzo[α]pyrene as a matrix recorded in a (+)-reflector mode. Thermogravimetric analyses of the polymers were conducted on a TA Instrument model Q50TGA. A heating rate of 10 °C/min under a flow of N₂ was used with runs conducted from room temperature to 800 °C. Cyclic voltammetry was performed on an EG&G Princeton Applied Research potentiostat/galvanostat (model 273A). Data were analyzed by using a Model 270 Electrochemical Analysis System Software on a PC computer. A three-electrode cell was used, using platinum wire electrodes as both counter and working electrode. Silver/silver ion (Ag in 0.1 M AgNO₃ solution, Bioanalytical System, Inc.) was used as a reference electrode. Ferrocene was used as an internal standard with Ferrocene/ferrocenium (Fc/Fc⁺) couple at 0.16 V vs SCE. All solutions were purged with argon for 20 min before each experiment. UV-Vis absorption spectra were collected on a Perkin-Elmer model Lambda 900 UV/Vis/near-IR spectrophotometer. The photoluminescence (PL) emission spectra were obtained with a Photon Technology International (PTI) Inc. ModelQM2001-4 spectrofluorimeter.

PART V

EXAMPLE 33— Synthesis of Ar-PABPI Polymers



Chromium trioxide and bis(dibenzylideneacetone)palladium(0), tri-*o*-tolylphosphine, tetrakis(triphenylphosphine)palladium(0), 4,7-dibromobenzo[*c*]-1,2,5-thiadiazole, and 2,5-dibromo-3,4-dinitrothiophene were purchased from Sigma-Aldrich. Acenaphthylene

dicarboxylic acid imide, 3,6-dibromobenzene-1,2-diamine (Hong, D.-J.; et al, *Chem. Commun.* **2010**, 46, (27), 4896-4898), 9,9-dioctyl-2,7-bis(4,4,5,5-tetramethyl-1,3,2-dioxaborolane)fluorene (Geng, Y.; et al, *Chem. Mater.* **2003**, 15, (2), 542-549), and 2,6-bis(trimethylsannanyl)-4,8-bis(2-butyloctoxyl)benzo[1,2-b:4,5-b']dithiophene (Hundt, N.; et al, *Org. Lett.* **2009**, 11, (19), 4422-4425) were synthesized according to reported procedures.

Synthesis of T-PABPI. Under argon protection, ABPI-Br₂ (250 mg, 0.31 mmole), 2,5-bis(trimethylsannanyl)thiophene (125 mg, 0.31 mmole), Pd(dba)₂ (3.0 mg, 0.005 mmole) and P(o-tol)₃ (6.0 mg, 0.010 mmole) were dissolved in 10 mL of toluene and transferred into a reaction tube. The solution was heated to 100 to 110 °C and kept stirring for 72 hours. After cooling back to room temperature, the volatile materials were removed in vacuo. The solid residue was re-dissolved in 8 mL of toluene and precipitated into 100 mL of methanol/HCl (20v:1v) mixed solvents. The solids were collected and subjected to sequential Soxhlet extraction with methanol, acetone, hexanes. T-PABPI was isolated as a blue solid. Yield: 156 mg (68.1%).

Synthesis of F8-PABPI. Under argon protection, ABPI-Br₂ (200 mg, 0.24 mmole), 9,9-dioctyl-2,7-bis(4,4,5,5-tetramethyl-1,3,2-dioxaborolane)fluorene (157 mg, 0.24 mmole), Pd(PPh₃)₄ (11.3 mg, 0.010 mmole) were dissolved in 10 mL of toluene, transferred into a reaction tube followed by adding 6 mL of K₂CO₃ aqueous solution (2M). The solution was heated to 100 to 110 °C and kept stirring for 72 hours. After cooling back to room temperature, the organic phase was collected and dried in vacuo. The solid residue was re-dissolved in 8 mL of toluene and precipitated into 100 mL of methanol/HCl (20v:1v) mixed solvents. The solids were collected and subjected to sequential Soxhlet extraction with methanol, acetone, hexanes. F8-PABPI was isolated as a red solid. Yield: 167 mg (66.5%).

Synthesis of BDT-PABPI. Under argon protection, ABPI-Br₂ (200 mg, 0.24 mmole), 2,6-bis(trimethylsannanyl)-4,8-bis(2-butyloctoxyl)benzo[1,2-b:4,5-b']dithiophene (217.4 mg, 0.24 mmole), Pd(dba)₂ (3.0mg, 0.005 mmole) and P(o-tol)₃ (6.0 mg, 0.01 mmole) were dissolved in 10 mL of toluene and transferred into a reaction tube. The solution was heated to 100 to 110 °C and kept stirring for 72 hours. After cooling back to room temperature, the volatile materials were removed in vacuo. The solid residue was re-dissolved in 8 mL of toluene and precipitated into 100 mL of methanol/HCl (20v:1v) mixed solvents. The solids were collected and subjected to sequential Soxhlet extraction with methanol, acetone, hexanes. BDT-PABPI was isolated as a green solid. Yield: 181 mg (62.1%).

EXAMPLE 34 – Characterization of Ar-PABPI Polymers

Both BDT-PABPI and F8-PABPI showed good solubility in common organic solvents, such as chloroform, chlorobenzene, toluene, tetrahydrofuran, etc. The weight average molecular weight M_w measured by gel permeation chromatography (GPC) analysis in chlorobenzene at 60 °C against polystyrene standards was 71.1 KDa for BDT-PABPI with a polydispersity index (PDI) of 3.9, and was 21.9 KDa for F8-PABPI with a PDI of 2.6. On the other hand, the solubility of T-PABPI was low, possibly due to lack of solubilizing groups on the thiophene ring and the better coplanarity between the thiophene unit and ABPI unit.

Thermal gravimetric analysis shows that the three polymers exhibited moderate to high thermal stability. The thermal decomposition temperatures (T_d) varied from 330 °C for BDT-PABPI, 440 °C for T-PABPI to 445 °C for F8-PABPI. Differential scanning calorimetry scans show that no apparent thermal transition was observed in the temperature range from 30 °C to 300 °C.

Similar absorption was observed for T-PABPI and BDT-PABPI. They both showed two absorption bands: one presents in the region from 500 to 900 nm and the other in the region from 300 to 490 nm. The optical energy band gaps estimated from the absorption edges were 1.48 eV for T-PABPI and 1.53 eV for BDT-PABPI. While for F8-PABPI, both absorption bands experienced a strong blue-shift and the optical band gap was ca. 2.18 eV, which is consistent with the fact that fluorene is a weaker electron donor with relatively poorer electron delocalization than thiophene and benzodithiophene.

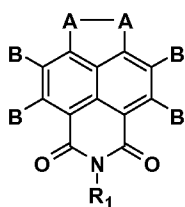
The electronic structures of the polymers were further investigated by cyclic voltammetry. BDT-PABPI exhibited two quasi-reversible reduction events at ca. -1.11 and -1.55 V (vs. SCE, $E_{1/2}$) and an irreversible oxidation event at ca. 0.80 V (vs. SCE, $E_{1/2}$). One irreversible reduction and oxidation event was observed for T-PABPI at ca. -1.02 V and 0.58 V, respectively. While for F8-PABPI, no oxidation signal was observed up to 1.2 V (vs. SCE) indicating a relatively high ionization potential due to the weak electron-donating property of fluorene moieties. Both BDT-PABPI and T-PABPI exhibited ambipolar electrochemical properties, i.e. they can be reduced and oxidized electrochemically at relatively low potentials, which is again in good agreement with the fact that benzodithiophene and thiophene are stronger electron-donors. The LUMO and HOMO energy levels calculated from the scan onsets of the cyclic voltammograms were -3.56 eV and -5.31 eV for BDT-PABPI, -3.62 eV and -5.22 eV for T-PABPI, and -3.52 eV (LUMO) for F8-PABPI, respectively.

In summary, a new acceptor-type functional group, acenaphthylene imide, was successfully incorporated into three polymers, BDT- PABPI, T- PABPI and F8-PABPI. A high electron affinity of 3.52 eV to 3.62 eV was observed. Depending on the second repeat unit, the HOMO ranged from -5.22 eV for T-PABPI, -5.31 eV for BDT-PABPI to lower than -5.90 eV for F9-PABPI.

^1H NMR and ^{13}C NMR spectra were recorded on a Bruker AV500 at 500 MHz using either deuteriochloroform (CDCl_3) as the solvent. Mass spectra were obtained from Bruker AutoFlex II Matrix-Assisted LASER Desorption Ionization - Time of Flight Mass Spectrometer (MALDI-TOF) using benzo[α]pyrene as a matrix recorded in a (+)-reflector mode. Thermogravimetric analyses of the polymers were conducted on a TA Instrument model Q50TGA. A heating rate of 10 °C/min under a flow of N_2 was used with runs conducted from room temperature to 800 °C. Cyclic voltammetry was performed on an EG&G Princeton Applied Research potentiostat/galvanostat (model 273A). Data were analyzed by using a Model 270 Electrochemical Analysis System Software on a PC computer. A three-electrode cell was used, using platinum wire electrodes as both counter and working electrode. Silver/silver ion (Ag in 0.1 M AgNO_3 solution, Bioanalytical System, Inc.) was used as a reference electrode. Ferrocene was used as an internal standard with Ferrocene/ferrocenium (Fc/Fc^+) couple at 0.16 V vs SCE. All solutions were purged with argon for 20 min before each experiment. UV-vis absorption spectra were collected on a Perkin-Elmer model Lambda 900 UV/vis/near-IR spectrophotometer. The photoluminescence (PL) emission spectra were obtained with a Photon Technology International (PTI) Inc. ModelQM2001-4 spectrofluorimeter.

WHAT IS CLAIMED IS:

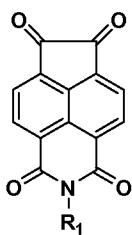
1. A compound represented by formula (I):



(I), wherein:

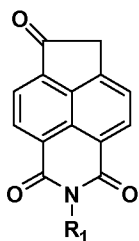
- (i) one or both of A are $-\text{C}(\text{O})-$, and the remaining A, if any, is $-\text{CH}_2-$;
- (ii) R_1 is an optionally substituted C_1 - C_{50} organic group; and
- (iii) B at each occurrence is independently selected from hydrogen, halogen, cyano, nitro, optionally substituted alkyl group and optionally substituted heteroalkyl group, or a structure wherein each pair of substituents B in ortho position optionally forms a conjugated ring.

2. The compound of claim 1, wherein the compound is represented by formula (II):



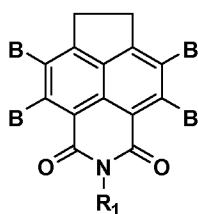
(II).

3. The compound of claim 1, wherein the compound is represented by formula (III):



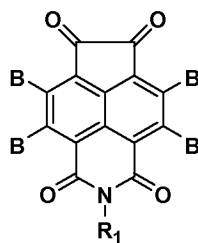
(III).

- 4. The compound of any of claims 1-3, wherein R_1 is an optionally substituted linear, branched or cyclic C_1 - C_{36} alkyl group or an optionally substituted linear, branched or cyclic C_1 - C_{36} heteroalkyl group.
- 5. A method for making the compound of any of claims 1-4, comprising reacting an oxidant with a compound represented by formula (IV):

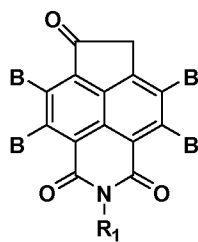


(IV), wherein: (i) R_1 is an optionally substituted C_1 - C_{50} organic

group, (ii) B at each occurrence is independently selected from hydrogen, halogen, cyano, nitro, optionally substituted alkyl group and optionally substituted heteroalkyl group, or a structure wherein each pair of substituents B in ortho position optionally forms a conjugated ring; and

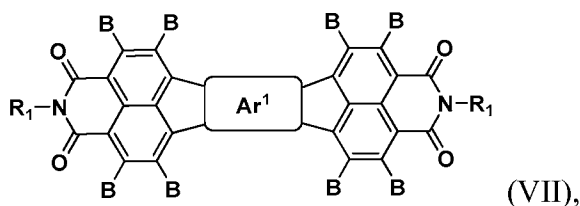


separating a first product represented by (V) from a second product



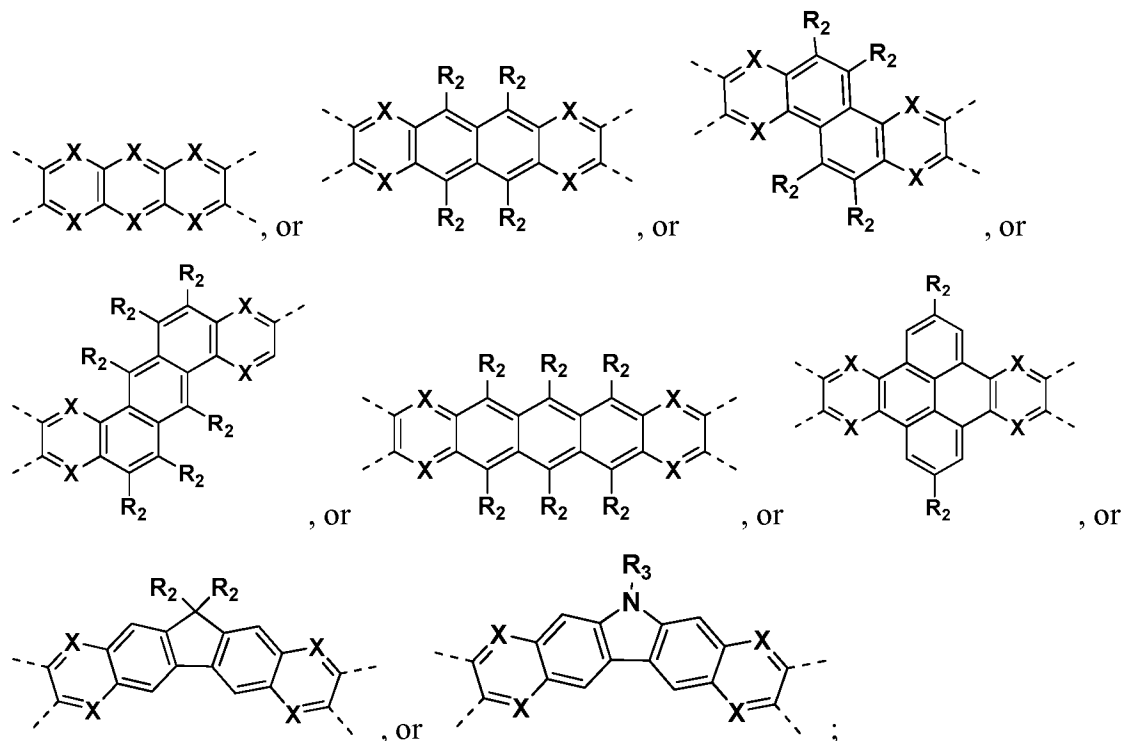
represented by (VI).

6. The method of claim 5, wherein the oxidant is CrO_3 or SeO_2 .
7. A method for using the compound of any of claims 1-4 or the compound prepared by the method according to claim 5 or 6, comprising reacting said compound with a second compound comprising one or more primary amino groups.
8. A compound represented by formula (VII):



wherein: (i) Ar^1 comprises three or more rings fused together, each ring is an optionally substituted aryl ring or an optionally substituted heteroaryl ring; (ii) R_1 at each occurrence is an optionally substituted C_1 - C_{50} organic group; and (iii) B at each occurrence is independently selected from hydrogen, halogen, cyano, nitro, optionally substituted alkyl group and optionally substituted heteroalkyl group, or a structure wherein each pair of substituents B in ortho position optionally forms a conjugated ring.

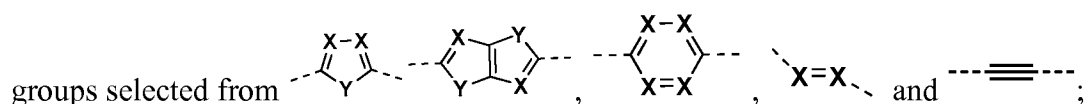
9. The compound of claim 8, wherein Ar¹ comprises two or more N heteroatoms.
10. The compound of claim 8 or 9, wherein B is hydrogen and Ar¹ is represented by



wherein X at each occurrence is independently selected from  and ; and
wherein R₂ at each occurrence is an end group optionally linked by a single bond or by one or more conjugation side groups; wherein the end group at each occurrence is independently selected from hydrogen, cyano, an optionally substituted C₁-C₂₄ alkyl group and an optionally substituted C₁-C₂₄ heteroalkyl group; and wherein the optional conjugation side group at each occurrence is independently selected from an optionally substituted aryl group, an optionally substituted heteroaryl group, an optionally substituted ethynylene, and ethynylene; and

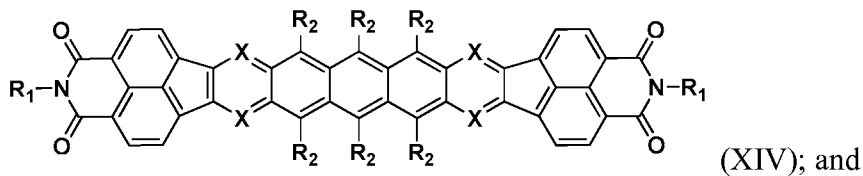
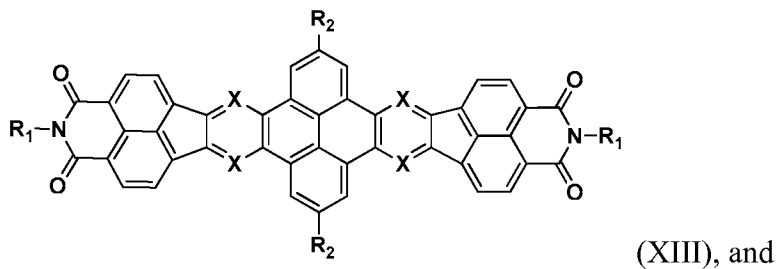
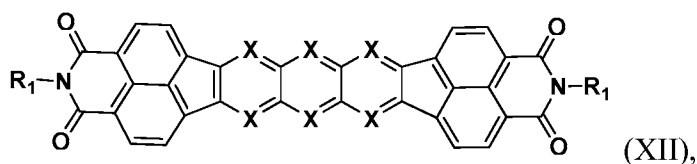
wherein R₃ is selected from hydrogen, an optionally substituted C₁-C₂₄ alkyl group and an optionally substituted C₁-C₂₄ heteroalkyl group.

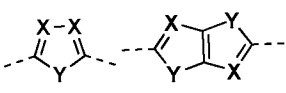
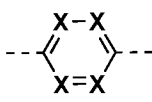
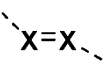
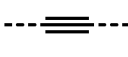
11. The compound of claim 10, wherein Ar¹ comprises one or more conjugation side



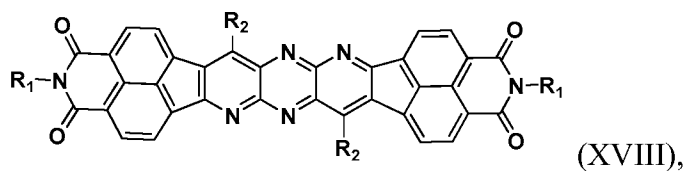
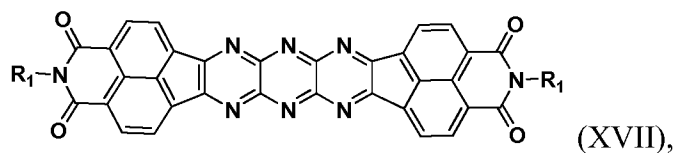
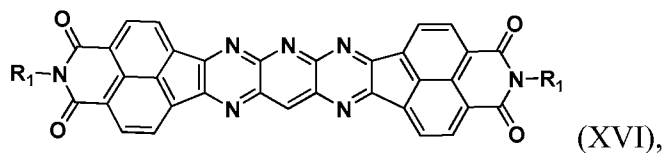
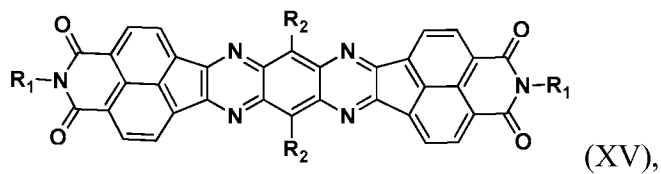
wherein Y at each occurrence is independently selected from O, S, Se, Te, N(R₃), C(R₃)₂ and Si(R₃)₂.

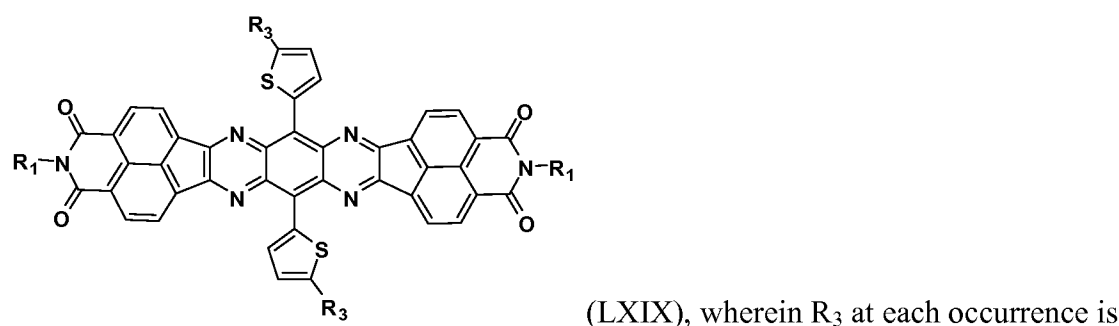
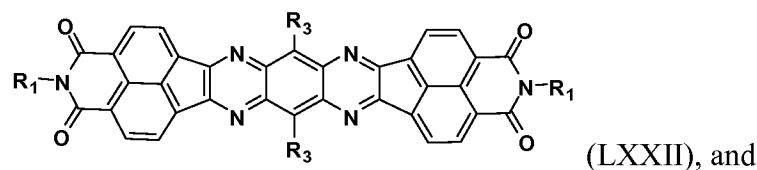
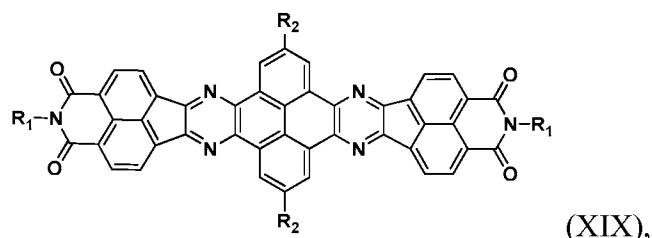
12. The compound of any of claims 10-11, wherein the compound is selected from:



wherein the optional conjugation side group is selected from , , , and , Y at each occurrence is independently selected from O, S, Se, Te, N(R₃), C(R₃)₂ and Si(R₃)₂.

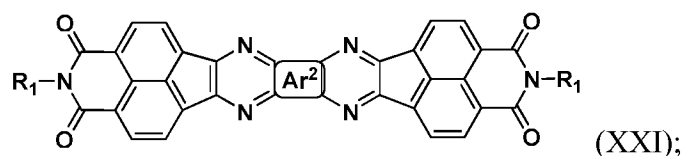
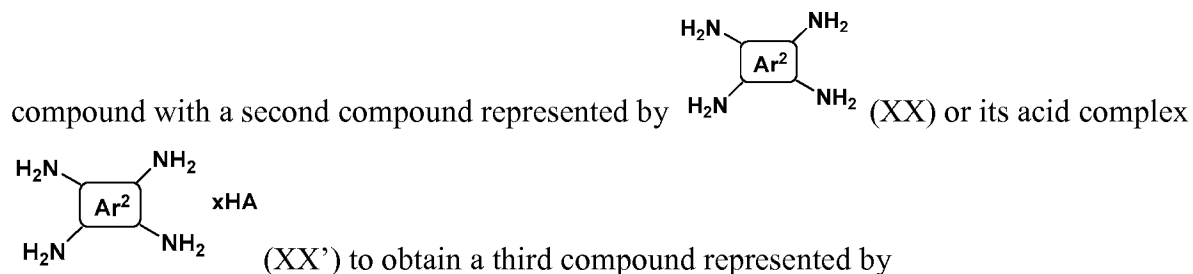
13. The compound of any of claims 8-12, wherein the compound is selected from:





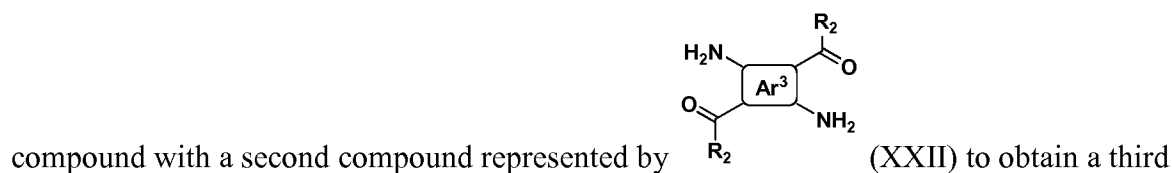
independently selected from hydrogen, cyano, an optionally substituted C₁-C₂₄ alkyl group and an optionally substituted C₁-C₂₄ heteroalkyl group.

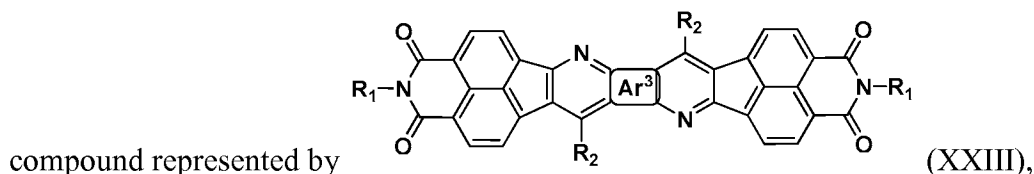
14. A method for using the compound of claim 2 or 4, comprising reacting said



wherein Ar² comprises an optionally substituted aryl ring or an optionally substituted heteroaryl ring, or two or more of said rings fused together; and wherein HA is HCl, HBr, HI, CH₃COOH, H₂SO₄ or H₃PO₄, x is 1, 2, 3 or 4.

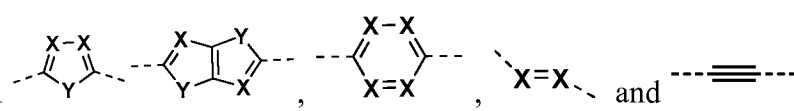
15. A method for using the compound of claim 3 or 4, comprising reacting said





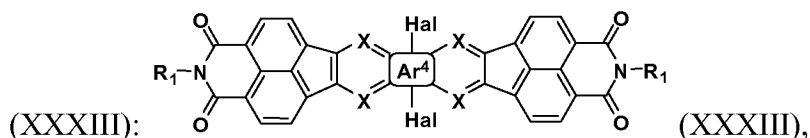
wherein Ar³ comprises an optionally substituted aryl ring or an optionally substituted heteroaryl ring, or two or more of said rings fused together, and

wherein R₂ at each occurrence is an end group optionally linked by a single bond or by one or more conjugation side groups, wherein the end group at each occurrence is independently selected from hydrogen, cyano, an optionally substituted C₁-C₂₄ alkyl group and an optionally substituted C₁-C₂₄ heteroalkyl group, wherein the optional conjugation side

group is selected from , wherein Y at each occurrence is independently selected from O, S, Se, Te, N(R₃), C(R₃)₂ and Si(R₃)₂, and wherein R₃ at each occurrence is independently selected from hydrogen, an optionally substituted C₁-C₂₄ alkyl group and an optionally substituted C₁-C₂₄ heteroalkyl group.

16. The compound of claim 8 or 9, wherein the compound is a monomer suitable for polymerization or copolymerization, and wherein Ar¹ comprises one or more halogen atoms that are polymerizable.

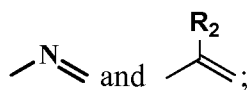
17. The compound of claim 16, wherein the compound is represented by formula



wherein:

(i) Ar⁴ comprises an optionally substituted aryl ring or an optionally substituted heteroaryl ring, or two or more of said rings fused together

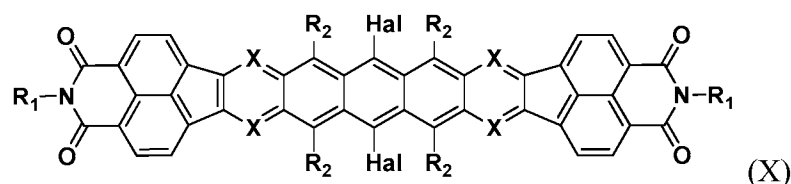
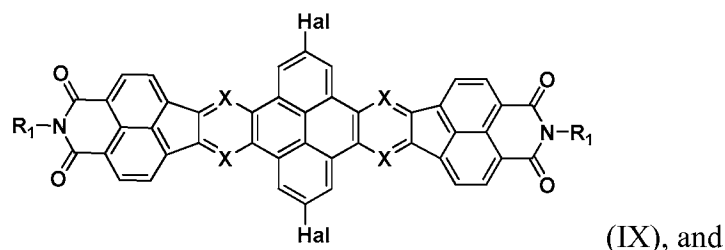
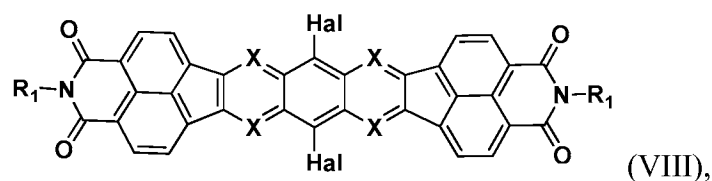
(ii) Hal at each occurrence comprises a halogen optionally linked by one or more conjugation side groups, wherein the optional conjugation side group at each occurrence is independently selected from an optionally substituted aryl group, an optionally substituted heteroaryl group, an optionally substituted ethenylene, and ethynylene;

(iii) X at each occurrence is independently selected from ;

(iv) R₂ at each occurrence is an end group optionally linked by a single bond or by one or more conjugation side groups, wherein the end group at each occurrence is independently selected from hydrogen, cyano, an optionally substituted linear or branched

C₁-C₂₄ alkyl group and an optionally substituted linear and branched C₁-C₂₄ heteroalkyl group.

18. The compound of claim 16 or 17, wherein the compound is selected from:



wherein:

(i) Hal at each occurrence is a halogen optionally linked by a single bond or by one or more conjugation side groups;

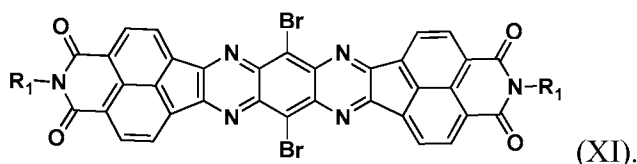
(ii) X at each occurrence is independently selected from —N= and $\text{—C(R}_2\text{)=}$;

(iii) R₂ at each occurrence is an end group optionally linked by a single bond or by one or more conjugation side groups, wherein the end group at each occurrence is independently selected from hydrogen, cyano, an optionally substituted linear or branched C₁-C₂₄ alkyl group and an optionally substituted linear and branched C₁-C₂₄ heteroalkyl group; and

(iv) the optional conjugation side group at each occurrence is independently selected

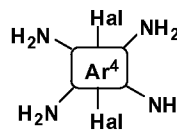
from —X—X— , —X—Y— , —X—X— , —X=X— , and $\text{—}\equiv\text{—}$, wherein Y at each occurrence is independently selected from O, S, Se, Te, N(R₃), C(R₃)₂ and Si(R₃)₂, and wherein R₃ at each occurrence is independently selected from hydrogen, an optionally substituted linear or branched C₁-C₂₄ alkyl group and an optionally substituted linear or branched C₁-C₂₄ heteroalkyl group.

19. The compound of any of claims 8-9 and 16-18, wherein the compound is:

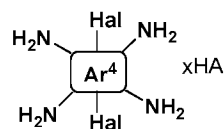


20. A method for using the compound of claim 2 or 4, comprising reacting said

compound with a second compound represented by



compound with a second compound represented by



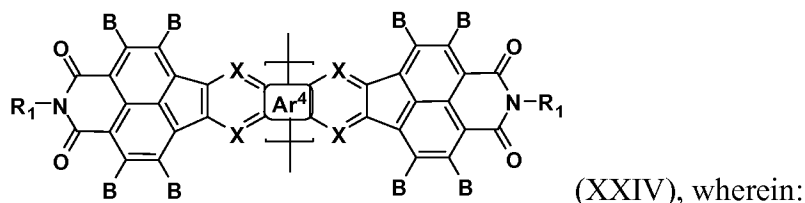
to obtain the compound of any of claims 16-18;

wherein Ar^4 comprises an optionally substituted aryl ring or an optionally substituted heteroaryl ring, or two or more of said rings fused together;

wherein Hal at each occurrence comprises a halogen optionally linked by one or more conjugation side groups, wherein the optional conjugation side group at each occurrence is independently selected from an optionally substituted aryl group, an optionally substituted heteroaryl group, an optionally substituted ethynylene, and ethynylene; and

wherein HA is HCl, HBr, HI, CH_3COOH , H_2SO_4 or H_3PO_4 , x is 1, 2, 3 or 4.

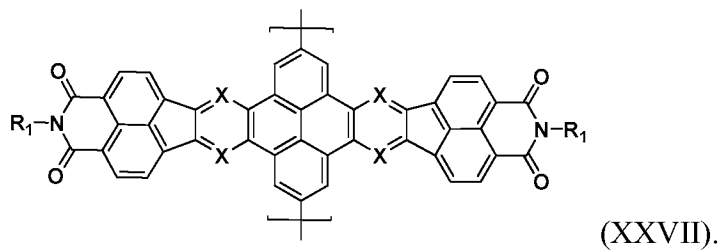
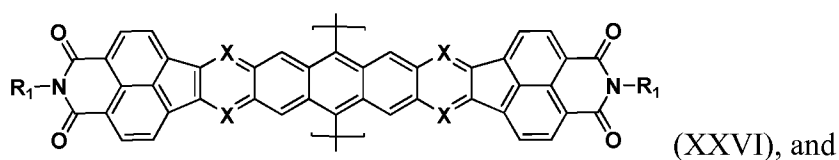
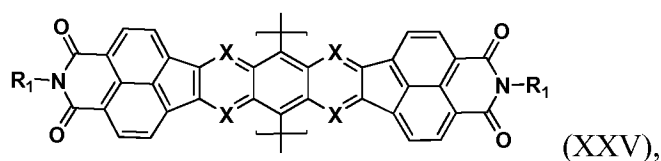
21. A polymer comprising one or more first repeating units RU1 represented by



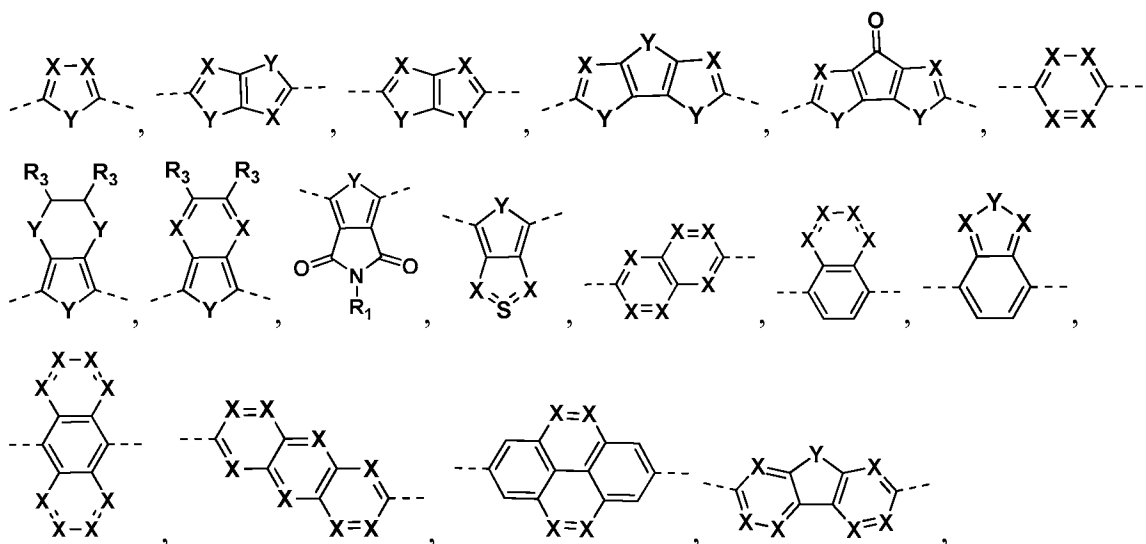
- (i) Ar^4 comprises an optionally substituted aryl ring or an optionally substituted heteroaryl ring, or two or more of said rings fused together;
- (ii) R_1 at each occurrence is an optionally substituted C_1 - C_{50} organic group;
- (iii) B at each occurrence is independently selected from hydrogen, halogen, cyano, nitro, optionally substituted alkyl group and optionally substituted heteroalkyl group, or a structure wherein each pair of substituents B in ortho position optionally forms a conjugated ring; and
- (iv) X at each occurrence is independently selected from —N= and $\text{—C(R}_2\text{)=}$, wherein R_2 at each occurrence is an end group optionally linked by a single bond or by one or more conjugation side groups, wherein the end group at each occurrence is independently selected

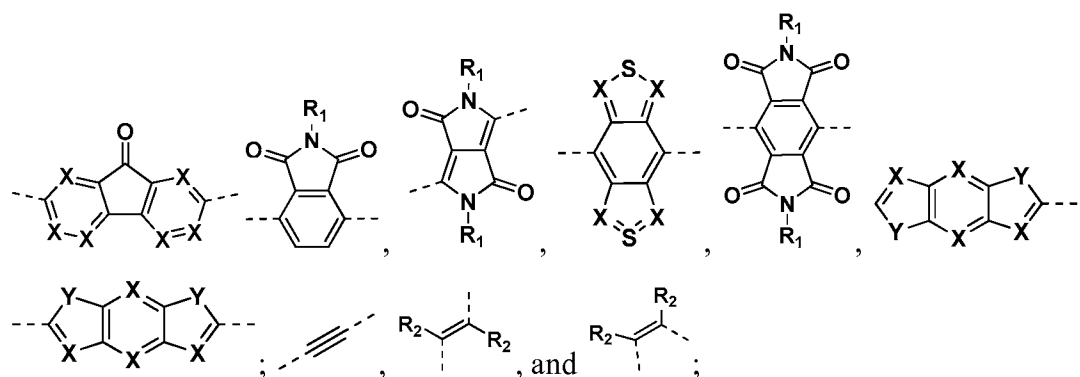
from hydrogen, cyano, an optionally substituted C₁-C₂₄ alkyl group and an optionally substituted C₁-C₂₄ heteroalkyl group, wherein the optional conjugation side group at each occurrence is independently selected from optionally substituted aryl group, an optionally substituted heteroaryl group, an optionally substituted ethynylene, and ethynylene.

22. The polymer of claim 22, wherein the one or more first repeating units RU1 are selected from



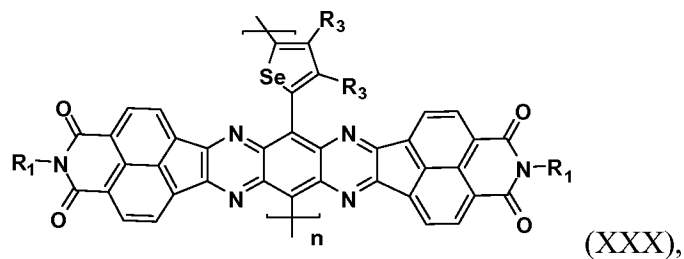
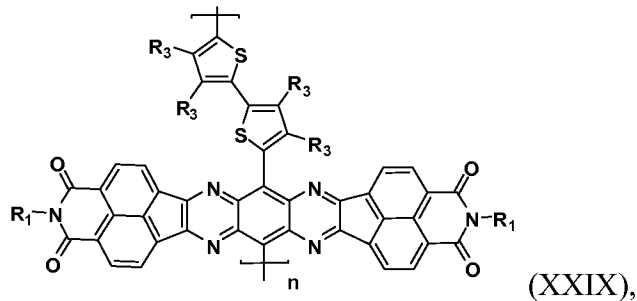
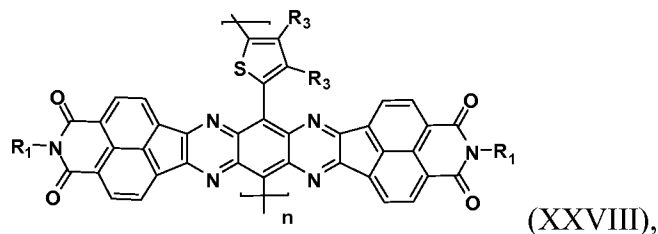
23. The polymer of claim 21 or 22, wherein the polymer is a copolymer further comprising one or more second repeating units RU2 selected from

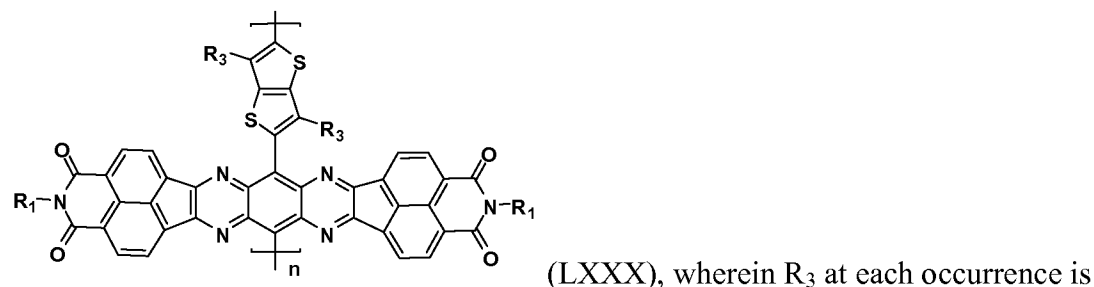
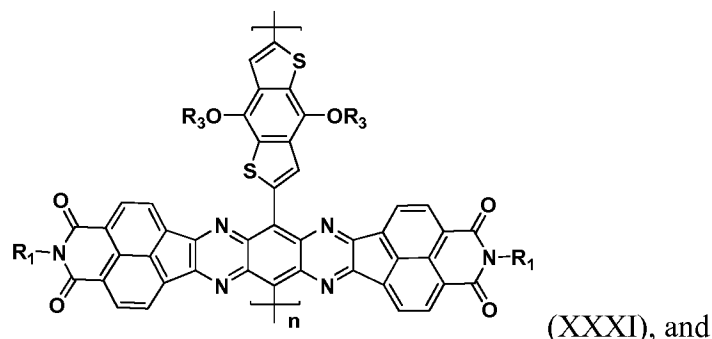




wherein Y at each occurrence is independently selected from O, S, Se, Te, N(R₃), C(R₃)₂ and Si(R₃)₂; and wherein R₃ at each occurrence is independently selected from hydrogen, an optionally substituted linear or branched C₁-C₂₄ alkyl group and an optionally substituted linear or branched C₁-C₂₄ heteroalkyl group.

24. The polymer of any of claims 21-23, wherein the polymer is selected from



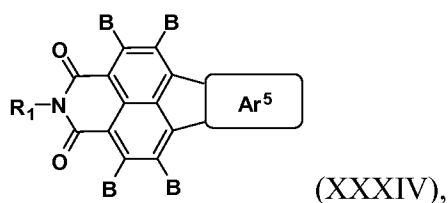


independently selected from hydrogen, an optionally substituted linear or branched C₁-C₂₄ alkyl group and an optionally substituted linear or branched C₁-C₂₄ heteroalkyl group.

25. A method for making the compound of any of claims 8-13, comprising Pd catalyzed coupling of the compound of any of claims 16-19 or made by the method of claim 20 or a halogenated derivative of the RU1 of claim 21 or 22, with a mono-tin derivative of the RU2 of claim 23.

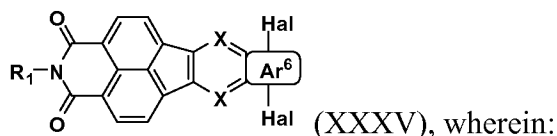
26. A method for making the polymer of any of claims 21-24, comprising Pd catalyzed coupling of the compound of any of claims 16-19 or made by the method of claim 20 or a halogenated derivative of the RU1 of claim 21 or 22, with a di-tin derivative of the RU2 of claim 23.

27. A compound represented by formula (XXXIV):

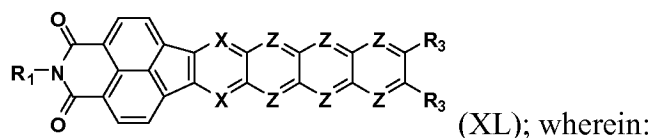
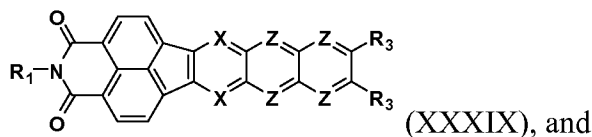
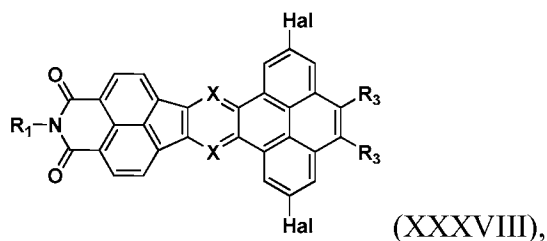
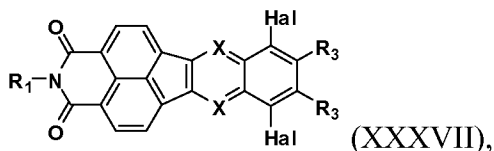
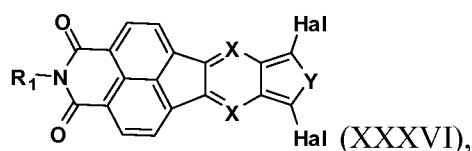


wherein: (i) Ar⁵ comprises two or more rings fused together, each ring is an optionally substituted aryl ring or an optionally substituted heteroaryl ring; (ii) R₁ at each occurrence is an optionally substituted C₁-C₅₀ organic group; and (iii) B at each occurrence is independently selected from hydrogen, halogen, cyano, nitro, optionally substituted alkyl group and optionally substituted heteroalkyl group, or a structure wherein each pair of substituents B in ortho position optionally forms a conjugated ring.

28. The compound of claim 27, wherein Ar⁵ comprises two or more N heteroatoms.
29. The compound of claim 27 or 28, wherein the compound is a monomer suitable for polymerization or copolymerization, and wherein Ar⁵ comprises one or more halogen atoms that are polymerizable.
30. The compound of any of claims 27-29, wherein B is hydrogen and the compound is represented by formula (XXXV):

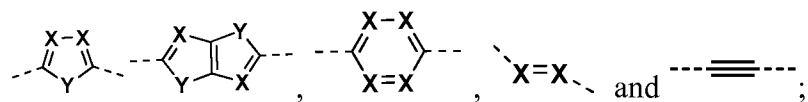


- (i) Ar⁶ comprises an optionally substituted aryl ring or an optionally substituted heteroaryl ring, or two or more of said rings fused together;
- (ii) Hal at each occurrence is a halogen optionally linked by a single bond or by one or more conjugation side groups, wherein the optional conjugation side group at each occurrence is independently selected from an optionally substituted aryl group, an optionally substituted heteroaryl group, an optionally substituted ethenylene, and ethynylene;
- (ii) X at each occurrence is independently selected from —N= and $\text{—C(R}_2\text{)=}$, wherein R₂ at each occurrence is an end group optionally linked by a single bond or by one or more conjugation side groups, wherein the end group at each occurrence is independently selected from hydrogen, cyano, an optionally substituted linear or branched alkyl group and an optionally substituted linear and branched heteroalkyl group.
31. The compound of claim 30, wherein the compound is selected from



(i) Z at each occurrence is independently selected from X and ;

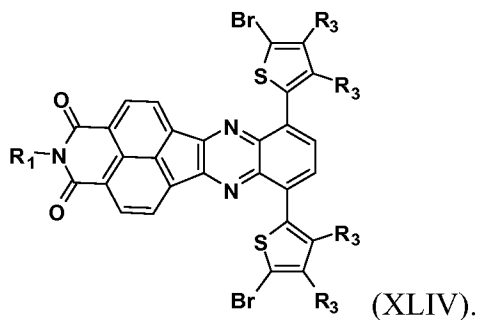
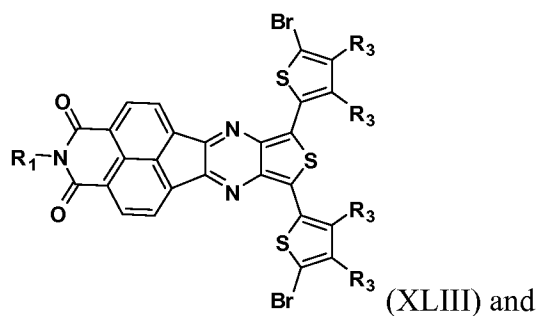
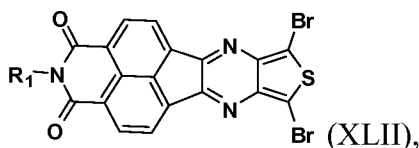
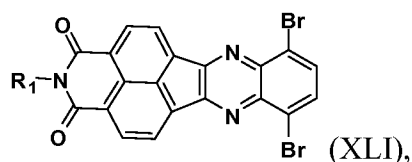
(ii) each  optionally comprises one or more conjugation side groups selected from



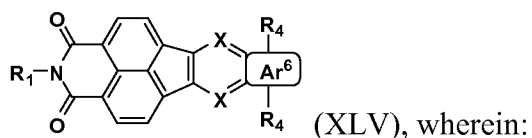
(iii) Y at each occurrence is independently selected from O, S, Se, Te, N(R₃), C(R₃)₂ and Si(R₃)₂; and

(iv) R₃ at each occurrence is independently selected from hydrogen, an optionally substituted C₁-C₂₄ alkyl group and an optionally substituted C₁-C₂₄ heteroalkyl group.

32. The compound of any of claims 27-31, wherein the compound is selected from:



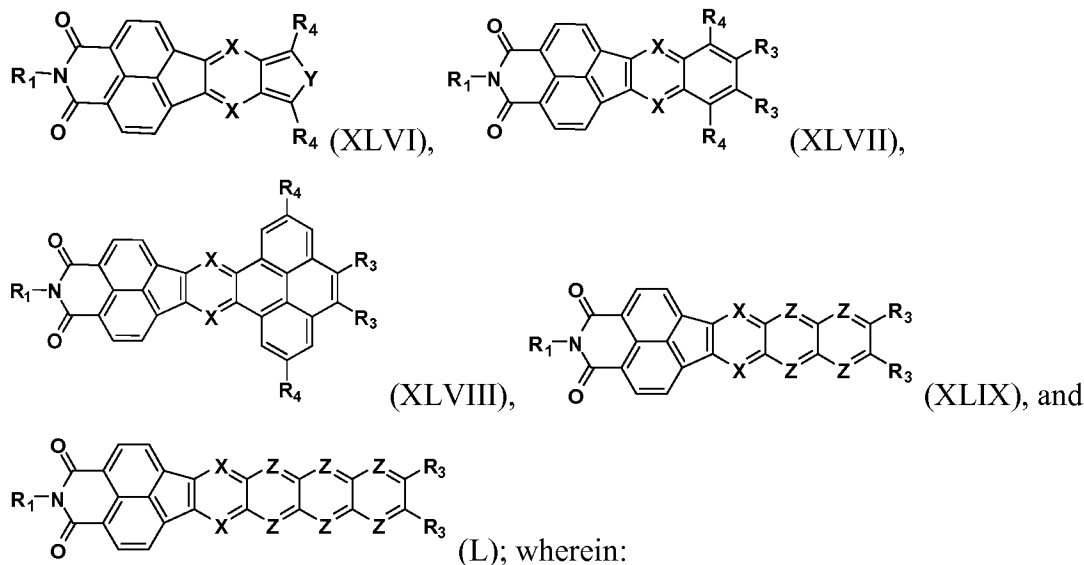
33. The compound of claim 27 or 28, wherein B is hydrogen and the compound is represented by formula (XLV):



- (i) Ar⁶ comprises an optionally substituted aryl ring or an optionally substituted heteroaryl ring, or two or more of said rings fused together;
- (ii) R₄ at each occurrence comprises an end group linked by one or more conjugation side groups, wherein the end group at each occurrence is independently selected from hydrogen, an optionally substituted linear or branched alkyl group and an optionally substituted linear and branched heteroalkyl group, and wherein the conjugation side group at each occurrence is independently selected from an optionally substituted aryl group, an optionally substituted heteroaryl group, an optionally substituted ethenylene, and ethynylene; and

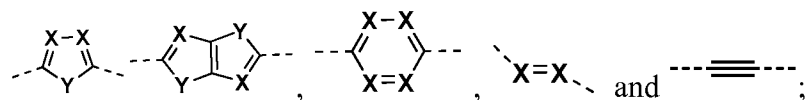
(iii) X at each occurrence is independently selected from ---N= and $\text{---C(R}_2\text{)=}$, wherein R₂ at each occurrence is an end group optionally linked by a single bond or by one or more conjugation side groups, wherein the end group at each occurrence is independently selected from hydrogen, cyano, an optionally substituted linear or branched alkyl group and an optionally substituted linear and branched heteroalkyl group.

34. The compound of claim 33, wherein the compound is selected from



(i) Z at each occurrence is independently selected from X and R₄;

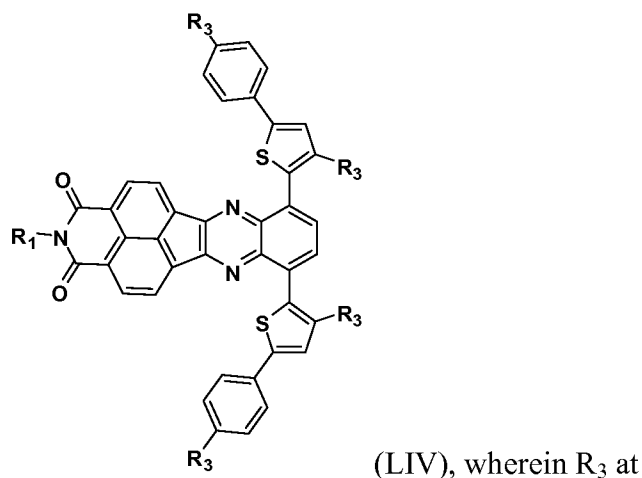
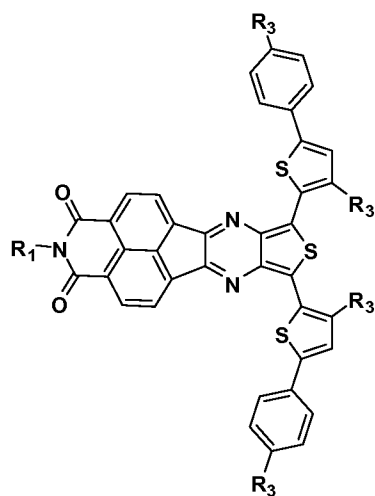
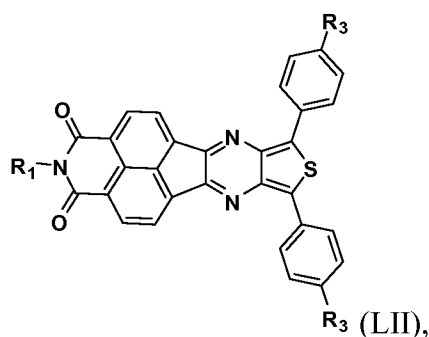
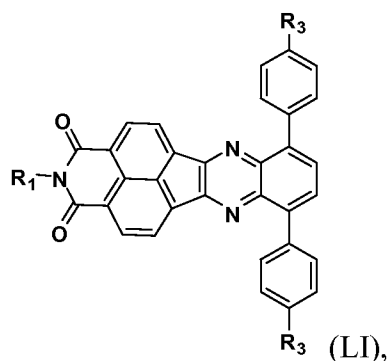
(ii) each R₄ comprises one or more conjugation side groups selected from



(iii) Y at each occurrence is independently selected from O, S, Se, Te, N(R₃), C(R₃)₂ and Si(R₃)₂; and

(iv) R₃ at each occurrence is independently selected from hydrogen, an optionally substituted C₁-C₂₄ alkyl group and an optionally substituted C₁-C₂₄ heteroalkyl group.

35. The compound of any of claims 27-28 and 33-34, wherein the compound is selected from:



each occurrence is independently selected from hydrogen, cyano, an optionally substituted C₁-C₂₄ alkyl group and an optionally substituted C₁-C₂₄ heteroalkyl group.

36. A method for using the compound of claim 2 or 4, comprising reacting said

compound with a second compound represented by (LV) or (LV') to

obtain a third compound represented by (LVI),

wherein Ar⁶ comprises an optionally substituted aryl ring or an optionally substituted heteroaryl ring, or two or more of said rings fused together,

wherein Hal at each occurrence comprises a halogen optionally linked by one or more conjugation side groups, wherein the optional conjugation side group at each occurrence is independently selected from an optionally substituted aryl group, an optionally substituted heteroaryl group, an optionally substituted ethynylene, and ethynylene, and

wherein HA is HCl, HBr, HI, CH₃COOH, H₂SO₄ or H₃PO₄, x is 1 or 2.

37. A method for using the compound of claim 2 or 4, comprising reacting said

compound with a second compound represented by (LVII) or (LVII')

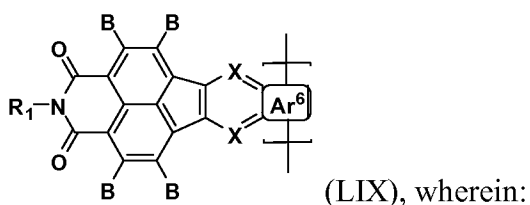
(LVII') to obtain a third compound represented by (LVIII);

wherein Ar⁶ comprises an optionally substituted aryl ring or an optionally substituted heteroaryl ring, or two or more of said rings fused together;

wherein R₄ at each occurrence comprises an end group linked by one or more conjugation side groups, wherein the end group at each occurrence is independently selected from hydrogen, cyano, an optionally substituted linear or branched alkyl group and an optionally substituted linear and branched heteroalkyl group, and wherein the conjugation side group at each occurrence is independently selected from an optionally substituted aryl group, an optionally substituted heteroaryl group, an optionally substituted ethynylene, and ethynylene; and

wherein HA is HCl, HBr, HI, CH₃COOH, H₂SO₄ or H₃PO₄, x is 1 or 2.

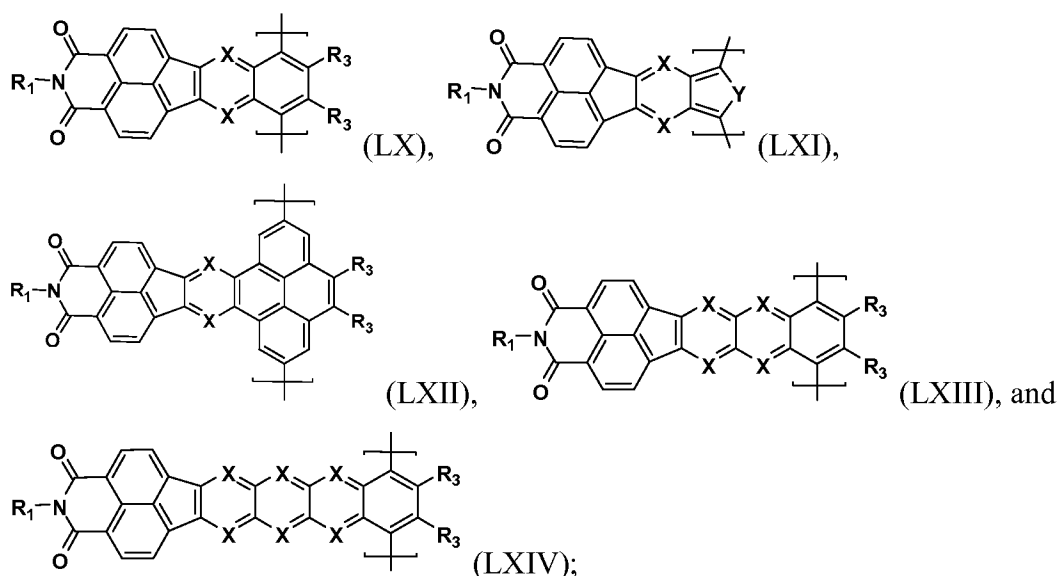
38. A polymer comprising one or more first repeating units RU3 represented by



- (i) Ar⁶ comprises an optionally substituted aryl ring or an optionally substituted heteroaryl ring, or two or more of said rings fused together;
- (ii) R₁ at each occurrence is an optionally substituted C₁-C₅₀ organic group;
- (iii) B at each occurrence is independently selected from hydrogen, halogen, cyano, nitro, optionally substituted alkyl group and optionally substituted heteroalkyl group, or a structure wherein each pair of substituents B in ortho position optionally forms a conjugated ring; and
- (iv) X at each occurrence is independently selected from and , wherein R₂ at each occurrence is an end group optionally linked by a single bond or by one or more conjugation side groups, wherein the end group at each occurrence is independently selected from hydrogen, cyano, an optionally substituted C₁-C₂₄ alkyl group and an optionally substituted C₁-C₂₄ heteroalkyl group, wherein the optional conjugation side group at each

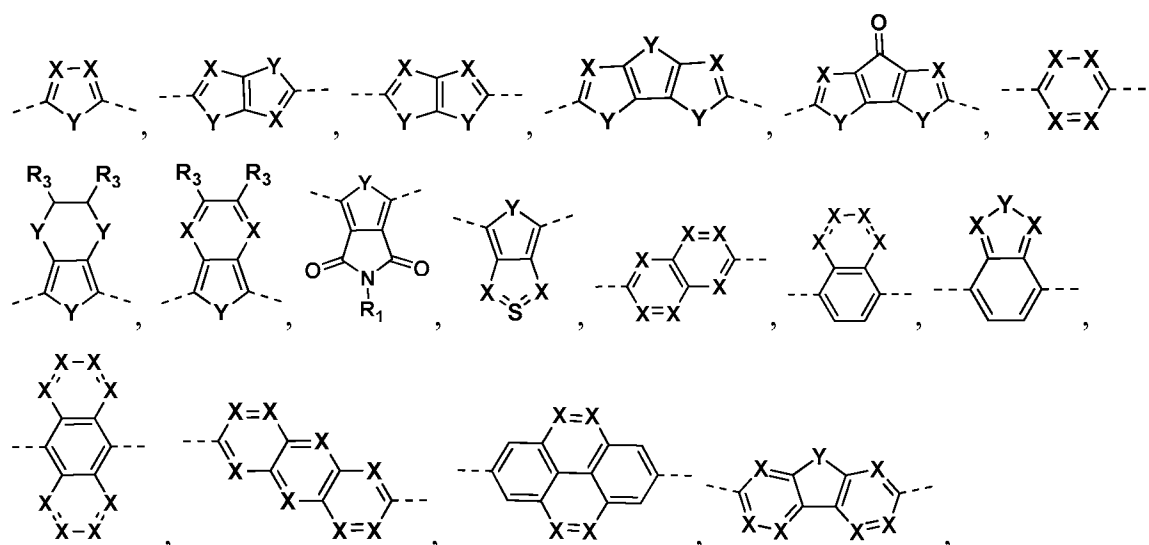
occurrence is independently selected from optionally substituted aryl group, an optionally substituted heteroaryl group, an optionally substituted ethenylene, and ethynylene.

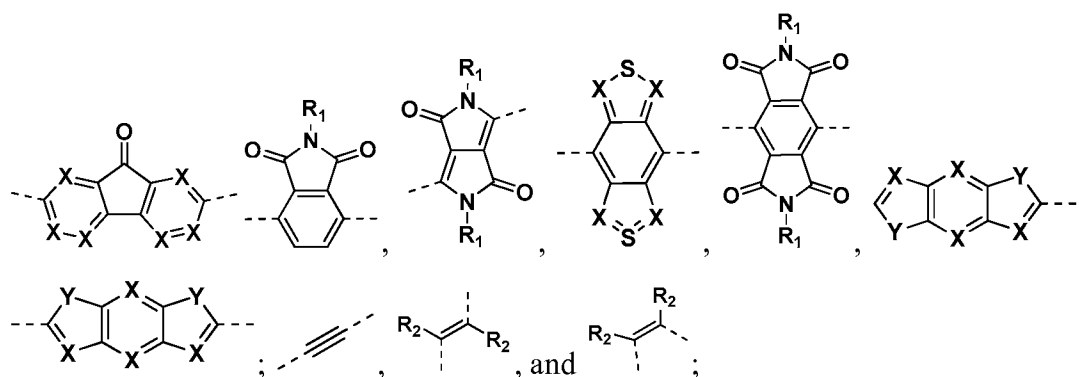
39. The polymer of claim 38, wherein the one or more first repeating units RU3 are selected from



wherein Y is selected from O, S, Se, Te, N(R₃), C(R₃)₂ and Si(R₃)₂, and wherein R₃ at each occurrence is independently selected from hydrogen, an optionally substituted C₁-C₂₄ alkyl group and an optionally substituted C₁-C₂₄ heteroalkyl group.

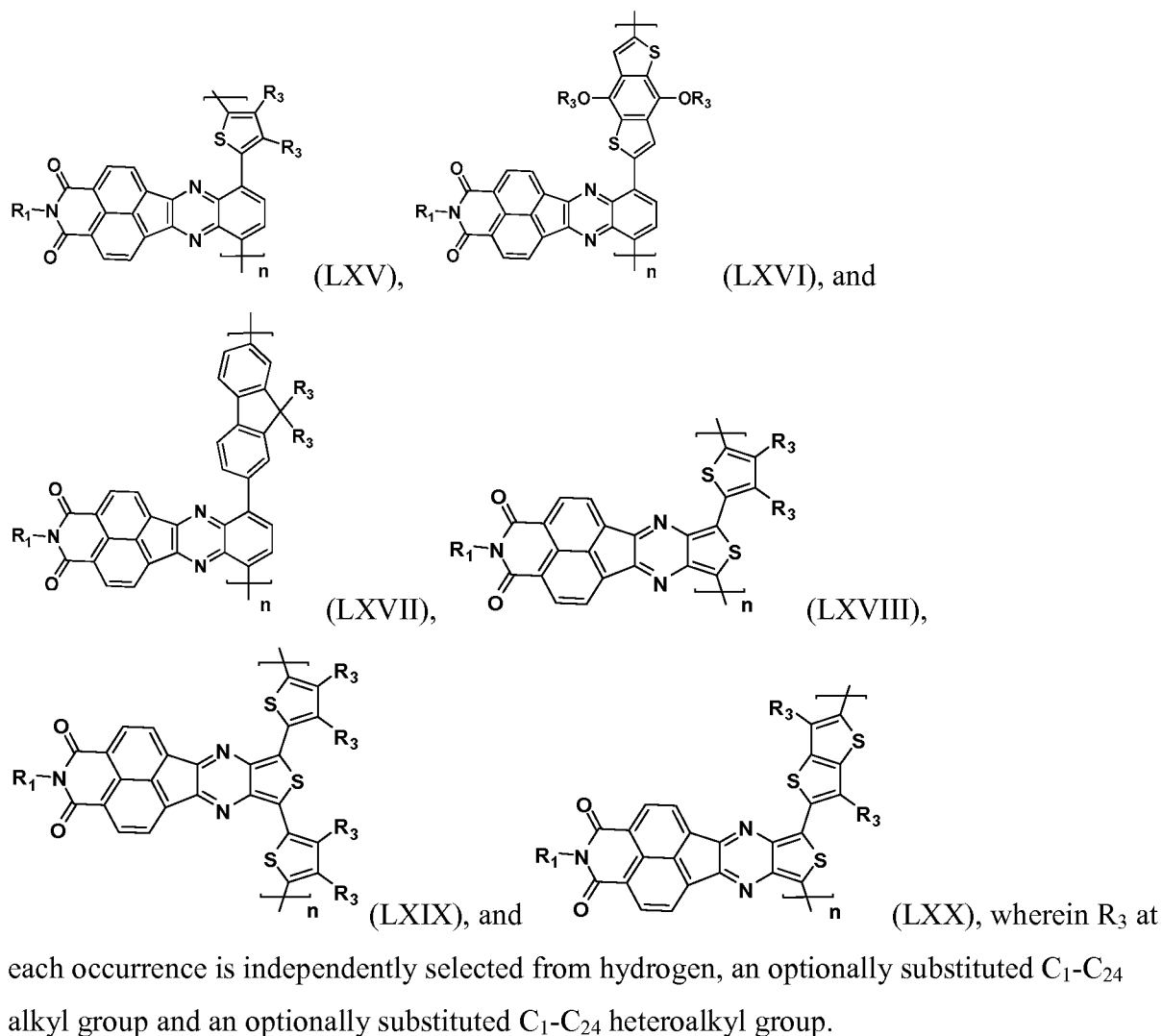
40. The polymer of claim 38 or 39, wherein the polymer is a copolymer further comprising one or more second repeating units RU4 selected from





wherein Y at each occurrence is independently selected from O, S, Se, Te, N(R₃), C(R₃)₂ and Si(R₃)₂; and wherein R₃ at each occurrence is independently selected from hydrogen, an optionally substituted linear or branched C₁-C₂₄ alkyl group and an optionally substituted linear or branched C₁-C₂₄ heteroalkyl group.

41. The polymer of any of claims 38-40, wherein the polymer is selected from



42. A method for making the compound of claim 33-35, comprising Pd catalyzed coupling of the compound of any of claims 29-32 or made by the method of claim 36 or a halogenated derivative of the RU3 of claim 38 or 39, with a mono-tin derivative of the RU4 of claim 40.
43. A method for making the polymer of any of claims 38-41, comprising Pd catalyzed coupling of the compound of any of claims 29-32 or made by the method of claim 36 or a halogenated derivative of the RU3 of claim 38 or 39, with a di-tin derivative of the RU4 of claim 40.
44. The method according to claim 7, which is selected from the group consisting of: (a) the method of claim 14; (b) the method of claim 15; (c) the method of claim 20; (d) the method of claim 36; and (e) the method of claim 37.
45. The method according to claim 7 or claim 43, further comprising applying a method selected from the group consisting of: (a) the method of claim 25; (b) the method of claim 26; (c) the method of claim 42; and (d) the method of claim 43.
46. The method according to any of claim 7, 43 and 44, wherein the method is adapted for making a compound or polymer selected from the group consisting of: (a) the compound of claim 8; (b) the compound of claim 9; (c) the compound of claim 10; (d) the compound of claim 11; (e) the compound of claim 12; (f) the compound of claim 13; (g) the compound of claim 16; (h) the compound of claim 17; (i) the compound of claim 18; (j) the polymer of claim 21; (k) the polymer of claim 22; (l) the polymer of claim 23; (m) the polymer of claim 24; (n) the compound of claim 27; (o) the compound of claim 28; (p) the compound of claim 29; (q) the compound of claim 30; (r) the compound of claim 31; (s) the compound of claim 32; (t) the compound of claim 33; (u) the compound of claim 34; (v) the compound of claim 35; (w) the polymer of claim 38; (x) the polymer of claim 39; (y) the polymer of claim 40; and (z) the polymer of claim 41.
47. A compound susceptible of being directly obtained by the method of any of claims 7 and 44-46.
48. A composition comprising at least one compound or polymer of any of claims 1-4, 8-13, 16-19, 21-24, 27-35, 38-41 and 47, or made by the method of any of claims 5-7, 14-15, 20, 25-26, 36-37 and 42-46.

49. An electronic or optoelectronic device, comprising the compound or polymer of any of claims 1-4, 8-13, 16-19, 21-24, 27-35, 38-41 and 47, or made by the method of any of claims 5-7, 14-15, 20, 25-26, 36-37 and 42-46, or the composition of claim 48.

50. An electronic or optoelectronic device, comprising a film obtained by solution processing and annealing a composition, said composition comprising at least one solvent and at least one compound or polymer of any of claims 1-4, 8-13, 16-19, 21-24, 27-35, 38-41 and 47, or made by the method of any of claims 5-7, 14-15, 20, 25-26, 36-37 and 42-46.

51. A nanostructure, optionally in the form of a nanowire, a nanobelt, a nanoribbon, a nanotube, or a nanorod, the nanostructure comprising the compound or polymer of any of claims 1-4, 8-13, 16-19, 21-24, 27-35, 38-41 and 47 or made by the method of any of claims 5-7, 14-15, 20, 25-26, 36-37 and 42-46, or the composition of claim 48.

52. An nano-electronic or nano-optoelectronic device comprising the nanostructure of claim 51.

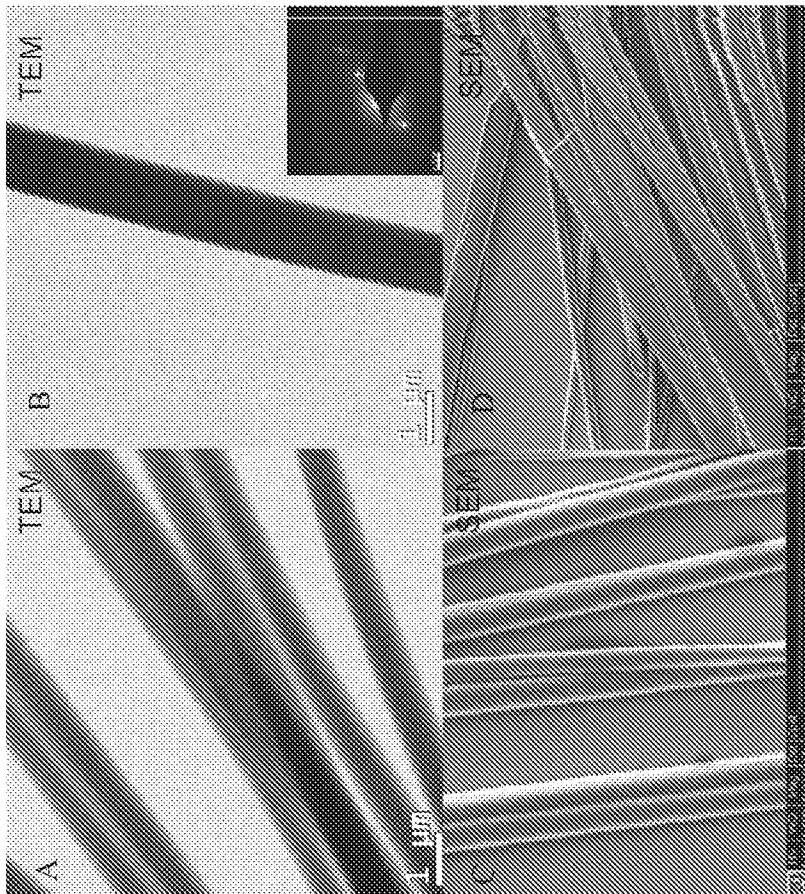


Figure 1

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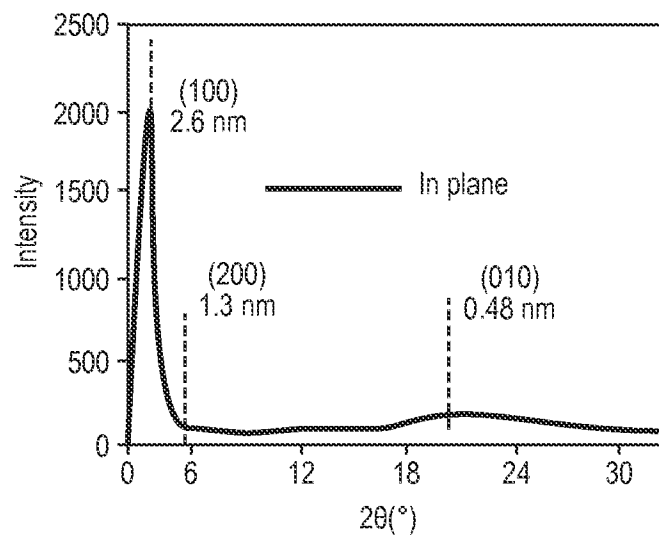


Figure 2A

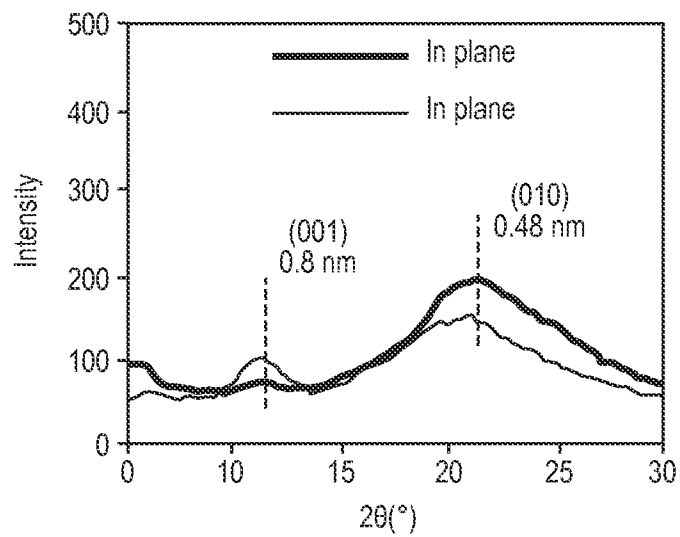


Figure 2B

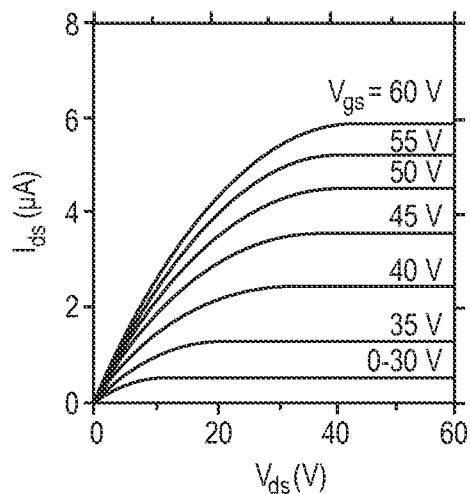


Figure 3A

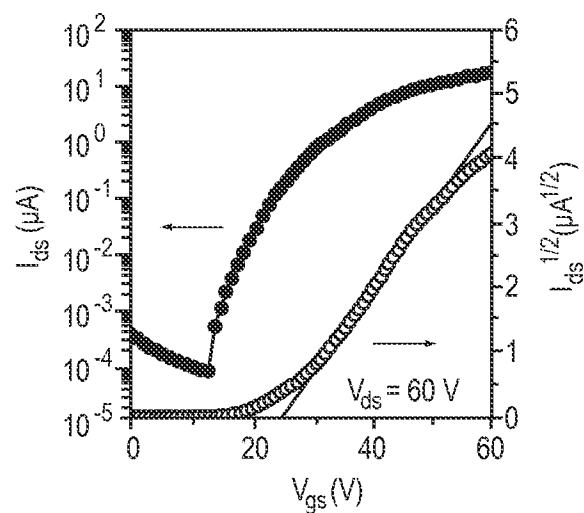


Figure 3B

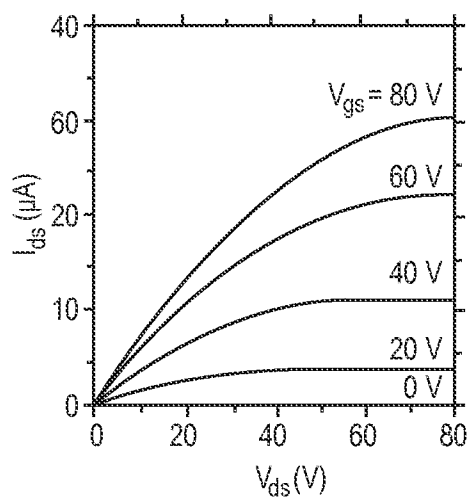


Figure 3C

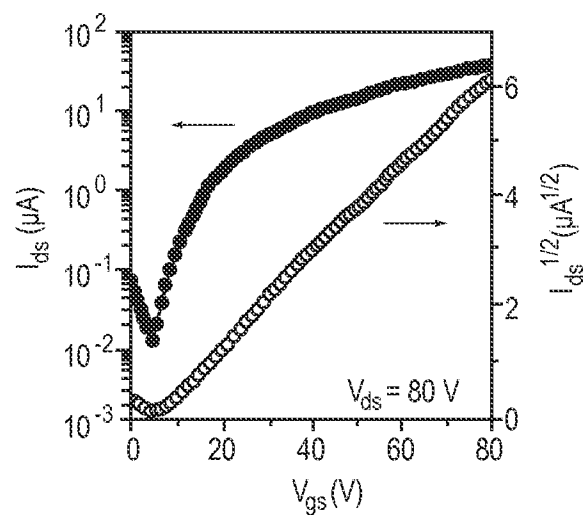


Figure 3D

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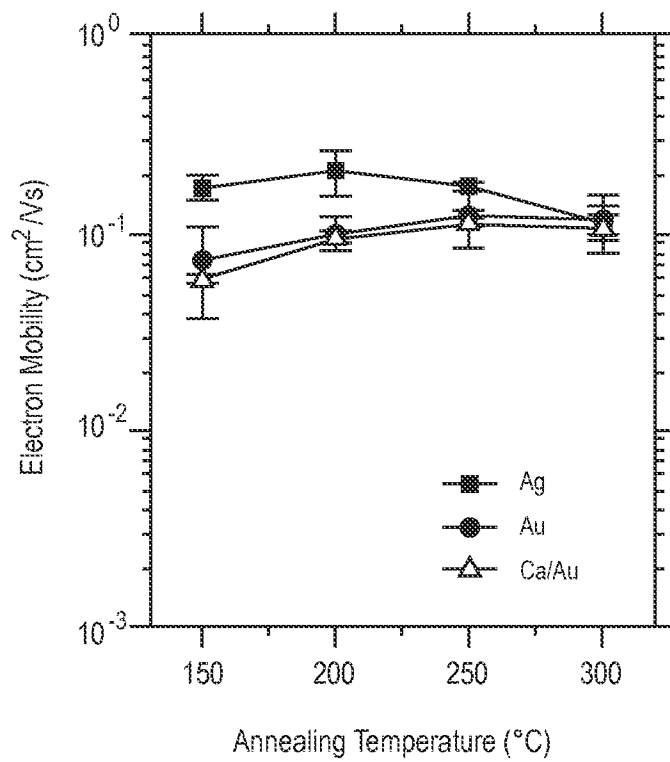


Figure 4

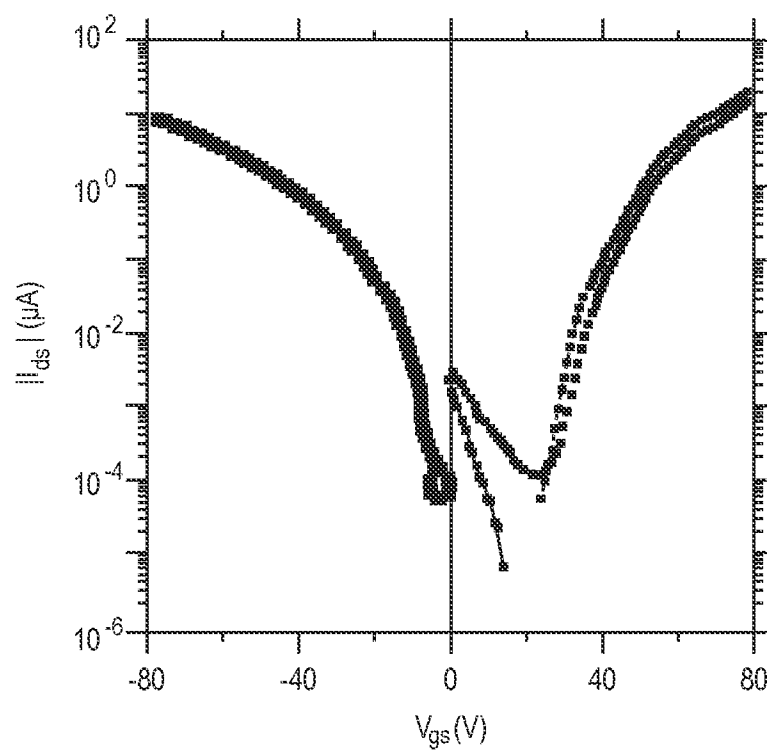


Figure 5

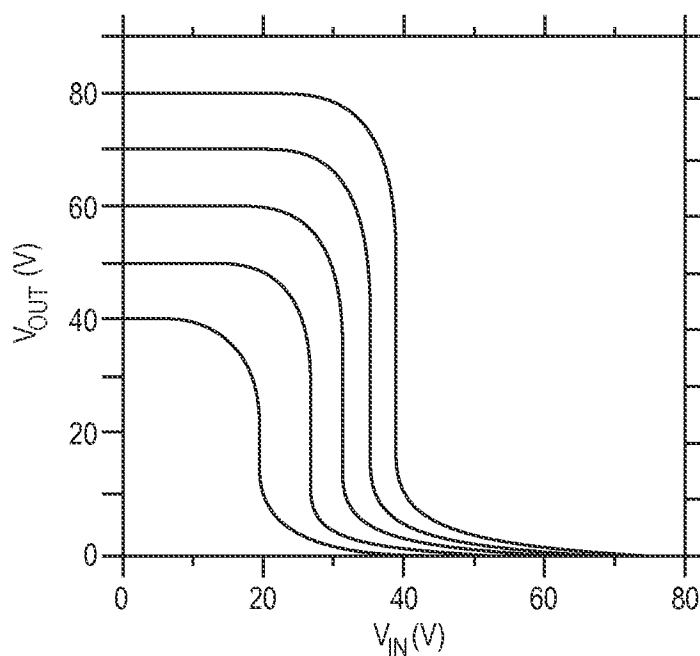


Figure 6A

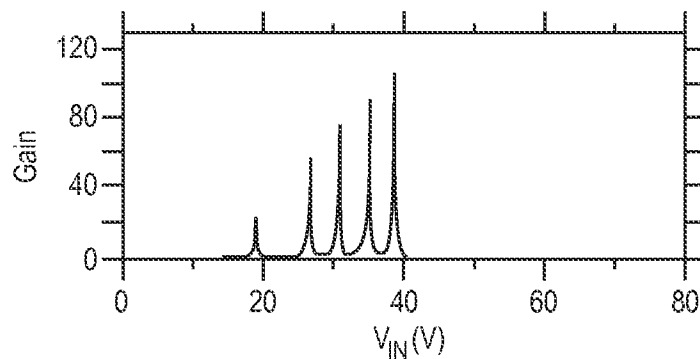


Figure 6B

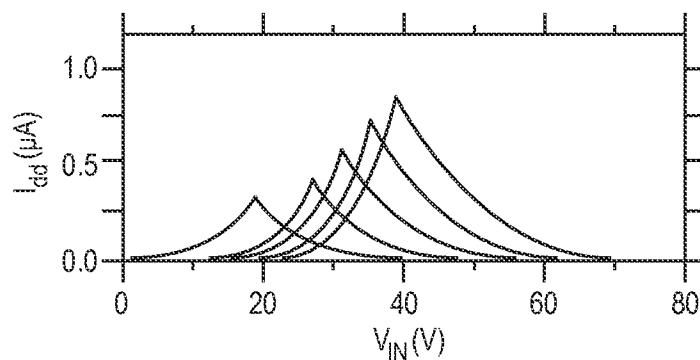


Figure 6C

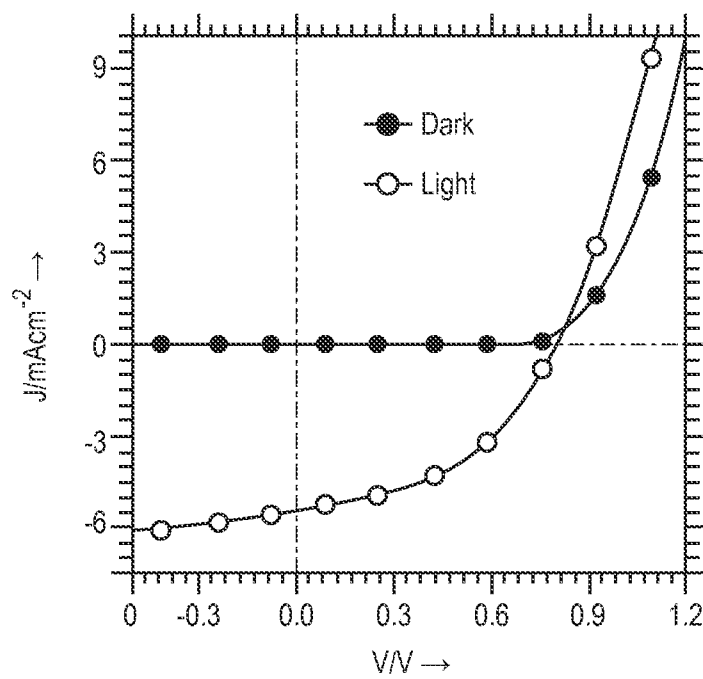


Figure 7A

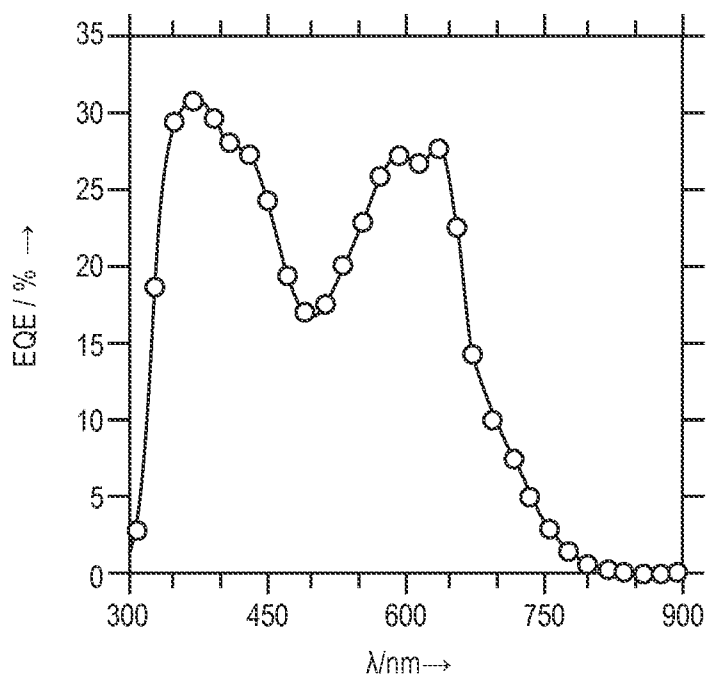


Figure 7B

INTERNATIONAL SEARCH REPORT

International application No
PCT/US2013/055984

A. CLASSIFICATION OF SUBJECT MATTER

INV. C07D221/18 C07D471/06 C07D471/22 C07D495/16 H01L51/00
ADD.

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)

C07D

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practicable, search terms used)

EPO-Internal, WPI Data, BEILSTEIN Data, BIOSIS, CHEM ABS Data

C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
A	JOHN E. ANTHONY ET AL: "n-Type Organic Semiconductors in Organic Electronics", ADVANCED MATERIALS, vol. 22, no. 34, 16 August 2010 (2010-08-16), pages 3876-3892, XP055029012, ISSN: 0935-9648, DOI: 10.1002/adma.200903628 chapter 3; figures 2, 3	1-52
A	WO 2009/126203 A1 (EASTMAN KODAK CO [US]; SHUKLA DEEPAK [US]; WELTER THOMAS ROBERT [US]) 15 October 2009 (2009-10-15) cited in the application compound Int-8 on page 32 ----- -/--	1-7

☒ Further documents are listed in the continuation of Box C.

☒ See patent family annex.

* Special categories of cited documents:

"A" document defining the general state of the art which is not considered to be of particular relevance

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"L" document which may throw doubts on priority claim(s) or which is cited to establish the publication date of another citation or other special reason (as specified)

"O" document referring to an oral disclosure, use, exhibition or other means

"P" document published prior to the international filing date but later than the priority date claimed

"T" later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the invention

"X" document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone

"Y" document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents, such combination being obvious to a person skilled in the art

"&" document member of the same patent family

Date of the actual completion of the international search

20 November 2013

Date of mailing of the international search report

04/12/2013

Name and mailing address of the ISA/

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Authorized officer

Stroeter, Thomas

INTERNATIONAL SEARCH REPORT

International application No

PCT/US2013/055984

C(Continuation). DOCUMENTS CONSIDERED TO BE RELEVANT

Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X	DUAN L ET AL: "Novel naphthalimide derivatives with near-infrared emission: synthesis via photochemical cycloaromatization, fluorescence in solvents and living cell", TETRAHEDRON LETTERS, PERGAMON, GB, vol. 50, no. 1, 7 January 2009 (2009-01-07), pages 22-25, XP025741549, ISSN: 0040-4039, DOI: 10.1016/J.TETLET.2008.10.022 [retrieved on 2008-10-11] compounds 1, 2 -----	27,33, 48-52
X,P	HAIYAN LI ET AL: "Tetraazabenzodifluoranthene Diimides: Building Blocks for Solution-Processable n-Type Organic Semiconductors", ANGEWANDTE CHEMIE INTERNATIONAL EDITION, vol. 52, no. 21, 17 May 2013 (2013-05-17), pages 5513-5517, XP055088185, ISSN: 1433-7851, DOI: 10.1002/anie.201210085 figures; compounds 8-10 -----	1-20,25, 27-37, 42,47-52
X,P	HAIYAN LI ET AL: "High-Mobility n-Type Conjugated Polymers Based on Electron-Deficient Tetraazabenzodifluoranthene Diimide for Organic Electronics", JOURNAL OF THE AMERICAN CHEMICAL SOCIETY, vol. 135, no. 40, 9 October 2013 (2013-10-09), pages 14920-14923, XP055087489, ISSN: 0002-7863, DOI: 10.1021/ja407471b Scheme 1 -----	21-24, 26, 38-41, 43-46
X,P	ROCÍO PONCE&EMSP14;ORTIZ? ET AL: "Molecular and Electronic-Structure Basis of the Ambipolar Behavior of Naphthalimide-Terthiophene Derivatives: Implementation in Organic Field-Effect Transistors", CHEMISTRY - A EUROPEAN JOURNAL, vol. 19, no. 37, 9 September 2013 (2013-09-09), pages 12458-12467, XP055088187, ISSN: 0947-6539, DOI: 10.1002/chem.201301489 Scheme 1; figure 1; compounds 1, 2, NIP-1T, NIP-3T ----- -/--	1-7, 27-37, 47-52

INTERNATIONAL SEARCH REPORT

International application No

PCT/US2013/055984

C(Continuation). DOCUMENTS CONSIDERED TO BE RELEVANT

Category	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X,P	HELENA HERRERA ET AL: "Linear and star-shaped naphthalimide-fused pyrazinacenes", CHEMICAL COMMUNICATIONS, vol. 49, no. 7, 1 January 2013 (2013-01-01), page 713, XP055088194, ISSN: 1359-7345, DOI: 10.1039/c2cc36791b abstract; compounds 1-3, 8 -----	1-20,25, 27-37, 42,47-52
X,P	TOAN PHO ET AL: "Self-Assembling Decacyclene Triimides Prepared through a Regioselective Hextuple Friedel-Crafts Carbamylation", ANGEWANDTE CHEMIE INTERNATIONAL EDITION, vol. 52, no. 5, 28 January 2013 (2013-01-28), pages 1446-1451, XP055087519, ISSN: 1433-7851, DOI: 10.1002/anie.201207608 abstract; compounds 4a,4b,4c -----	8-20,25, 27-37, 42,47-52

INTERNATIONAL SEARCH REPORT

Information on patent family members

International application No

PCT/US2013/055984

Patent document cited in search report	Publication date	Patent family member(s)	Publication date
WO 2009126203 A1	15-10-2009	CN 102027611 A	20-04-2011
		EP 2266150 A1	29-12-2010
		JP 2011520246 A	14-07-2011
		US 2009256137 A1	15-10-2009
		WO 2009126203 A1	15-10-2009
